

# **FM25M32A**

**1.8V 32M-BIT**

**Serial Flash Memory with 4KB Sectors, Dual and Quad I/O SPI & QPI**



## Documents title

32M bit Serial Flash Memory with 4KB Sectors, Dual and Quad I/O SPI &QPI

## Revision History

Revision No.	History	Draft date	Remark
0.0	Initial Draft	Feb.10.2011	preliminary

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## 1. GENERAL DESCRIPTION

The FM25M32A Serial Flash memory provides a storage solution for systems with limited space, pins and power. The 25M series offers flexibility and performance well beyond ordinary Serial Flash devices. They are ideal for code shadowing to RAM, executing code directly from Dual/Quad SPI (XIP) and storing voice, text and data. The devices operate on a single 1.65V to 1.95V power supply with current consumption as low as 5mA active and 3µA for power-down. All devices offered in space-saving packages.

The FM25M32A array is organized into 16,384 programmable pages of 256-bytes each. Up to 256 bytes can be programmed at a time using the Page Program instructions. Pages can be erased in groups of 16 (4KB sector erase), groups of 128 (32KB block erase), groups of 256 (64KB block erase) or the entire chip (chip erase). The FM25M32A has 1,024 erasable sectors and 64 erasable blocks respectively. The small 4KB sectors allow for greater flexibility in applications that require data and parameter storage.

The FM25M32A supports the standard Serial peripheral Interface (SPI), and a high performance Dual output as well as Dual I/O SPI using pins: Serial Clock, Chip Select, Serial Data I/O0(DI), Serial Data I/O1(DO). SPI clock frequencies of up to 104MHz are supported allowing equivalent clock rates of 208MHz for Dual Output and 416MHz for Quad Output when using the Fast Read Dual/Quad Output instructions. These transfer rates are comparable to those of 8 and 16-bit Parallel Flash memories.

A Hold pin, Write protect pin and programmable write protection, with top or bottom array control, provide further control flexibility. Additionally, the device supports JEDEC standard manufacturer and device identification with a 4K-bit Secured OTP.

## 2. FEATURES

- **SpiFlash Memory**
  - FM25M32A: 32M-bit / 4M-byte
  - 256-bytes per programmable page
  - 4K-bit secured OTP
- **Standard, Dual or Quad SPI and QPI**
  - standard SPI: CLK, /CS, DI, DO, /WP, /Hold
  - Dual SPI: CLK, /CS, IO<sub>0</sub>, IO<sub>1</sub>, /WP, /Hold
  - Quad SPI: CLK, /CS, IO<sub>0</sub>, IO<sub>1</sub>, IO<sub>2</sub>, IO<sub>3</sub>
  - QPI: CLK, /CS, IO<sub>0</sub>, IO<sub>1</sub>, IO<sub>2</sub>, IO<sub>3</sub>
- **Highest Performance Serial Flash**
  - Up to 7X that of ordinary Serial Flash
  - 104MHz clock operation
  - 208MHz equivalent Dual SPI
  - 416MHz equivalent Quad SPI
  - 50MB/S continuous data transfer rate
  - 31MB/S random access (32-byte fetch)
  - Comparable to X16 Parallel Flash
- **Package Material**
  - Fidelix all product Green package
    - Lead-free
    - RoHS Compliant
    - Halogen-free
- **Flexible Architecture with 4KB sectors**
  - Uniform Sector Erase (4K-byte)
  - Uniform Block Erase (32K and 64K-bytes)
  - program one to 256 bytes
  - Up to 100,000 erase/write cycles
  - 20-years data retention
  - Erase/Program Suspend & Resume
- **Low Power, wide Temperature Range**
  - Single 1.65 to 1.95V supply
  - 5mA active current, <3µA Power-down (typ.)
  - -40°C to +85°C operating range
- **Advanced Security Features**
  - Software and Hardware Write-protect
  - Top or Bottom, Sector or Block selection
  - Lock-Down and OTP protection
  - Discoverable Parameters(SFDP) Register
- **Space Efficient Packaging**
  - 8-pin SOIC 208mil
  - 8-pad WSON 6x5-mm
  - 16-pin SOIC 300-mil
  - 8-pin DIP 300mil

**3. PIN CONFIGURATION SOIC 208-MIL**

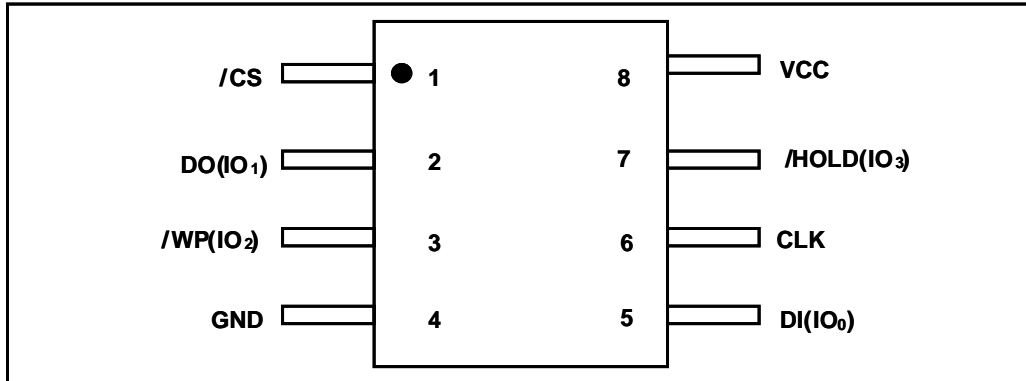


Figure 1a. pin Assignments, 8-pin SOIC 208-mil

**4. PAD CONFIGURATION WSON 6X5-MM**

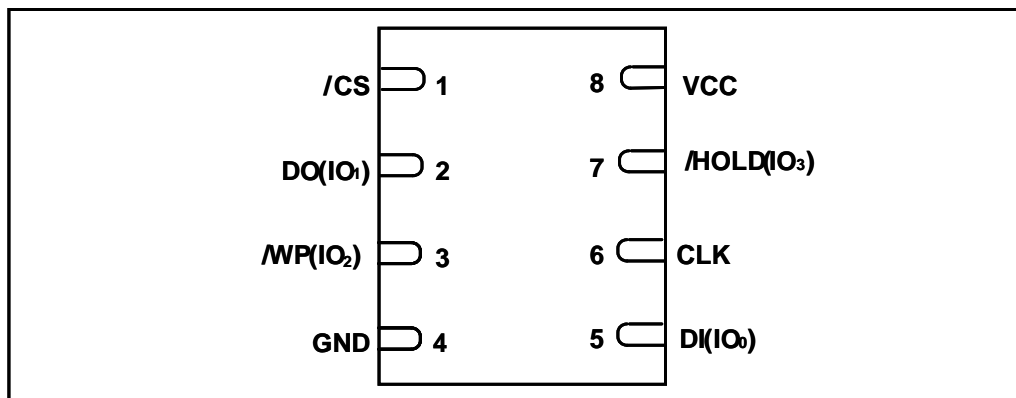


Figure 1b. Pad Assignments, 8-pad WSON

**5. PIN CONFIGURATION 8-Pin PDIP 300-Mil**

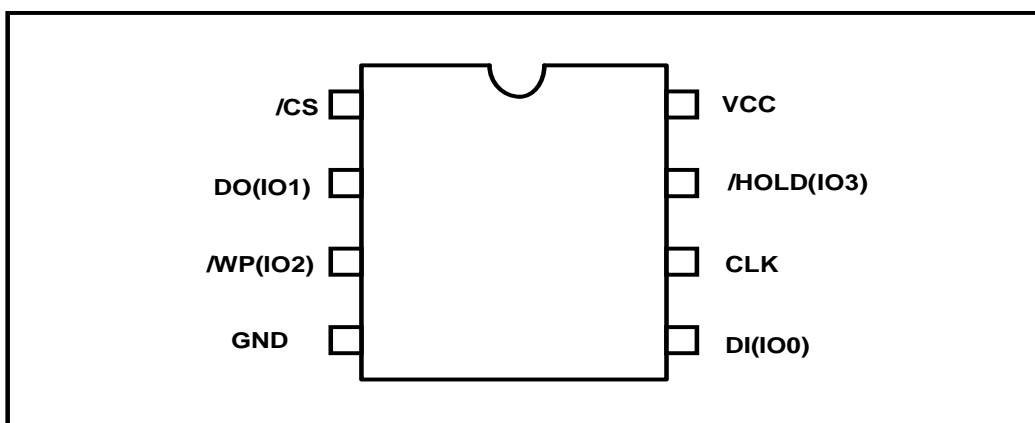


Figure 1c. Assignments, 8-pin PDIP 300-mil

**6. PIN DESCRIPTION SOIC 208-MIL, PDIP 300MIL, WSON 6X5MM**

PIN NO.	PIN NAME	I/O	FUNCTION
1	/CS	I	Chip Select Input
2	DO(IO1)	I/O	Data Output (Data Input Output 1)*1
3	/WP(IO2)	I/O	Write Protect Input (Data Input Output 2) *2
4	GND		Ground
5	DI(IO0)	I/O	Data Input (Data Input Output 0)*1
6	CLK	I	Serial Clock Input
7	/HOLD(IO3)	I/O	Hold Input (Data Input Output 3) *2
8	VCC		Power Supply

\*1 IO0 and IO1 are used for Dual and Quad instructions

\*2 IO0 – IO3 are used for Quad instructions

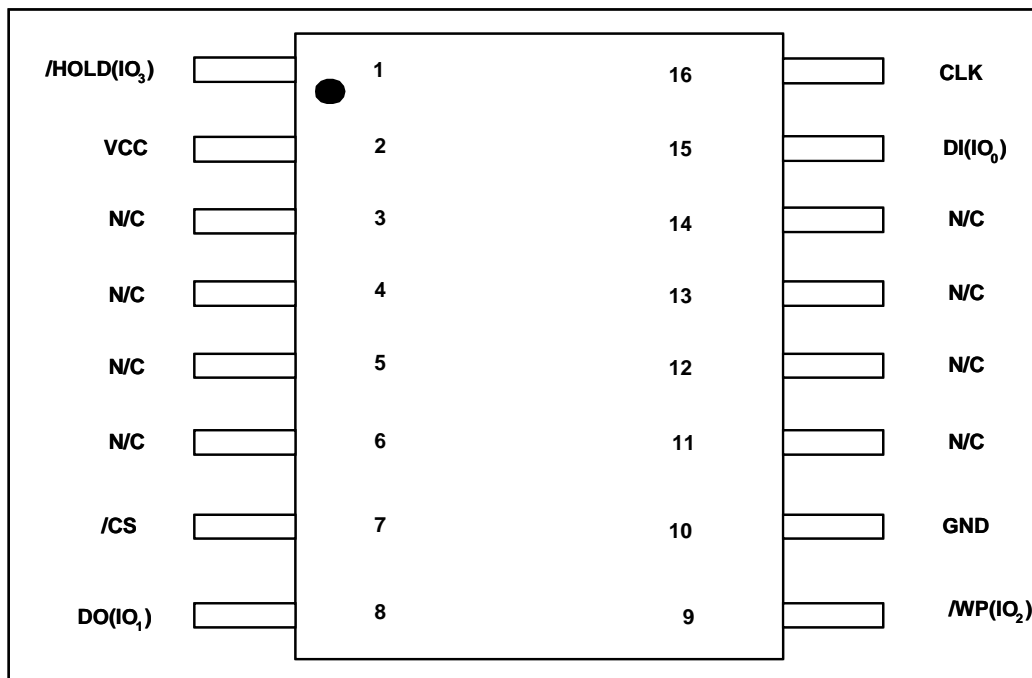
**7. PIN CONFIGURATION SOIC 300-MIL**


Figure 1d. Pin Assignments, 16-pin SOIC 300-mil



**8. PIN DESCRIPTION SOIC 300-MIL**

PAD NO.	PAD NAME	I/O	FUCTION
1	/HOLD(IO3)	I/O	Hold Input(Data Input Output 3)* <sup>2</sup>
2	VCC		Power Supply
3	N/C		No Connect
4	N/C		No Connect
5	N/C		No Connect
6	N/C		No Connect
7	/CS	I	Chip Select Input
8	DO(IO1)	I/O	Data output (Data Input Output 1)* <sup>1</sup>
9	/WP(IO2)	I/O	Write Protection Input (Data Input Output 2)* <sup>2</sup>
10	GND		Ground
11	N/C		No Connect
12	N/C		No Connect
13	N/C		No Connect
14	N/C		No Connect
15	DI(IO0)	I/O	Data Input (Data Input Output 0)* <sup>1</sup>
16	CLK	I	Serial Clock Input

\*1 IO0 and IO1 are used for Dual and Quad instructions

\*2 IO0\_IO3 are used for Quad instructions

## 8.1 Package Types

8-pin plastic 208-mil width SOIC, 6x5-mm WSON, 8-pin PDIP and 16-pin plastic 300-mil width SOIC as shown in figure 1a, 1b, 1c and 1d respectively.

Package diagrams and dimensions are illustrated at the end of this datasheet.

## 8.2 Chip Select (/CS)

The SPI Chip Select (/CS) pin enables and disables device operation. When /CS is high the device is deselected and the Serial Data Output (DO, or IO0, IO1, IO2, IO3) pins are at high impedance. When deselected, the device power consumption will be at standby levels unless an internal erase, program or write status register cycle is in progress. When /CS is brought low the device will be selected, power consumption will increase to active levels and instructions can be written to and read data from the device. After power-up, /CS must transition from high to low before a new instruction will be accepted. The /CS input must track the VCC supply level at power-up (see "Write Protection" and figure 47). If needed a pull-up resistor on /CS can be used to accomplish this.

## 8.3 Serial Data Input, Output and IOs (DI, DO and IO0, IO1, IO2, IO3)

The FM25M32A supports standard SPI, Dual SPI, Quad SPI and QPI operation. Standard SPI instructions use the unidirectional DI (input) pin to serially write instructions, addresses or data to the device on the rising edge of the Serial Clock (CLK) input pin. Standard SPI also uses the unidirectional DO (output) to read data or status from the device on the falling edge of CLK.

Dual/Quad SPI and QPI instructions use the bidirectional IO pins to serially write instructions, addresses or data to the device on the rising edge of CLK and read data or status from the device on the falling edge of CLK. Quad SPI and QPI instructions require the non-volatile Quad Enable bit (QE) in Status Register-2 to be set. When QE=1 the /WP pin becomes IO2 and /HOLD pin becomes IO3.

## 8.4 Write Protect (/WP)

The Write Protect (/WP) pin can be used to prevent the Status Register from being written used in conjunction with the Status Register's Block Protect (CMP, SEC, TB, BP2, BP1 and BP0) bits and Status.

Register Protect (SRP) bits, a portion or the entire memory array can be hardware protected. The /WP pin is active low. When the QE bit of Status Register-2 is set for Quad I/O, the /WP pin (Hardware Write Protect) function is not available since this pin is used for IO2. See figure 1a, 1b, 1c and 1d for the pin configuration of Quad I/O operation.

## 8.5 HOLD (/HOLD)

The /HOLD pin allows the device to be paused while it is actively selected. When /HOLD is brought low, while /CS is low, the DO pin will be at high impedance and signals on the DI and CLK pins will be ignored (don't care). When /HOLD is brought high, device operation can resume. The /HOLD function can be useful when multiple devices are sharing the same SPI signals. The /HOLD pin is active low. When the QE bit of Status Register-2 is set Quad I/O, the /HOLD pin function is not available since this pin used for IO3. See figure 1a, 1b, 1c and 1d for the pin configuration of Quad I/O operation.

## 8.6 Serial Clock (CLK)

The SPI Serial Clock Input (CLK) pin provides the timing for serial input and output operations. ("See SPI Operations")

### 9. BLOCK DIAGRAM

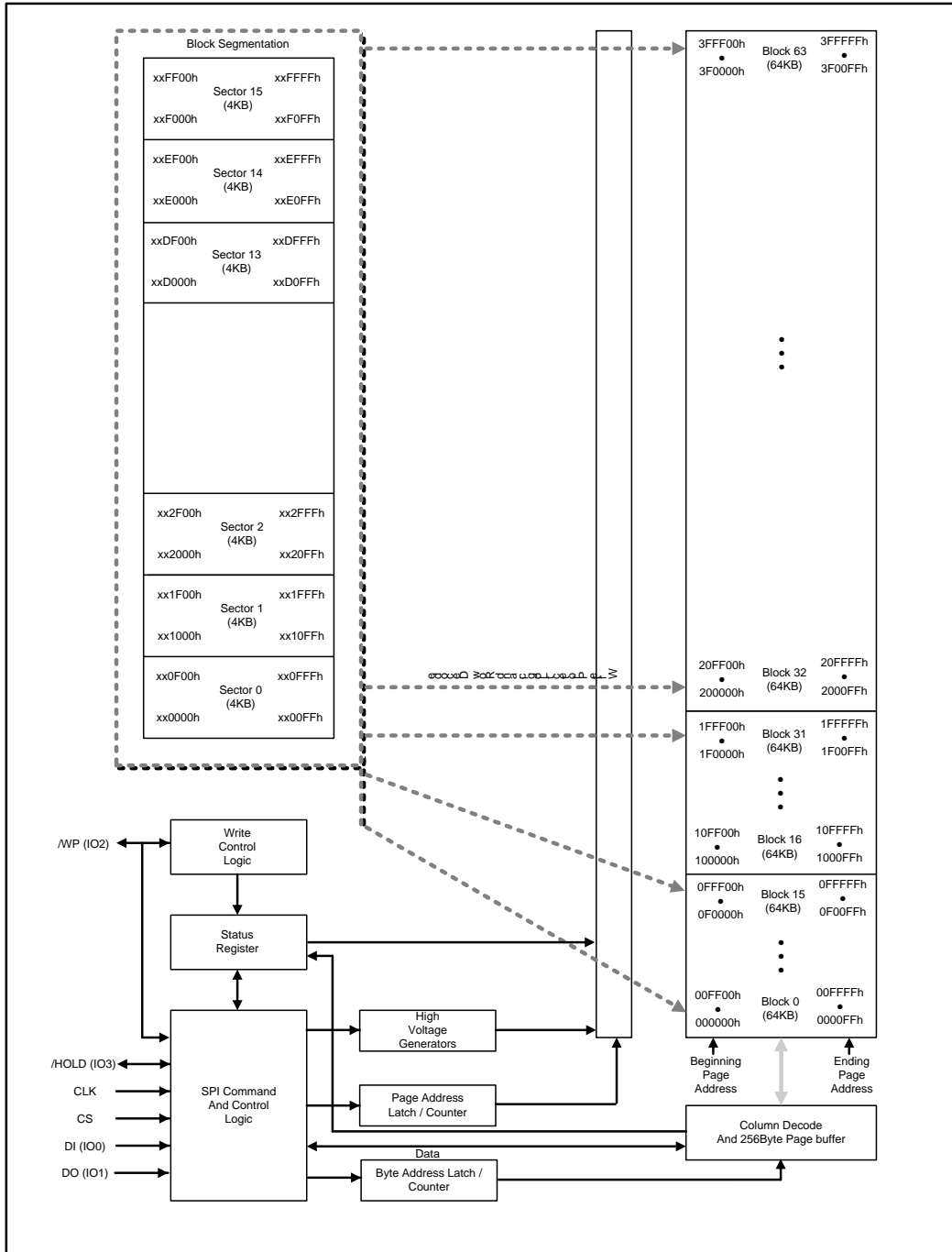


Figure 2. Block Diagram of FM25M32A

## 10. FUNCTIONAL DESCRIPTION

### 10.1 SPI/QPI OPERATIONS

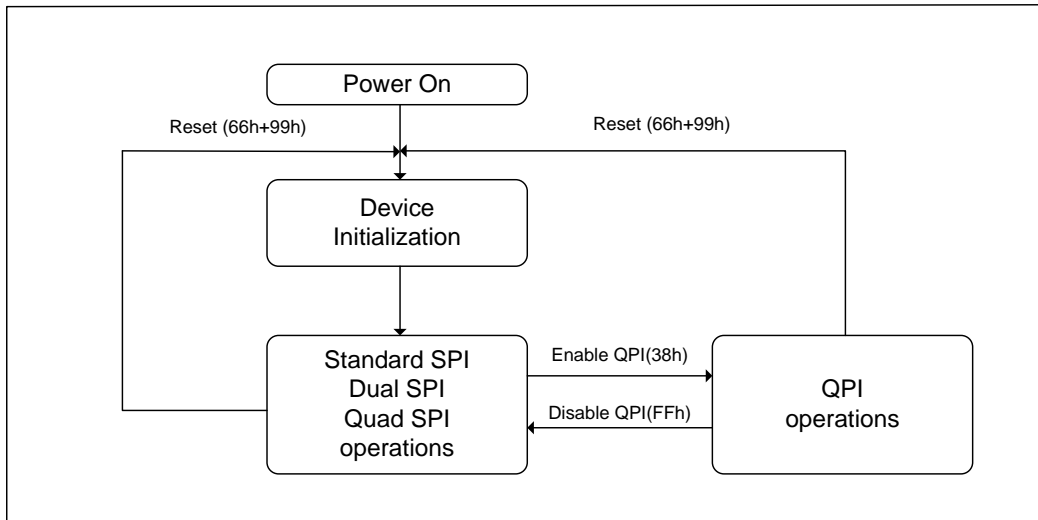


Figure 3. Operation Diagram of FM25M32A

#### 10.1.1 Standard SPI Instructions

The FM25M32A is accessed through an SPI compatible bus consisting of four signals: Serial Clock (CLK), Chip Select (/CS), Serial Data Input (DI) and Serial Data Output (DO). Standard SPI instructions use the DI input pin to serially write instructions, addresses or data to the device on the rising edge of CLK. The DO output pin is used to read data or status from the device on the falling edge of CLK.

SPI bus operation Modes 0 (0, 0) and 3 (1, 1) are supported. The primary difference between Mode 0 and Mode 3 concerns the normal state of the CLK signal when the SPI bus master is in standby and data is not being transferred to the Serial Flash. For Mode 0 the CLK signal is normally low on the falling and rising edges of /CS. For Mode 3 the CLK signal is normally high on the falling and rising edges of /CS.

#### 10.1.2 Dual SPI Instructions

The FM25M32A supports Dual SPI operation when using the “Fast Read Dual I/O” (BB hex) instruction. This instruction allows data to be transferred to or from the device at three to four the rate ordinary Serial Flash devices. The Dual Read instruction is ideal for quickly downloading code to RAM upon power-up (code-shadowing) or for executing non-speed-critical code directly from the SPI bus (XIP). When using Dual SPI instructions the DI and DO pins become bidirectional I/O pins; IO0 and IO1.

#### 10.1.3 Quad SPI Instructions

The FM25M32A supports Quad SPI operation when using the “Fast Read Quad I/O” (EB hex). This instruction allows data to be transferred to or from the device six to seven times the rate of ordinary Serial Flash. The Quad Read instruction offers a significant improvement in continuous and random access transfer rates allowing fast code-shadowing to RAM or execution directly from the SPI bus (XIP). When using Quad SPI instruction the DI and DO pins become bidirectional IO0 and IO1, and the /WP and /HOLD pins become IO2 and IO3 respectively. Quad SPI instructions require the non-volatile Quad Enable bit (QE) in Status Register-2 to be set.

### 10.1.4 QPI Function

The FM25M32A supports Quad Peripheral Interface (QPI) operation when the device is switched from Standard/ Dual/ Quad SPI mode to QPI mode using the “Enable QPI (38h)” instruction. The typical SPI protocol requires that the byte-long instruction code being shifted into the device only via DI pin in eight serial clocks. The QPI mode utilizes all four IO pins to input the instruction code, thus only two serial clocks are required. This can significantly reduce the SPI instruction overhead and improve system performance in an XIP environment. Standard/ Dual/ Quad SPI mode and QPI mode are exclusive. Only one mode can be active at any given time, “Enable QPI (38h)” and “Disable QPI (FFh)” instructions are used to switch between these two modes. Upon power-up or after software reset using “Reset (99h)” instruction, the default state of the device is Standard/ Dual/ Quad SPI mode. To enable QPI mode, the non-volatile Quad Enable bit (QE) in Status Register-2 is required to be set. When using QPI instructions, the DI and DO pins become bidirectional IO0 and IO1, and the /WP and /HOLD pins become IO2 and IO3 respectively. See Figure 3 for the device operation modes.

### 10.1.5 Hold Function

For Standard SPI and Dual SPI operations, the /HOLD signal allows the FM25M32A operation to be paused while it is actively selected (when /CS is low). The /HOLD function may be useful in cases where the SPI data and clock signals are shared with other devices. For example, consider if the page buffer was only partially written when a priority interrupt requires use of the SPI bus. In this case the /HOLD function can save the state of the instruction and the data in the buffer so programming can resume where it left off once the bus is available again. The /HOLD function is only available for standard SPI and Dual SPI operation, not during Quad SPI or QPI.

To initiate a /HOLD condition, the device must be selected with /CS low. A /HOLD condition will activate on the falling edge of the /HOLD signal if the CLK signal is already low. If the CLK is not already low the /HOLD condition will activate after the next falling edge of CLK. The /HOLD condition will terminate on the rising edge of the /HOLD signal if the CLK signal is already low. If the CLK is not already low the /HOLD condition will terminate after the next falling edge of CLK. During a /HOLD condition, the Serial Data Output (DO) is high impedance, and Serial Data Input (DI) and Serial Clock (CLK) are ignored. The Chip Select (/CS) signal should be kept active (low) for the full duration of the /HOLD operation to avoid resetting the internal logic state of the device.

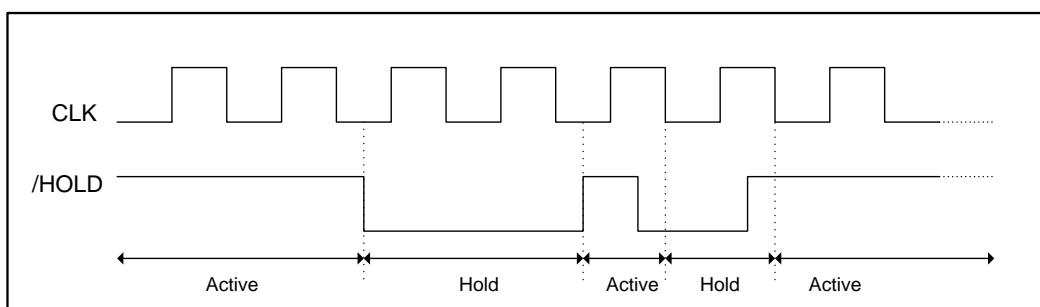


Figure 4. Hold condition waveform (only available Standard/ Dual SPI mode)

## 10.2 WRITE PROTECTION

Applications that use non-volatile memory must take consideration the possibility of noise and other adverse system conditions that may compromise data integrity. To address this concern the FM25M32A provides several means to protect data from inadvertent writes.

### 10.2.1 Write protect Features

- Device resets when VCC is below threshold
- Time delay write disable after Power-up
- Write enable/disable instructions and automatic write disable after program and erase
- Software and Hardware (/WP pin) write protection using Status Register
- Write Protection using Power-down instruction
- Lock Down write protection until next power-up
- One Time Program (OTP) write protection

Upon power-up at power down the FM25M32A will maintain a reset condition while VCC is below the threshold value of VWI, (See Power-up Timing and Voltage Levels and Figure 47). While reset, all operations are disabled and no instruction is recognized. During power-up and after the VCC voltage exceeds VWI, instructions related with all program and erase are further disabled for a time delay of tPUW. This includes the write Enable, Page program, Sector Erase, Block Erase, Chip Erase, Write Security Register and the Write Status Register instructions. Note that the chip select pin (/CS) must track the VCC supply level at power-up until the VCC-min level and tVSL time delay is reached. If a pull-up resistor on /CS can be used to accomplish this.

After power-up the device is automatically placed in a write-disabled state with Status Register Write Enable Latch (WEL) set to a 0. A Write Enable instruction must be issued before a Page Program, Sector Erase Chip Erase or Write Status Register and then instructions will be accepted. After completing a program, erase or write instruction the write Enable (WEL) is automatically cleared to write-disabled state of 0.

Software controlled write protection is facilitated using the Write Status Register instruction and setting the Status Register protect (SRP0, SRP1) and Block protect (CMP, SEC, TB, BP2, BP1, and BP0) bits. These setting allow a portion or all the memory to be configured as read only. Used in conjunction with the Write Protect (/WP) pin, changes to the Status Register can be enabled or disabled under hardware control. See Status Register for further information. Additionally, the Power-down instruction offers an extra level of write protection as all instructions are ignored except for Release power-down instruction.

## 11. CONTROL AND STATUS REGISTER

The Read Status Register-1 and Read Status Register-2 instructions can be used to provide status on the availability of the Flash memory array, if the device is write enabled or disabled, the state of write protection and the Quad SPI setting. The Write Status Register-1 and Write Status Register-2 instructions can be used to configure the devices write protection features and Quad SPI setting. Write access to the Status Register is controlled by in some cases of the /WP pin.

### 11.1 STATUS REGISTER

#### 11.1.1 BUSY

BUSY is a read only bit in the status register(S0) that is set to a 1 state when the device is executing a Page Program, Quad Data Input Page Program, Quad Page Program, Sector Erase, Block Erase, Chip Erase, Write Status Register or Write Security Register instruction. During this time the device will ignore further instruction except for the Read Status Register, Read Security Register and Erase/ Program Suspend instruction (see tW, tPP, tSE, tBE1, tBE2 and tCE in AC Characteristics). When the program, erase, write security register or write status register

instruction has completed, the BUSY bit will be cleared to a 0 state indicating the device is ready for further instructions.

### **11.1.2 Write Enable Latch (WEL)**

Write Enable Latch (WEL) is a read only bit in the status register(S1) that is set to a 1 after executing a Write Enable instruction. The WEL status bit is cleared to a 0, when device is write disabled. A write disable state occurs upon power-up or after any of the following instructions: Write Disable, Page Program, Quad Page Program, Quad Data Input Page Program, Sector Erase, Block Erase, Chip Erase and Write Status Register.

### **11.1.3 Block Protect Bits (BP2, BP1, BP0)**

The Block Protect Bits (BP2, BP1, BP0) are non-volatile read/write bits in the status register (S4, S3, and S2) that provide write protection control and status. Block protect bits can be set using the Write Status Register-1 Instruction (see tW in AC characteristics). All none or a portion of the memory array can be protected from Program and Erase instructions (see Status Register Memory Protection table). The factory default setting for the Block Protection Bits is 0, none of the array protected.

### **11.1.4 Top/Bottom Block protect (TB)**

The non-volatile Top/Bottom bit (TB) controls if the Block Protect Bits (BP2, BP1, BP0) protect from the Top (TB=0) or the Bottom (TB=1) of the array as shown in the Status Register Memory Protection table. The factory default setting is TB=0. The TB bit can be set with the Write Status Register-1 Instruction depending on the state of the SRP0, SRP1 and WEL bits.

### **11.1.5 Sector/Block Protect (SEC)**

The non-volatile Sector protect bit (SEC) controls if the Block Protect Bits (BP2, BP1, BP0) protect 4KB Sectors (SEC=1) or 64KB Blocks (SEC=0) in the Top (TB=0) or the Bottom (TB=1) of the array as shown in the Status Register Memory protection table. The default setting is SEC=0.

### **11.1.6 Complement Protect (CMP)**

The Complement Protect bit (CMP) is a non-volatile read/write bit in the status register (S14). It is used in conjunction with SEC, TB, BP2, BP1 and BP0 bits to provide more flexibility for the array protection. Once CMP is set to 1, previous array protection set by SEC, TB, BP2, BP1 and BP0 will be reversed. For instance, when CMP=0, a top 4KB sector can be protected while the rest of the array is not; when CMP=1, the top 4KB sector will become unprotected while the rest of the array become read-only. Please refer to the Status Register Memory Protection table for details. The default setting is CMP=0.

### **11.1.7 Status Register protect (SRP1, SRP0)**

The Status Register Protect bits (SRP1 and SRP0) are non-volatile read/write bits in the status register (S8 and S7). The SRP bits control the method of write protection: software protection, hardware protection, power supply lock-down or one time programmable (OTP) protection.

SRP1	SRP0	/WP	Status Register	Description
0	0	X	Software Protection	/WP pin no control. The register can be written to after a Write Enable instruction, WEL=1. [Factory Default]
0	1	0	Hardware Protected	When /WP pin is low the Status Register locked and can not be written to.
0	1	1	Hardware Unprotected	When /WP pin is high the Status register is unlocked and can be written to after a Write Enable instruction, WEL=1
1	0	X	Power Supply Lock-Down	Status Register is protected and can not be written to again until the next power-down, power-up cycle <sup>(1)</sup> .
1	1	X	One Time Program	Status Register is permanently protected and can not be written to.

Note:

1. When SRP1, SRP0=(1,0), a power-down, power-up cycle will change SRP1, SRP0 to(0,0) state.

#### 11.1.8 Erase/Program Suspend Status (SUS)

The Suspend Status bit is a read only bit in the status register (S15) that is set to 1 after executing an Erase/Program Suspend (75h) instruction. The SUS status bit is cleared to 0 by Erase/Program Resume (7Ah) instruction as well as a power-down, power-up cycle.

#### 11.1.9 Quad Enable (QE)

The Quad Enable (QE) bit is a non-volatile read/write bit in the status register (S9) that allows Quad operation. When the QE bit is set to a 0 state (factory default) the /WP pin and /Hold are enabled. When the QE pin is set to a 1 the Quad IO2 and IO3 pins are enabled.

**WARNING : The QE bit should never be set to a 1 during standard SPI or Dual SPI operation if the /WP or /HOLD pins are tied directly to the power supply or ground.**



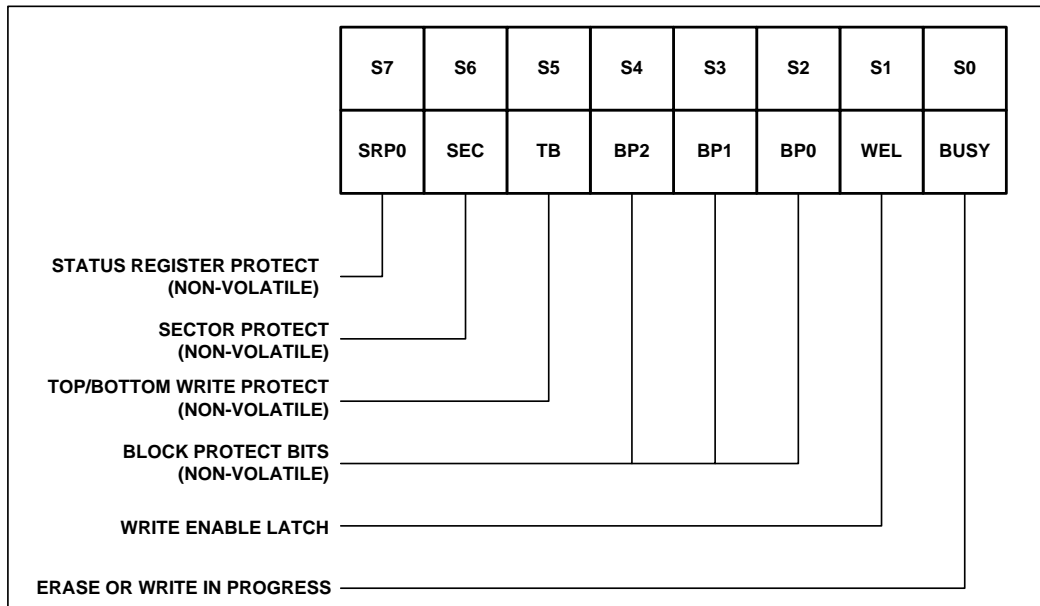


Figure 5a. Status Register-1

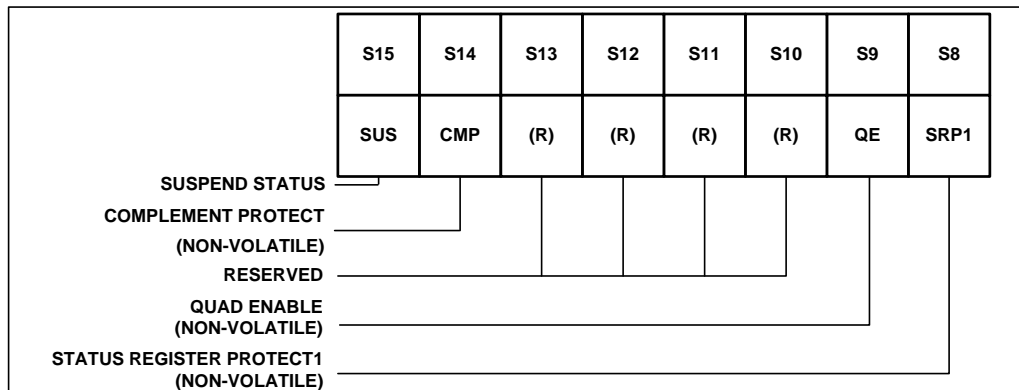


Figure 5b. Status Register-2

**11.1.10 Status Register Memory Protection (CMP= 0)**

STATUS REGISTER <sup>(1)</sup>					MEMORY PROTECTION			
SEC	TB	BP2	BP1	BP0	BLOCK(S)	ADDRESSES	DENSITY	PORTION
X	X	0	0	0	NONE	NONE	NONE	NONE
0	0	0	0	1	63	3F0000h-3FFFFFFh	64KB	Upper 1/64
0	0	0	1	0	62 and 63	3E0000h-3FFFFFFh	128KB	Upper 1/32
0	0	0	1	1	60 thru 63	3C0000h-3FFFFFFh	256KB	Upper 1/16
0	0	1	0	0	56 thru 63	380000h-3FFFFFFh	512KB	Upper 1/8
0	0	1	0	1	48 thru 63	300000h-3FFFFFFh	1MB	Upper 1/4
0	0	1	1	0	32 thru 63	200000h-3FFFFFFh	2MB	Upper 1/2
0	1	0	0	1	0	000000h-00FFFFh	64KB	Lower 1/64
0	1	0	1	0	0 and 1	000000h-01FFFFh	128KB	Lower 1/32
0	1	0	1	1	0 thru 3	000000h-03FFFFh	256KB	Lower 1/16
0	1	1	0	0	0 thru 7	000000h-07FFFFh	512KB	Lower 1/8
0	1	1	0	1	0 thru 15	000000h-0FFFFFFh	1MB	Lower 1/4
0	1	1	1	0	0 thru 31	000000h-1FFFFFFh	2MB	Lower 1/2
X	X	1	1	1	0 thru 63	000000h-3FFFFFFh	4MB	ALL
1	0	0	0	1	63	3FF000h-3FFFFFFh	4KB	Top Block
1	0	0	1	0	63	3FE000h-3FFFFFFh	8KB	Top Block
1	0	0	1	1	63	3FC000h-3FFFFFFh	16KB	Top Block
1	0	1	0	X	63	3F8000h-3FFFFFFh	32KB	Top Block
1	1	0	0	1	0	000000h-000FFFh	4KB	Bottom Block
1	1	0	1	0	0	000000h-001FFFh	8KB	Bottom Block
1	1	0	1	1	0	000000h-003FFFh	16KB	Bottom Block
1	1	1	0	X	0	000000h-007FFFh	32KB	Bottom Block

**Note :**

1. X = don't care
2. L = Lower; U = Upper
3. If any Erase or Program command specifies a memory region that contains protected data portion, this command will be ignored.

**11.1.11 Status Register Memory Protection (CMP= 1)**

STATUS REGISTER <sup>(1)</sup>					MEMORY PROTECTION			
SEC	TB	BP2	BP1	BP0	BLOCK(S)	ADDRESSES	DENSITY	PORTION
X	X	0	0	0	0 thru 63	000000h - 3FFFFFFh	4MB	ALL
0	0	0	0	1	0 thru 62	000000h - 3EFFFFh	4,032KB	Lower 63/64
0	0	0	1	0	0 and 61	000000h - 3DFFFFh	3,968KB	Lower 31/32
0	0	0	1	1	0 thru 59	000000h - 3BFFFFh	3,840KB	Lower 15/16
0	0	1	0	0	0 thru 55	000000h - 27FFFFh	3,584KB	Lower 7/8
0	0	1	0	1	0 thru 47	000000h - 2FFFFFFh	3MB	Lower 3/4
0	0	1	1	0	0 thru 31	000000h - 1FFFFFFh	2MB	Lower 1/2
0	1	0	0	1	1 thru 63	010000h - 3FFFFFFh	4,032KB	Upper 63/64
0	1	0	1	0	2 and 63	020000h - 3FFFFFFh	3,968KB	Upper 31/32
0	1	0	1	1	4 thru 63	040000h - 3FFFFFFh	3,840KB	Upper 15/16
0	1	1	0	0	8 thru 63	080000h - 3FFFFFFh	3,854KB	Upper 7/8
0	1	1	0	1	16 thru 63	100000h - 3FFFFFFh	3MB	Upper 3/4
0	1	1	1	0	32 thru 63	200000h - 3FFFFFFh	2MB	Upper 1/2
X	X	1	1	1	NONE	NONE	NONE	NONE
1	0	0	0	1	0 thru 63	000000h - 3EFFFFh	4,092KB	L - 1023/1024
1	0	0	1	0	0 thru 63	000000h - 3DFFFFh	4,088KB	L - 511/512
1	0	0	1	1	0 thru 63	000000h - 3BFFFFh	4,080KB	L - 255/256
1	0	1	0	X	0 thru 63	000000h - 3F7FFFh	4,064KB	L - 127/128
1	1	0	0	1	0 thru 63	001000h - 3FFFFFFh	4,092KB	U - 1023/1024
1	1	0	1	0	0 thru 63	002000h - 3FFFFFFh	4,088KB	L - 511/512
1	1	0	1	1	0 thru 63	004000h - 3FFFFFFh	4,080KB	L - 255/256
1	1	1	0	X	0 thru 63	008000h - 3FFFFFFh	4,064KB	L - 127/128

Note :

1. X = don't care
2. L = Lower; U = Upper
3. If any Erase or Program command specifies a memory region that contains protected data portion, this command will be ignored.

## 11.2 INSTRUCTIONS

The Standard/Dual/Quad SPI instruction set of the FM25M32A consists of thirty seven basic instructions that are fully controlled through the SPI bus (see Instruction Set table 1-3). Instructions are initiated with the falling edge of Chip Select (/CS). The first byte of data clocked into the DI input provides the instruction code. Data on the DI input is sampled on the rising edge of clock with most significant bit (MSB) first.

The QPI instruction set of the FM25M32A consists of thirty one basic instructions that are fully controlled through the SPI bus (see Instruction Set table 4). Instructions are initiated with the falling edge of Chip Select (/CS). The first byte of data clocked through IO[3:0] pins provides the instruction code. Data on all four IO pins are sampled on the rising edge of clock with most significant bit (MSB) first. All QPI instructions, addresses, data and dummy bytes are using all four IO pins to transfer every byte of data with every two serial clocks (CLK).

### 11.2.1 Manufacturer and Device Identification

<b>MANUFACTRER ID</b>	<b>(M7-M0)</b>	
Fidelix Semiconductor	F8h	
<b>Device ID</b>	<b>(ID7-ID0)</b>	<b>(ID15-ID0)</b>
<b>Instruction</b>	<b>ABh,90h,92h,94h</b>	<b>9Fh</b>
FM25M32A	15h	4216h

**11.2.2 Instruction Set Table 1 (SPI)<sup>(1)</sup>**

INSTRUCTION NAME	BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
(CLOCK NUMBER)	(0 - 7)	(8 - 15)	(16 - 23)	(24 - 31)	(32 - 39)	(40 - 47)
Write Enable	06h					
Write Enable For Volatile Status Register	50h					
Write Disable	04h					
Read Status Register-1	05h	(S7-S0) <sup>(2)</sup>				
Read Status Register-2	35h	(S15-S8) <sup>(2)</sup>				
Write Status Register-1 <sup>(6)</sup>	01h	(S7-S0)	(S15-S8)			
Write Status Register-2	31h	(S15-S8)				
Read Data	03h	A23-A16	A15-A8	A7-A0	(D7-D0)	
Fast Read Data	0Bh	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Page Program	02h	A23-A16	A15-A8	A7-A0	(D7-D0) <sup>(3)</sup>	
Enable QPI	38h					
Sector Erase(4KB)	20h	A23-A16	A15-A8	A7-A0		
Block Erase(32KB)	52h	A23-A16	A15-A8	A7-A0		
Block Erase(64KB)	D8h	A23-A16	A15-A8	A7-A0		
Chip Erase	60h/C7h					
Erase/Program Suspend	75h					
Erase/Program Resume	7Ah					
Power-down	B9h					
Release power down/ Device ID <sup>(4)</sup>	ABh	dummy	dummy	dummy	(ID7-ID0) <sup>(2)</sup>	
Read Manufacturer/ Device ID <sup>(4)</sup>	90h	dummy	dummy	00h or 01h	(M7-M0)	(ID7-ID0)
Read JEDEC ID	9Fh	(M7-M0) Manufacturer	(ID7-ID0) Memory Type	(ID7-ID0) Capacity		
Reset Enable	66h					
Reset	99h					
Enter Secured OTP	B1h					
Exit Secured OTP	C1h					
Read Security Register	2Bh	(S7-S0)				
Write Security Register	2Fh					

**11.2.3 Instruction Set Table 2 (Dual SPI Instruction)**

(CLOCK NUMBER) INSTRUCTION NAME	(0 - 7)	(8 - 15)	(16 - 23)	(24 - 31)	(32 - 39)	(40 - 47)
Fast Read Dual Output	<b>3Bh</b>	A23-A16	A15-A7	A7-A0	dummy	(D7-D0) <sup>(7)</sup>
Fast Read Dual I/O	<b>BBh</b>	A23-A8 <sup>(6)</sup>	A7-A0, M7-M0 <sup>(6)</sup>	(D7-D0, ...) <sup>(7)</sup>		
Read Dual Manufacture/ Device ID <sup>(4)</sup>	<b>92h</b>	0000h	(00h, xxxx) or (01h, xxxx)	(M7-M0) (ID7-ID0) <sup>(7)</sup>		

**11.2.4 Instruction Set Table 3 (Quad SPI Instruction)**

(CLOCK NUMBER) INSTRUCTION NAME	(0 - 7)	(8 - 15)	(16 - 23)	(24 - 31)	(32 - 39)	(40 - 47)
Fast Read Quad Output	<b>6Bh</b>	A23-A16	A15-A8	A7-A0	dummy	(D7-D0) <sup>(9)</sup>
Fast Read Quad I/O	<b>EBh</b>	A23-A0, M7-M0 <sup>(8)</sup>	(xxxx, D7-D0,...) <sup>(10)</sup>	(D7-D0, ...) <sup>(9)</sup>		
Quad Data Input Page Program	<b>32h</b>	A23-A16	A15-A8	A7-A0	(D7-D0, ...) <sup>(3)</sup>	
Quad Page Program	<b>33h</b>	A23-A0 (D7-D0, ...) <sup>(8)</sup>				
Read Quad Manufacture/Device ID <sup>(4)</sup>	<b>94h</b>	(00_0000h, xx) or (00_0001h, xx)	(xxxx, M7-M0) (xxxx, ID7-ID0) <sup>(10)</sup>			
Word Read Quad I/O	<b>E7h</b>	A23-A0, M7-M0 <sup>(8)</sup>	(xx, D7-D0..)	(D7-D0) <sup>(9)</sup>		
Set Burst with Wrap	<b>77h</b>	xxxxxx, W6-W4 <sup>(8)</sup>				

**11.2.5 Instruction Set Table 4 (QPI)**

INSTRUCTION NAME		BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6	BYTE 7	BYTE 8
(CLOCK NUMBER)		(0 , 1 )	(2 , 3)	(4 , 5)	(6 , 7)	(8 , 9)	(10 , 11)	(12 , 13)	(14 , 15)
Write Enable		06h							
Write Enable for Volatile Status Register		50h							
Write Disable		04h							
Read Status Register-1		05h	(S7-S0) <sup>(2)</sup>						
Read Status Register-2		35h	(S15-S8) <sup>(2)</sup>						
Write Status Register-1 <sup>(6)</sup>		01h	(S7-S0)	(S15-S8)					
Write Status Register-2		31h	(S15-S8)						
Fast Read Data	>80MHz	0Bh	A23-A16	A15-A8	A7-A0	dummy	dummy	(D7-D0)	
	>104MHz		A23-A16	A15-A8	A7-A0	dummy	dummy	dummy	(D7-D0)
Page Program		02h	A23-A16	A15-A8	A7-A0	(D7-D0) <sup>(3)</sup>			
Sector Erase(4KB)		20h	A23-A16	A15-A8	A7-A0				
Block Erase(32KB)		52h	A23-A16	A15-A8	A7-A0				
Block Erase(64KB)		D8h	A23-A16	A15-A8	A7-A0				
Chip Erase		60h/ C7h							
Erase/Program Suspend		75h							
Erase/Program Resume		7Ah							
Power-down		B9h							
Release power down/ Device ID <sup>(4)</sup>		ABh	dummy	dummy	dummy	(ID7-ID0) <sup>(2)</sup>			
Read Manufacturer/ Device ID <sup>(4)</sup>		90h	00h	00h	00h or 01h	(M7-M0)	(ID7-ID0)		
Read JEDEC ID <sup>(4)</sup>		9Fh	(M7-M0) Manufactur er	(ID7-ID0) Memory Type	(ID7-ID0) Capacity				
Enter Security		B1h							
Exit Security		C1h							
Read Security Register		2Bh	(ID7-ID0)						
Write Security Register		2Fh							
Fast Read Quad I/O	>80MHz	EBh	A23-A16	A15-A8	A7-A0	(M7-M0)	dummy	(ID7-ID0)	
	>104MHz		A23-A16	A15-A8	A7-A0	(M7-M0)	dummy	dummy	(ID7-ID0)
Reset Enable		66h							
Reset		99h							
Disable QPI		FFh							
Disable QPI 2		ALL FFh	ALL FFh	ALL FFh	ALL FFh				
Burst Read with Wrap	>80MHz	0Ch	A23-A16	A15-A8	A7-A0	dummy	dummy	(D7-D0)	
	>104MHz		A23-A16	A15-A8	A7-A0	dummy	dummy	dummy	(D7-D0)

Set Read Parameter	<b>C0h</b>	P7-P0				
Quad Page Program	<b>33h</b>	A23-A16	A15-A8	A7-A0	(D7-D0)	

**Notes:**

1. Data bytes are shifted with Most Significant Bit first. Byte fields with data in parenthesis “()” indicate data being read from the device on the IO pin.
2. The Status Register contents and Device ID will repeat continuously until /CS terminates the instruction.
3. At least one byte of data input is required for Page Program, Quad Page Program and Program Security Register, up to 256 bytes of data input. If more than 256 bytes of data are sent to the device, the addressing will wrap to the beginning of the page and overwrite previously sent data.
4. See Manufacturer and Device Identification table for Device ID information.
5. See section 11.2.10 for more information.

**6. Dual Input Address**

$$IO0 = A22, A20, A18, A16, A14, A12, A10, A8, A6, A4, A2, A0, M6, M4, M2, M0$$

$$IO1 = A23, A21, A19, A17, A15, A13, A11, A9, A7, A5, A3, A1, M7, M5, M3, M1$$
**7. Dual Output data**

$$IO0 = (D6, D4, D2, D0)$$

$$IO1 = (D7, D5, D3, D1)$$
**8. Quad Input Address**

$$IO0 = A20, A16, A12, A8, A4, A0, M4, M0$$

$$IO1 = A21, A17, A13, A9, A5, A1, M5, M1$$

$$IO2 = A22, A18, A14, A10, A6, A2, M6, M2$$

$$IO3 = A23, A19, A15, A11, A7, A3, M7, M3$$
**Set Burst with Wrap Input**

$$IO0 = x, x, x, x, x, x, W4, x$$

$$IO1 = x, x, x, x, x, x, W5, x$$

$$IO2 = x, x, x, x, x, x, W6, x$$

$$IO3 = x, x, x, x, x, x, x, x$$
**9. Quad Input/ Output Data**

$$IO0 = (D4, D0...)$$

$$IO1 = (D5, D1...)$$

$$IO2 = (D6, D2...)$$

$$IO3 = (D7, D3...)$$
**10. Fast Read Quad I/O Data Output**

$$IO0 = (x, x, x, x, D4, D0...)$$

$$IO1 = (x, x, x, x, D5, D1...)$$

$$IO2 = (x, x, x, x, D6, D2...)$$

$$IO3 = (x, x, x, x, D7, D3...)$$



### 11.2.6 Write Enable (06h)

The Write Enable instruction (Figure 6) sets the Write Enable Latch (WEL) bit in the Status Register to a 1. The WEL bit must be set prior to every Page Program, Quad Page Program, Quad Data Input Page Program, Sector Erase, Block Erase, Chip Erase, Write Status Register-1 and Write Status Register-2 instruction. The Write Enable instruction is entered by driving /CS low, shifting the instruction code "06h" into Data Input (DI) pin on the rising edge of CLK, and then driving /CS high.

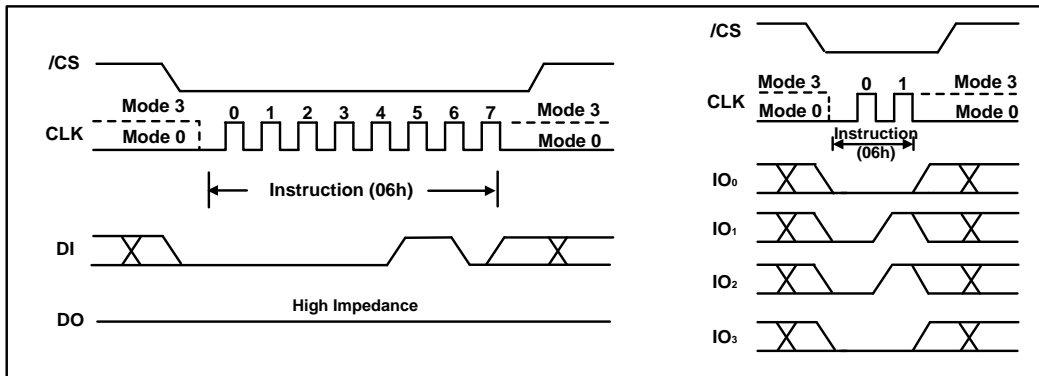


Figure 6. Write Enable Instruction for SPI Mode (left) or QPI Mode (right)

### 11.2.7 Write Enable for Volatile Status Register (50h)

The non-volatile Status Register bits described in section 11.1 can also be written to as volatile bits. This gives more flexibility to change the system configuration and memory protection schemes quickly without waiting for the typical non-volatile bit write cycles or affecting the endurance of the Status Register non-volatile bits. To write the volatile values into the Status Register bits, the Write Enable for Volatile Status Register (50h) instruction must be issued prior to a Write Status Register (01h) instruction. Write Enable for Volatile Status Register instruction (Figure 7) will not set the Write Enable Latch (WEL) bit, it is only valid for the Write Status Register-1 and Write Status Register-2 instruction to change the volatile Status Register bit values

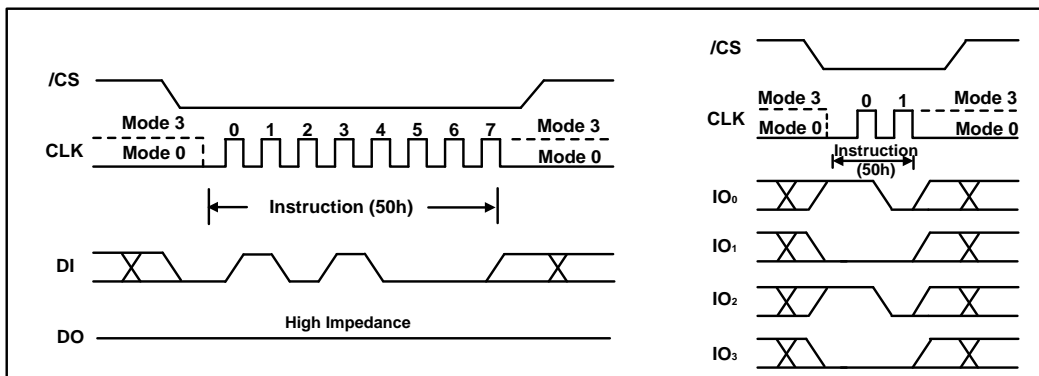


Figure 7. Write Enable for Volatile Status Register Instruction for SPI Mode (left) or QPI Mode (right)

**11.2.8 Write Disable (04h)**

The Write Disable instruction (Figure 8) resets the Write Enable Latch (WEL) bit in the Status Register to a 0. The Write Disable instruction is entered by driving /CS low, shifting the instruction code “04h” into the DI pin and then driving /CS high. Note that the WEL bit is automatically reset after Power-up and upon completion of the Write Status Register-1, Write Status Register-2, Page Program, Quad Page Program, Quad Data Input Page Program, Sector Erase, Block Erase, Chip Erase and Reset instructions.

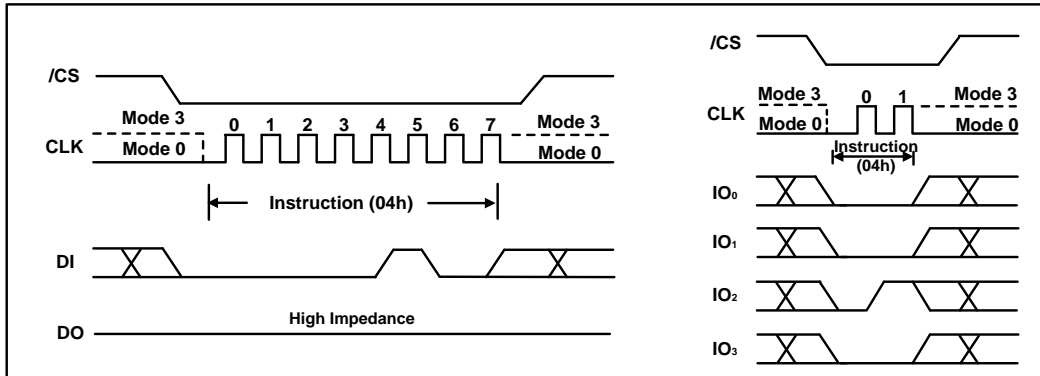


Figure 8. Write Disable Instruction for SPI Mode (left) or QPI Mode (right)

### 11.2.9 Read Status Register-1 (05h) and Read Status Register-2 (35h)

The Read Status Register instructions allow the 8-bit Status Register to be read. The instruction is entered by driving /CS low and shifting the instruction code “05h” for Status Register-1 and “35h” for Status Register-2 into the DI pin on the rising edge of CLK. The status register bits are then shifted out on the DO pin at the falling edge of CLK with most significant bit (MSB) first as shown in figure 9. The Status Register bits are shown in figure 5a and 5b include the BUSY, WEL, BP2-BP0, TB, SEC, SRP0, SRP1, QE, CMP and SUS bits (see description of the Status Register earlier in this datasheet).

The Read Status Register instruction may be used at any time, even while a Program, Erase, Write Security Register or Write Status Register cycle is in progress. This allows the BUSY status bit to be checked to determine when the cycle is complete and if the device can accept another instruction. The Status Register can be read continuously, as shown in Figure 9. The instruction is completed by driving /CS high.

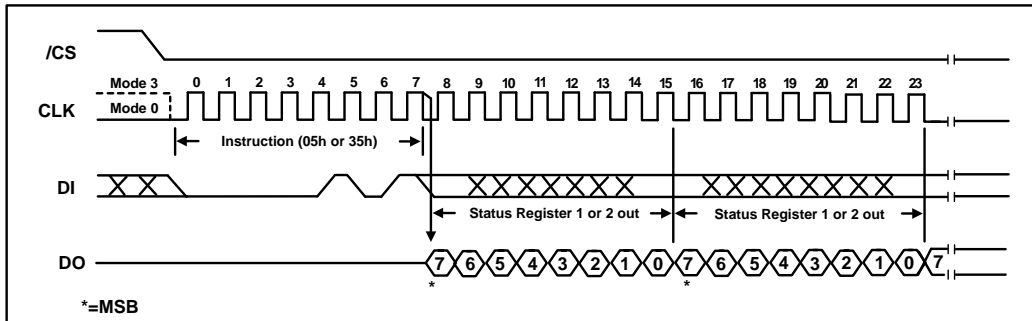


Figure 9a. Read Status Register Instruction (SPI Mode)

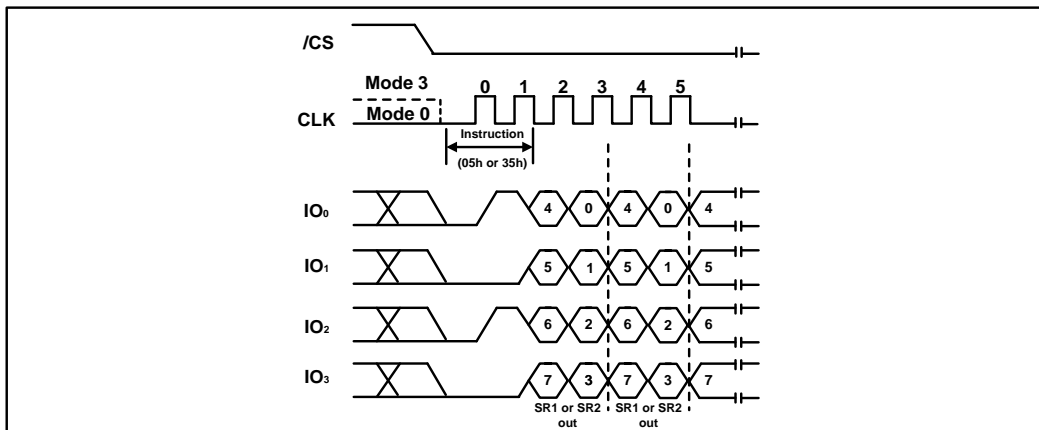


Figure 9b. Read Status Register Instruction (QPI Mode)

### 11.2.10 Write Status Register-1 (01h)

The Write Status Register instruction allows the Status Register to be written. A Write Enable instruction must previously have been executed for the device to accept the Write Status Register Instruction (Status Register bit WEL must equal 1). Once write is enabled, the instruction is entered by driving /CS low, sending the instruction code “01h”, and then writing the status register data byte or word as illustrated in figure 10. The Status Register bits are shown in figure 5a and figure 5b and described earlier in this datasheet.

Only non-volatile Status Register bits SRP0, SEC, TB, BP2, BP1, BP0 (bits 7, 6, 5, 4, 3, 2 of Status Register-1) and CMP, QE, SRP1 (bits 14, 9 and 8 of Status Register-2) can be written to. All other Status Register bit locations are read-only and will not be affected by the Write Status Register-1 instruction. Upon power off or the execution of a “Reset (99h)” instruction, the volatile Status Register bit values will be lost and the non-volatile Status Register bit values will be restored.

The /CS pin must be driven high after the eighth or sixteenth bit of data that is clocked in. If this is not done the Write Status Register instruction will not be executed. If /CS is driven high after the eighth clock, the CMP, QE and SRP1 bits will not be changed. After /CS is driven high, the self-timed Write Status Register cycle will commence for a time duration of tW (See AC Characteristics). While the Write Status Register cycle is in progress, the Read Status Register instruction may still be accessed to check the status of the BUSY bit. The BUSY bit is a 1 during the Write Status Register cycle and a 0 when the cycle is finished and ready to accept other instructions again. After the Write Status Register cycle has finished, The Write Enable Latch (WEL) bit in Status Register will be cleared to 0. (pending issue!!!)

During volatile Status Register write operation (50h combined with 01h), after /CS is driven high, the Status Register bits will be refreshed to the new values within the time period of tSHSL2 (See AC Characteristics). BUSY bit will remain 0 during the Status Register bit refresh period.

The Write Status Register instruction can be used in both SPI mode and QPI mode. However, the QE bit cannot be written to when the device is in the QPI mode, because QE=1 is required for the device to enter and operate in the QPI mode.

The Write Status Register instruction allows the Block Protect bits (SEC, TB, BP2, BP1 and BP0) to be set for protecting all, a portion, or none of the memory from erase and program instructions. Protected areas become read-only (see Status Register Memory Protection table and description). The Write Status Register instruction also allows the Status Register Protect bits (SRP0, SRP1) to be set. Those bits are used in conjunction with the Write protect (/WP) pin, Lock out or OTP features to disable writes to the status register. Please refer to 11.1 for detailed descriptions Status Register protection methods. Factory default all Status Register bits are 0.

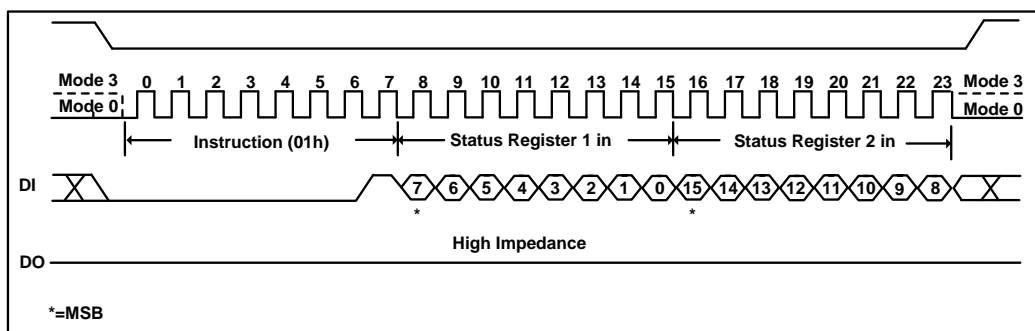


Figure 10a. Write Status Register Instruction (SPI Mode)

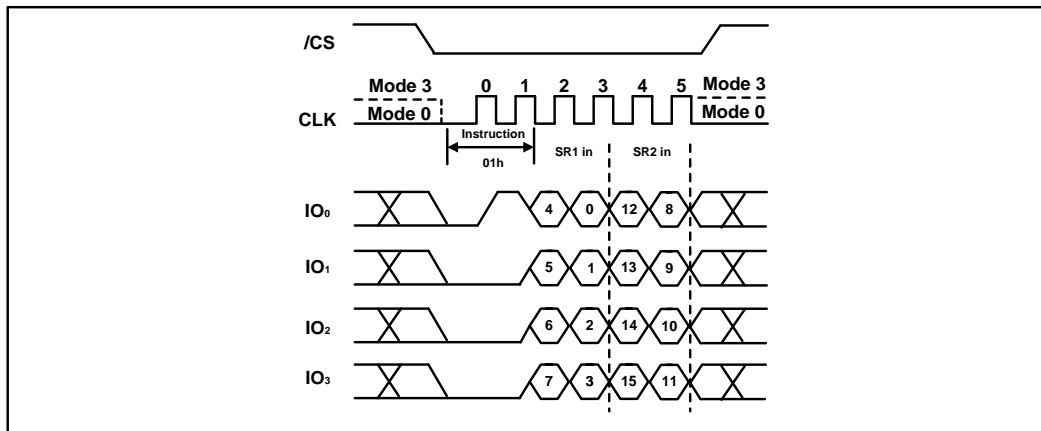


Figure 10b. Write Status Register Instruction (QPI Mode)

**11.2.11 Write Status Register-2 (31h)**

The Write Status 2 instruction allows the Status Register 2 to be written. Only non-volatile Status Register bits CMP, QE, SRP1 of Status Register 2 can be written to. The Status Register bits are shown in Figure 5a and 5b, and described in 11.1

To Write non-volatile Status Register bits, a standard Write Enable instruction must previously have been executed for the device to accept the Write Status Register 2 instruction (Status Register bit WEL must equal 1). Once write enabled, the instruction is entered by driving /CS low, sending the instruction code “(31h)”, and then writing the status register data byte as illustrated in figure 11.

Using Write Status Register-2(31h) command, software can individually access each one-byte status registers via different commands.

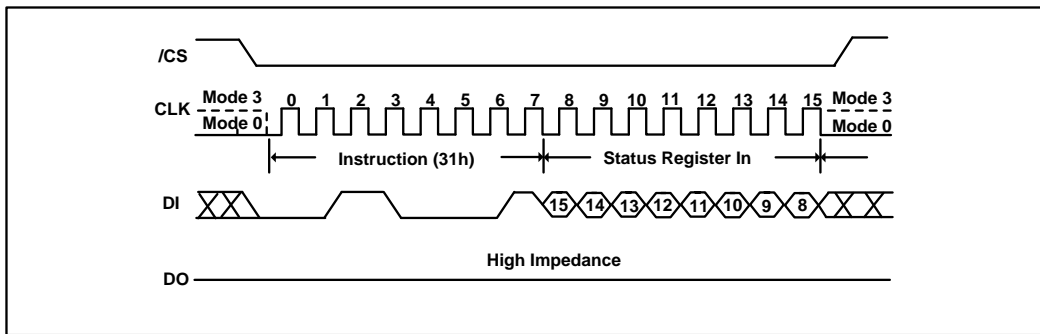


Figure 11a. Write Status Register-2 Instruction (SPI Mode)

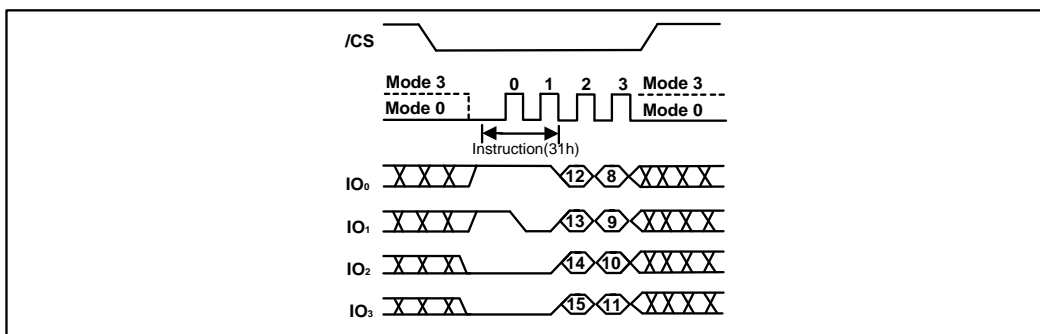


Figure 11b. Write Status Register-2 Instruction (QPI Mode)

**11.2.12 Read Data (03h)**

The Read Data instruction allows one or more data bytes to be sequentially read from the memory. The instruction is initiated by driving the /CS pin low and then shifting the instruction code “03h” followed by a 24-bit address (A23-A0) into the DI pin. The code and address bits are latched on the rising edge of the CLK pin. After the address is received, the data byte of the addressed memory location will be shifted out on the DO pin at the falling edge of CLK with most significant bit (MSB) first. The address is automatically incremented to the next higher address after each byte of data is shifted out allowing for a continuous stream of data. This means that the entire memory can be accessed with a single instruction as long as the clock continues. The instruction is completed by driving /CS high.

The Read Data instruction sequence is shown in figure 12. If a Read Data instruction is issued while an Erase, Program or Write Status Register cycle is in process (BUSY=1) the instruction is ignored and will not have any effects on the current cycle. The Read Data instruction allows clock rates from D.C to a maximum of  $f_R$  (see AC Electrical Characteristics).

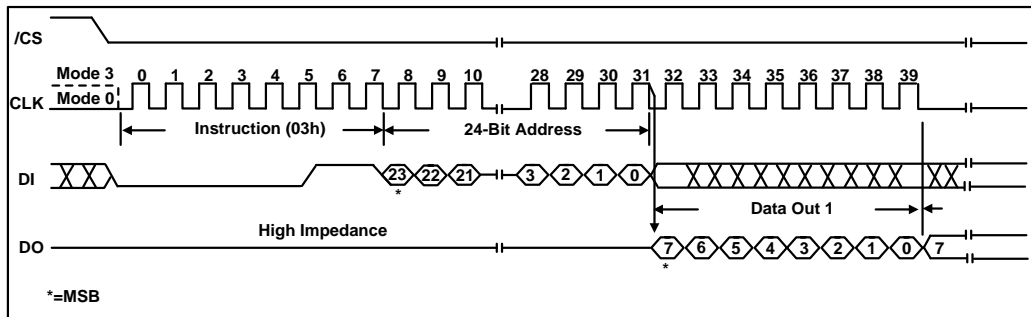


Figure 12. Read Data Register Instruction

### 11.2.13 Fast Read (0Bh)

The Fast Read instruction is similar to the Read Data instruction except that it can operate at the highest possible frequency of  $F_R$  (see AC Electrical Characteristics). This is accomplished by adding eight “dummy” clocks after the 24-bit address as shown in figure 13a and figure 13b. The dummy clocks allow the device’s internal circuits additional time for setting up the initial address. During the dummy clocks, the data value on the DO pin is a “don’t care”.

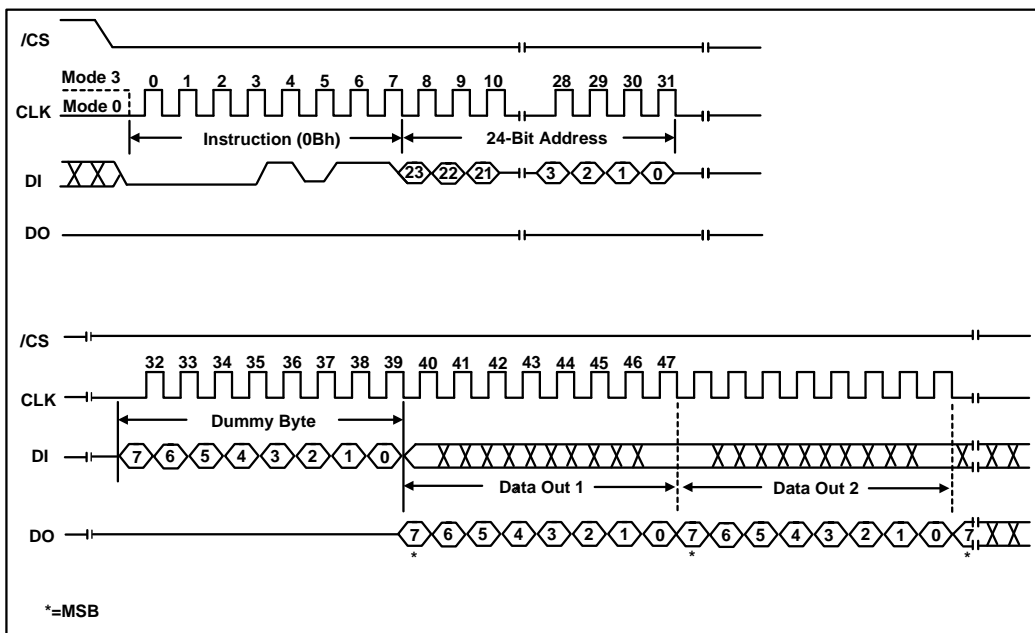


Figure 13a. Fast Read Register Instruction (SPI Mode)

### Fast Read (0Bh) in QPI Mode

The Fast Read instruction is also supported in QPI mode. When QPI mode is enabled, the number of dummy clock is configured by the “Set Read Parameters (C0h)” instruction to accommodate wide range applications with different needs for either maximum Fast Read frequency or minimum data access latency. Depending on the Read Parameter Bit P[4] setting, the number of dummy clocks can be configured as either 4, or 6. The default number of dummy clocks upon power up or after a Reset instruction is 4.



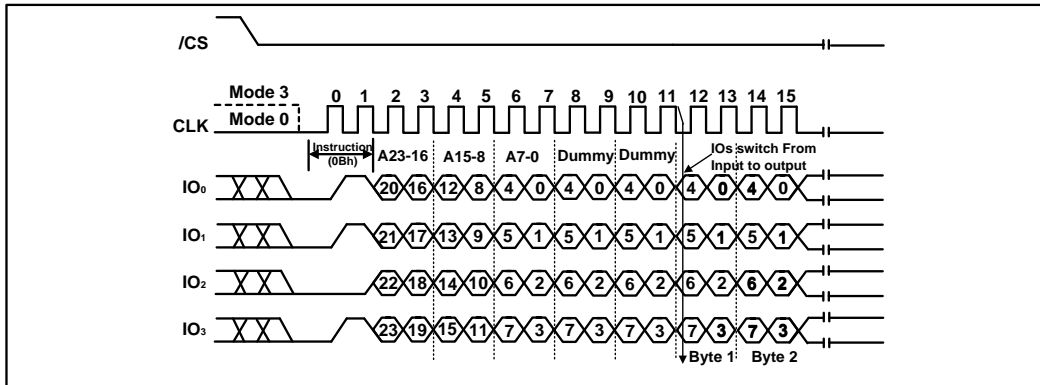


Figure 13b. Fast Read Data instruction (QPI Mode, 80MHz)

**11.2.14 Fast Read Dual Output (3Bh)**

The Fast Read Dual Output instruction is similar to the standard Fast Read (0Bh) instruction except that data is output on two pins: IO<sub>0</sub> and IO<sub>1</sub>, instead of just IO<sub>0</sub>. This allows data to be transferred from the FM25M32A at twice the rate of standard SPI devices. The Fast Read Dual Output instruction is ideal for quickly downloading code from Flash to RAM upon power-up or for application that cache code-segments to RAM for execution.

Similar to the Fast Read instruction, the Fast Read Dual Output instruction can operate at the highest possible frequency of F<sub>R</sub> (see AC Electrical Characteristics). This is accomplished by adding eight “dummy” clocks after the 24-bit address as shown in figure 14. The dummy clocks allow the device’s internal circuits additional time for setting up the initial address. During the dummy clocks, the data value on the DO pin is a “don’t care”. However, the IO<sub>0</sub> pin should be high-impedance prior to the falling edge of the first data out clock. During the dummy clocks, the data value on the DO pin is a “don’t care”. However, the IO<sub>0</sub> pin should be high-impedance prior to the falling edge of the first data out clock.

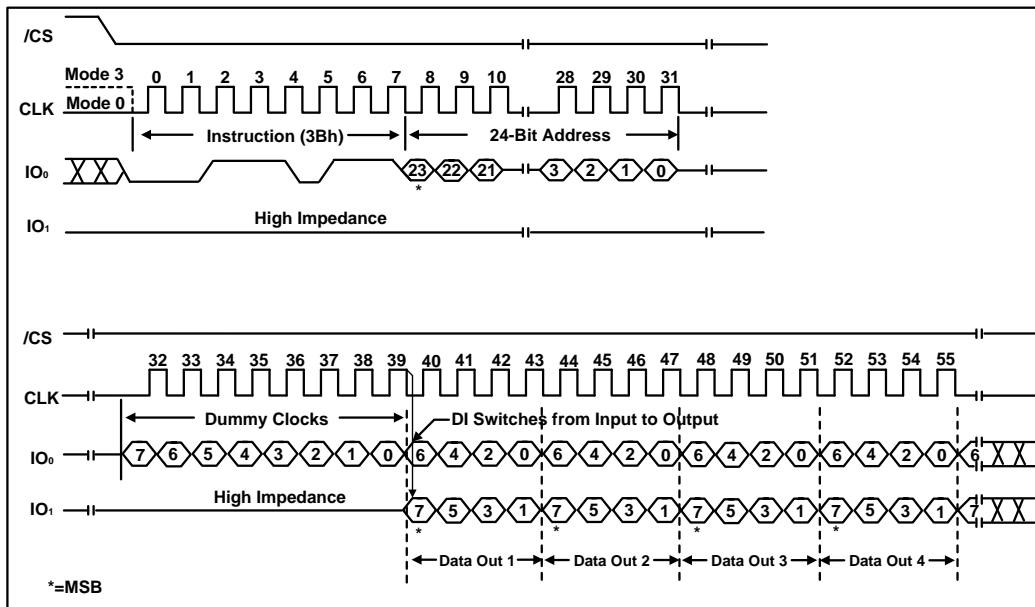


Figure14. Fast Read Dual Output instruction (SPI Mode)

**11.2.15 Fast Read Quad Output (6Bh)**

The Fast Read Quad Output instruction is similar to the Fast Read Dual Output (3Bh) instruction except that data is output on four pins: IO<sub>0</sub>, IO<sub>1</sub>, IO<sub>2</sub>, and IO<sub>3</sub>. A Quad enable of Status Register-2 must be executed before the device will accept the Fast Read Quad Output instruction (Status Register bit QE must equal 1). The Fast Read Quad Output instruction allows data to be transferred from the FM25M32A at four times the rate of standard SPI devices.

The Fast Read Dual Output instruction can operate at the highest possible frequency of F<sub>R</sub> (see AC Electrical Characteristics). This is accomplished by adding eight “dummy” clocks after the 24-bit address as shown in figure 15. The dummy clocks allow the device’s internal circuits additional time for setting up the initial address. During the dummy clocks, the data value on the IO pins is a “don’t care”. However, the IO pins should be high-impedance prior to the falling edge of the first data out clock.

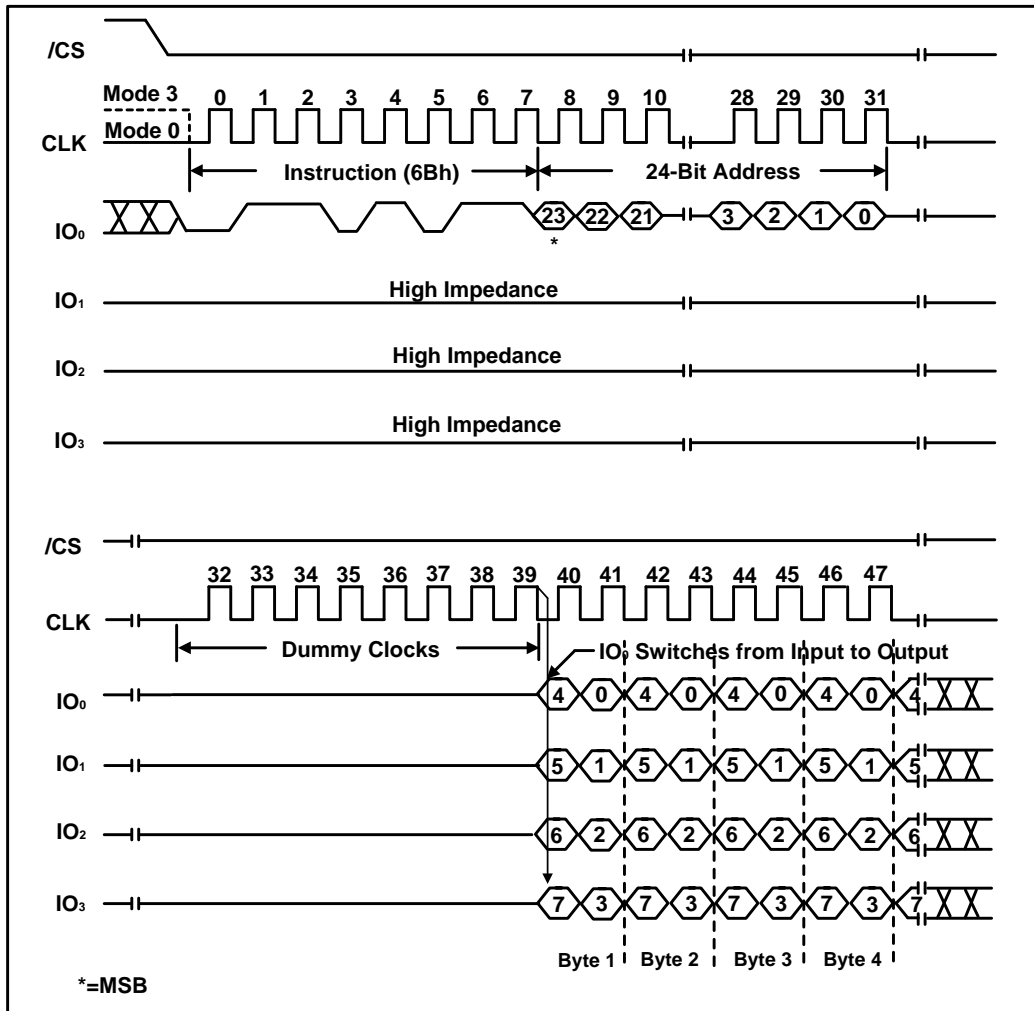


Figure 15. Fast Read Quad Output instruction (SPI Mode)

**11.2.16 Fast Read Dual I/O (BBh)**

The Fast Read Dual I/O (BBh) instruction allows for improved random access while maintaining two IO pins, IO<sub>0</sub> and IO<sub>1</sub>. It is similar to the Fast Read Output (0Bh) instruction but with the capability to input the Address bits (A23-0) two bits and output data two bits per clock. This reduced instruction overhead may allow for code execution (XIP) directly from the Dual SPI in some applications.

**Fast Read Dual I/O with “Continuous Read Mode”**

The Fast Read Dual I/O instruction can further reduce instruction overhead through setting the Mode bits (M7-0) after the input Address bits (A23-0), as shown in figure 16a. The upper nibble of the Mode (M7-4) controls the length of the next Fast Read Dual I/O instruction through the instruction or exclusion of the first byte instruction code. The lower nibble bits of the Mode (M3-0) are don't care (“X”), However, the IO pins should be high-impedance prior to the falling edge of the first data out clock.

If the Mode bits (M7-0) equal “Ax” hex, then the next Fast Dual I/O instruction (after /CS is raised and then lowered) does not require the BBh instruction code, as shown in figure 16b. This reduces the instruction sequence by eight clocks and allows the address to be immediately entered after /CS is asserted low. If Mode bits (M7-0) are any value other “Ax” hex, the next instruction (after /CS is raised and then lowered) requires the first byte instruction code, thus returning to normal operation. Reset instruction(99h) can be used to reset Mode Bits (M7-0) before issuing normal instructions (See 11.2.45 for detailed descriptions).

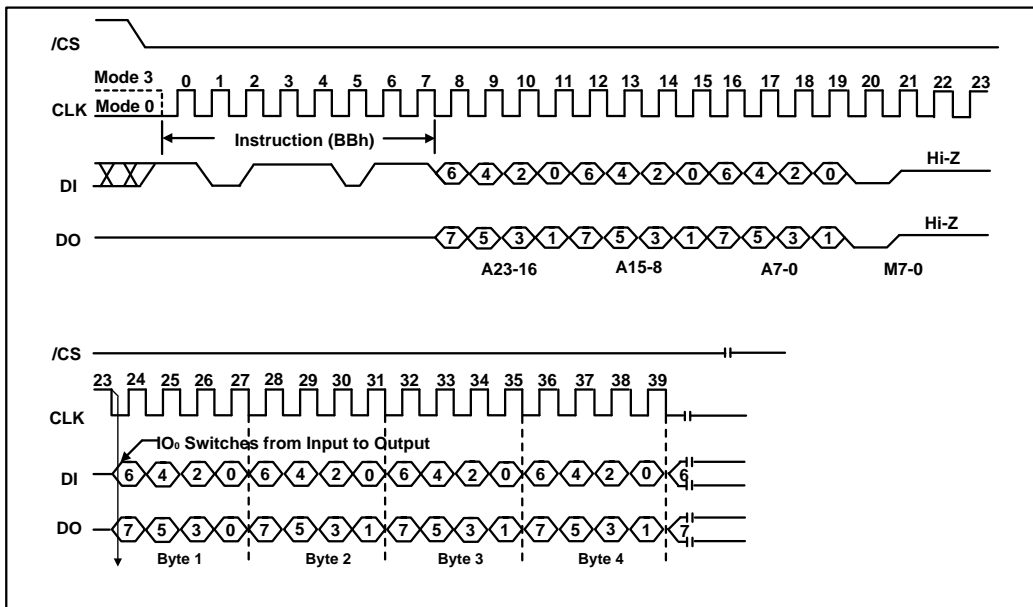


Figure 16a. Fast Read Dual Input/Output Instruction Sequence Diagram (initial instruction or previous M7-0 ≠ Axh)

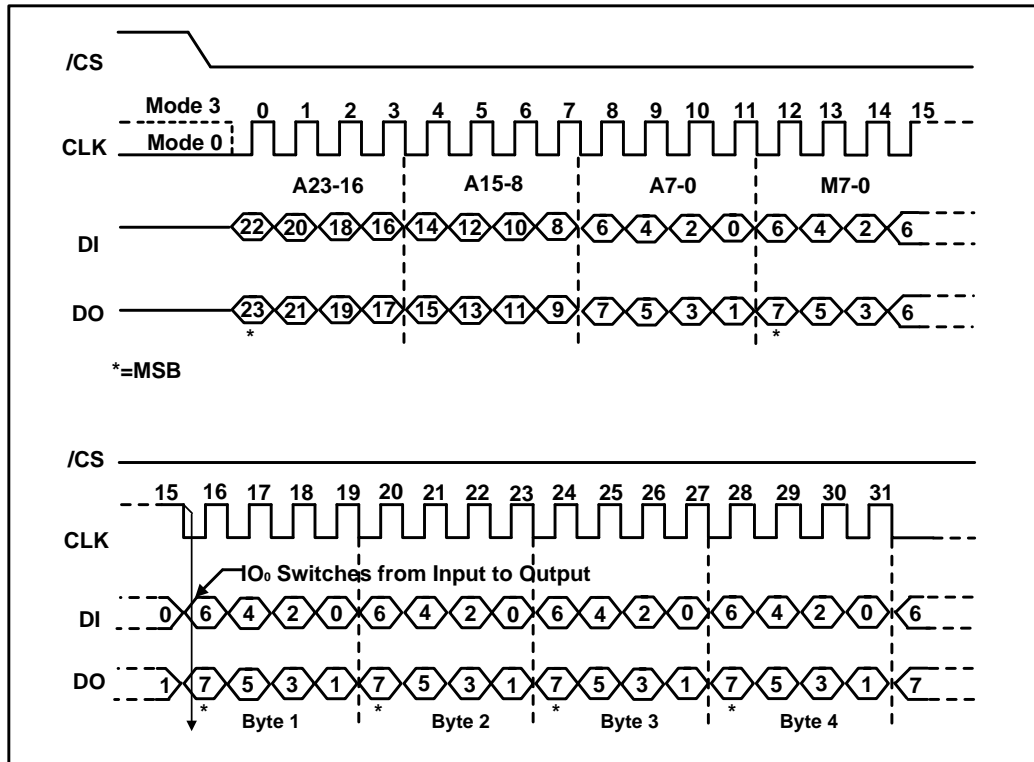


Figure 16b. Fast Read Dual Input/Output Instruction Sequence Diagram (previous M7-0= Axh)

**11.2.17 Fast Read Quad I/O (EBh)**

The Fast Read Quad I/O (EBh) instruction is similar to the Fast Read Dual I/O (BBh) instruction except that address and data bits are input and output through four pins IO<sub>0</sub>, IO<sub>1</sub>, IO<sub>2</sub>, and IO<sub>3</sub> and four Dummy clock are required prior to the data output. The Quad I/O dramatically reduces instruction overhead allowing faster random access for code executing (XIP) directly from the Quad SPI. The Quad Enable bit (QE) of Status Register-2 must be set to enable the Fast read Quad I/O Instruction.

**Fast Read Quad I/O with “Continuous Read Mode”**

The Fast Read Quad I/O instruction can further reduce instruction overhead through setting the Mode bits (M7-0) after the input Address bits (A23-0), as shown in figure 17a. The upper nibble of the Mode (M7-4) controls the length of the next Fast Read Quad I/O instruction through the instruction or exclusion of the first byte instruction code. The lower nibble bits of the Mode (M3-0) are don't care (“X”). However, the IO pins should be high-impedance prior to the falling edge of the first data out clock.

If the Mode bits (M7-0) equal “Ax” hex, then the next Fast Read Quad I/O instruction (after /CS is raised and then lowered) does not require the EBh instruction code, as shown in figure 17b. This reduces the instruction sequence by eight clocks allows the address to be immediately entered after /CS is asserted low. If the Mode bits (M7-0) are any value other than “Ax” hex, the next instruction (after /CS is raised and then lowered) requires the first byte instruction code, thus retuning normal operation. Reset instruction (99h) can be used to reset Mode Bits (M7-0) before issuing normal instructions (See 11.2.45 for detailed descriptions.)

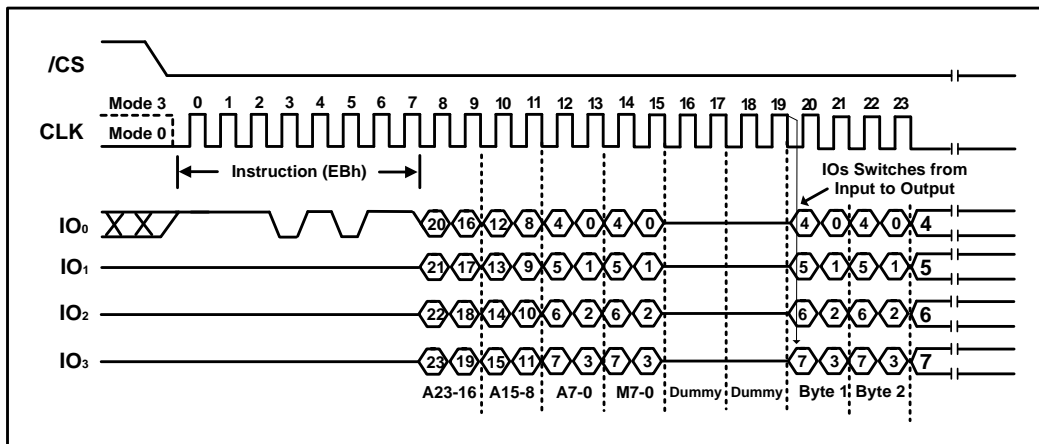


Figure 17a. Fast Read Quad I/O Instruction Sequence Diagram  
(initial instruction or previous M7-0 ≠ Axh, SPI mode)

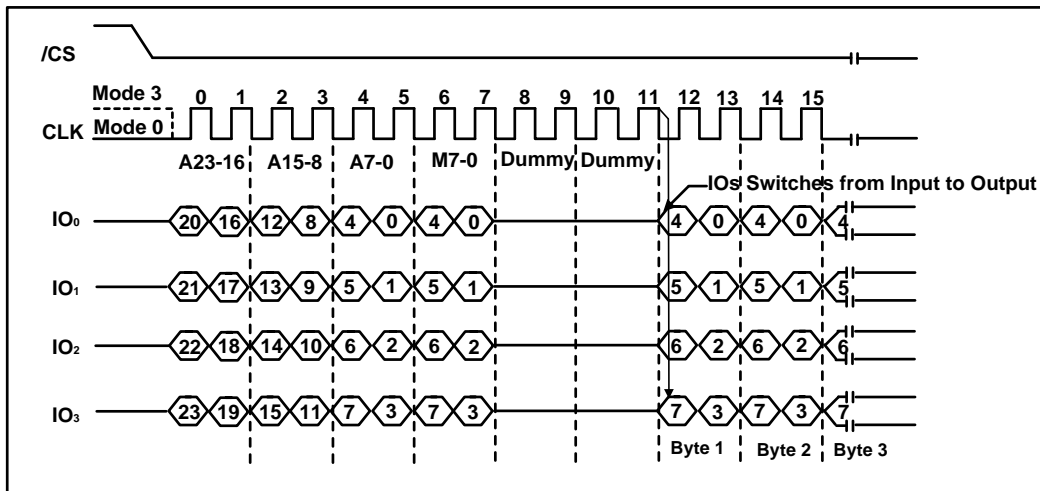


Figure 17b. Fast Read Quad I/O Instruction Sequence Diagram (previous M7-0 = Axh, SPI mode)

#### Fast Read Quad I/O with “8/16/32/64-Byte Wrap Around” in Standard SPI mode

The Fast Read Quad I/O instruction can also be used to access specific portion within a page by issuing a “Set Burst with Wrap” (77h) command prior to EBh. The “Set Burst with Wrap” (77h) command can either enable or disable the “Wrap Around” feature for the following EBh commands. When “Wrap Around” is enabled, the data being accessed can be limited to an 8, 16, 32 or 64-byte section of a 256-byte page. The output data starts at the initial address specified in the instruction, once it reaches the ending boundary of the 8/16/32/64-byte section, the output will wrap around to the beginning boundary automatically until /CS is pulled high to terminate the command.

The Burst with Wrap feature allows applications that use cache to quickly fetch a critical address and then fill the cache afterwards within a fixed length (8/16/32/64-byte) of data without issuing multiple read commands.

The “Set Burst with Wrap” instruction allows three “Wrap Bits”, W6-4 to be set. The W4 bit is used to enable or disable the “Wrap Around” operation while W6-5 are used to specify the length of the wrap around section within a page. [See 11.2.41 for detail descriptions.](#)

#### Fast Read Quad I/O (EBh) in QPI mode

The Fast Read Quad I/O instruction is also supported in QPI mode, as shown in Figure 17c. When QPI mode is enabled, the number of dummy clocks is configured by the “Set Read Parameters (C0h)” instruction to accommodate a wide range applications with different needs for either maximum Fast Read frequency or minimum data access latency. Depending on the Read Parameter Bits P [4] setting, the number of dummy clocks can be configured as either 4 or 6. The default number of dummy clocks upon power up or after a Reset (99h) instruction is 4. In QPI mode, the “Continuous Read Mode” bit M7-0 are also considered as dummy clocks. In the default setting, the data output will follow the Continuous Read Mode bits immediately.

“Continuous Read Mode” feature is also available in QPI mode for Fast Read Quad I/O instruction. Please refer to the description on previous pages.

“Wrap Around feature is not available in QPI mode for Fast Read Quad I/O instruction. To perform a read operation with fixed data length wrap around in QPI mode, a “Burst Read with Wrap” (0Ch) instruction must be used. Please refer to the 11.2.43 for details.

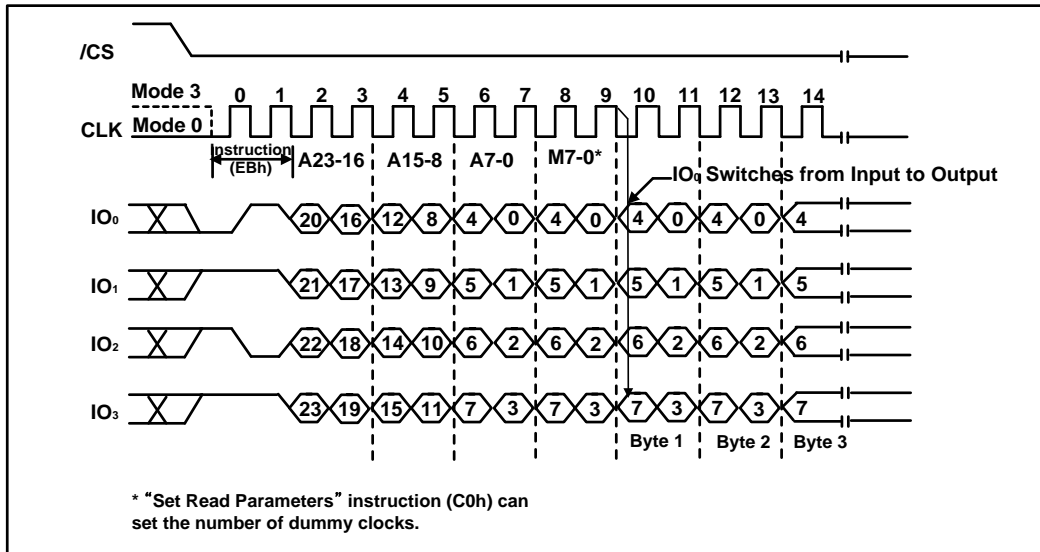


Figure 17c. Fast Read Quad I/O Instruction Sequence Diagram  
(initial instruction or previous M7-0 = Axh, QPI mode)



**11.2.18 Page Program (02h)**

The Page Program instruction allows from one byte to 256 bytes (a page) of data to be programmed at previously erased (FFh) memory locations. A Write Enable instruction must be executed before the device will accept the Page Program Instruction (Status Register bit, WEL= 1). The instruction is initiated by driving the /CS pin low and then shifting the instruction code "02h" followed by a 24-bits address (A23-A0) and at least one data byte, into the DI pin. The /CS pin must be held low for the entire length of the instruction while data is being sent to the device. The Page Program instruction sequence is shown in figure 18.

If an entire 256 byte page is to be programmed, the last address byte (the 8 least significant address bits) should be set to 0. If the last address byte is not zero, and the number of clocks exceeds the remaining page length, the addressing will wrap to the beginning of the page. In some cases, less than 256 bytes (a partial page) can be programmed without having any effect on other bytes within the same page. One condition to perform a partial page program is that the number of clocks cannot exceed the remaining page length. If more than 256 bytes are sent to the device the addressing will wrap to the beginning of the page and overwrite previously sent data.

As with the write and erase instructions, the /CS pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Page Program instruction will not be executed. After /CS is driven high, the self-timed Page Program instruction will commence for a time duration of tPP (See AC Characteristics). While the Page Program cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the BUSY bit. The BUSY bit is a 1 during the Page Program cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Page Program cycle has finished and Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Page Program instruction will not be executed if the addressed page is protected by the Block Protect (CMP, SEC, TB, BP2, BP1, and BP0) bits,

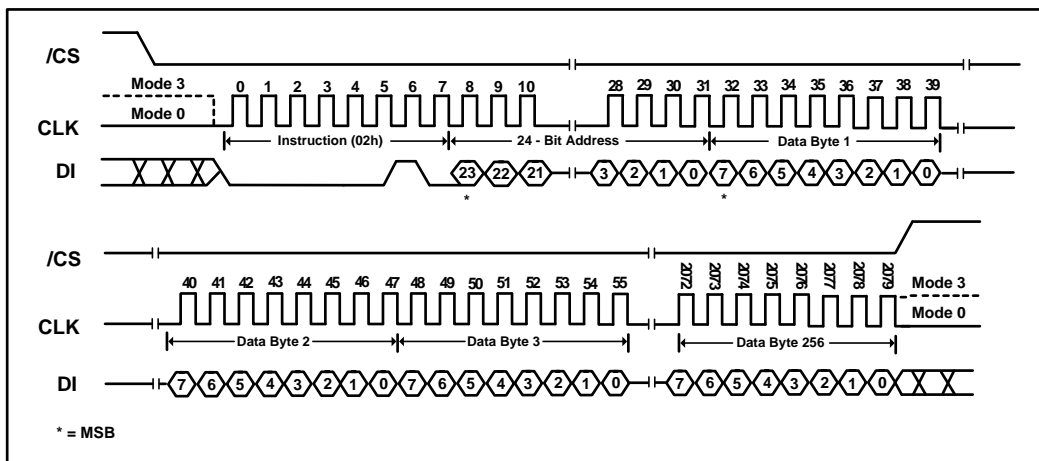


Figure 18a. Page Program Instruction (SPI Mode)

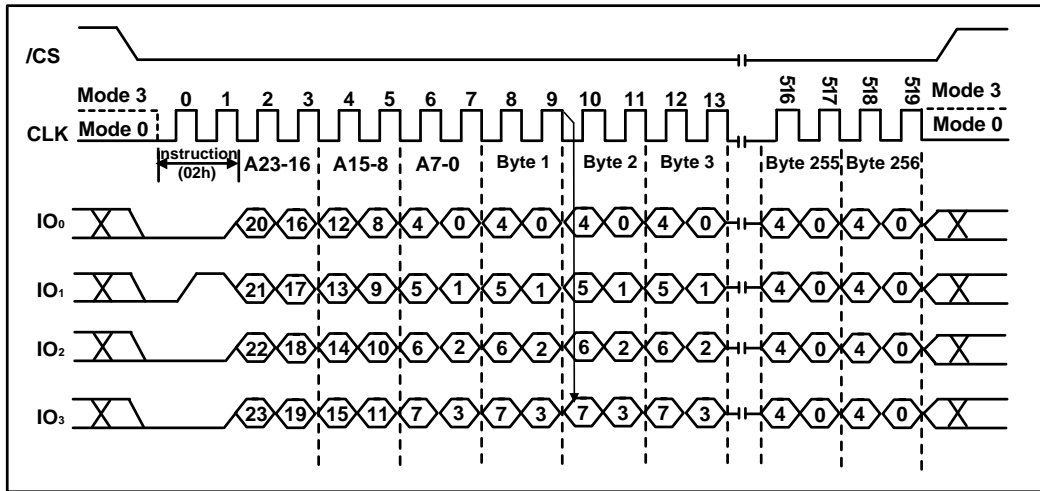


Figure 18b. Page Program Instruction (QPI Mode)

**11.2.19 Quad Data Input Page Program (32h)**

The Quad Data Input Page Program instruction allows up to 256 bytes of data to be programmed at previously erased (FFh) memory locations using four pins: IO<sub>0</sub>, IO<sub>1</sub>, IO<sub>2</sub> and IO<sub>3</sub>. The Quad Data Input Page Program can improve performance for PROM Programmer and applications that have slow clock speed <5MHz. System with faster clock speed will not realize much benefit for the Quad Data Input Program instruction since the inherent page program time is much greater than the time it takes to clock-in the data.

To use Quad Data Input Page Program the Quad Enable in Status Register-2 must be set (QE=1), A Write Enable instruction must be executed before the device will accept the Quad Data Input Page Program instruction (Status Register-1, WEL=1). The instruction is initiated by driving the /CS pin low and then shifting the instruction code “32h” followed by a 24-bit address (A23-A0) and at least one data, into the IO pins. The /CS pin must be held low for the entire length of the instruction while data is being sent to the device. All other functions of Quad Data Input Page Program are identical standard Page Program. The Quad Data Input Page Program instruction sequence is shown in figure 19.

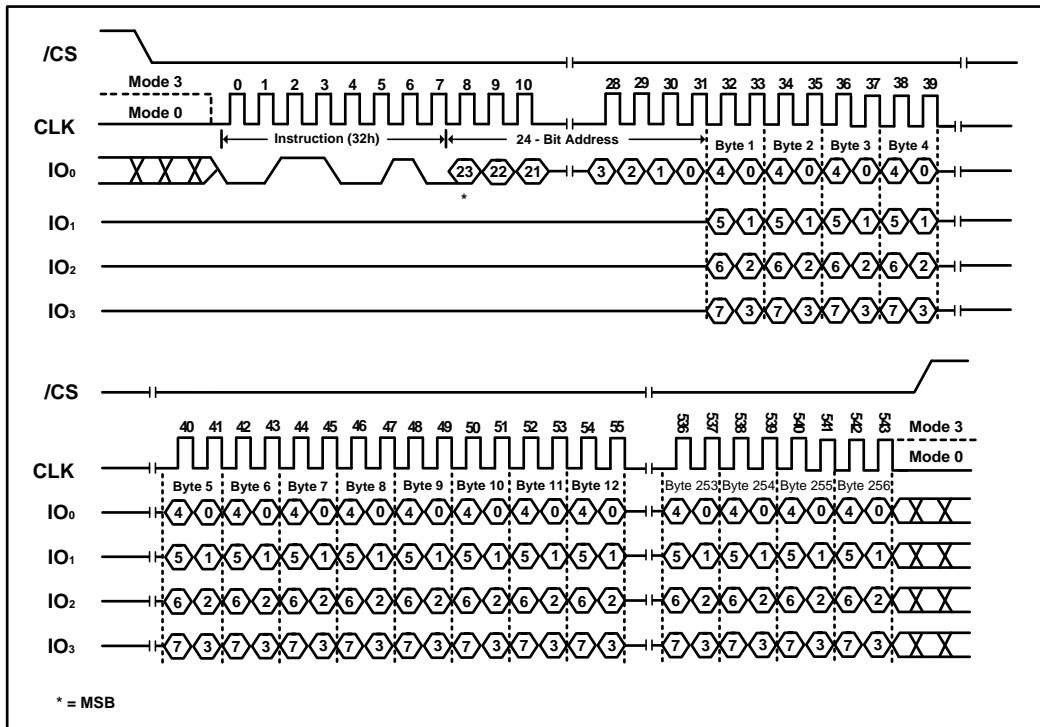


Figure 19. Quad Data Input Page Program Instruction Sequence Diagram

**11.2.20 Quad Page Program (33h)**

The Quad Page Program instruction allows 24-bit address and up to 256 bytes of data to be programmed at previously erased (FFh) memory locations using four pins: IO<sub>0</sub>, IO<sub>1</sub>, IO<sub>2</sub> and IO<sub>3</sub>. The Quad Page Program can improve performance for PROM Programmer and applications that have slow clock speed <5MHz. System with faster clock speed will not realize much benefit for the Quad Page Program instruction since the inherent page program time is much greater than the time it takes to clock-in the data.

To use Quad Page Program the Quad Enable in Status Register-2 must be set (QE=1), A Write Enable instruction must be executed before the device will accept the Quad Page Program instruction (Status Register-1, WEL=1). The instruction is initiated by driving the /CS pin low then shifting the instruction code "33h" followed by a 24-bit address (A23-A0) and at least one data, into the IO pins. The /CS pin must be held low for the entire length of the instruction while data is being sent to the device. All other functions of Quad Page Program are identical standard Page Program. The Quad Page Program instruction sequence is shown in figure 20.

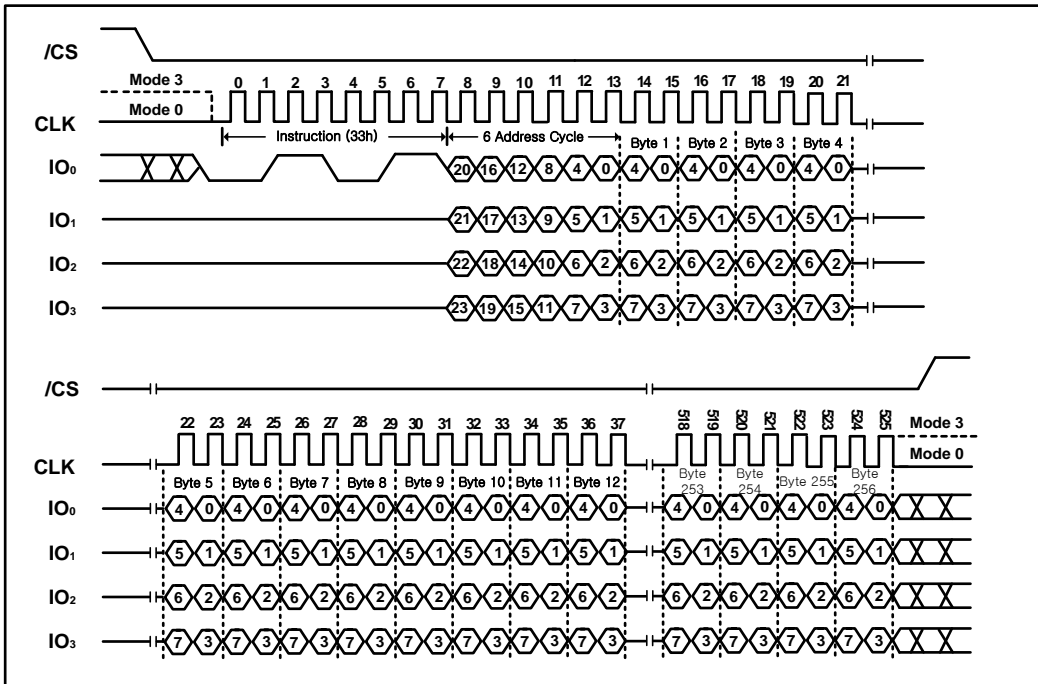


Figure 20a. Quad Page Program Instruction Sequence Diagram

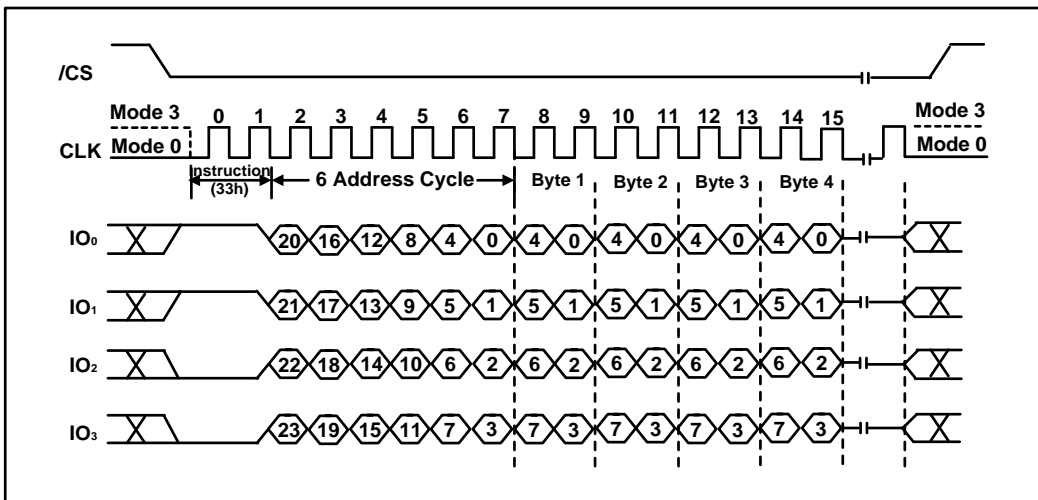


Figure 20b. Quad Page Program Instruction Sequence Diagram (QPI mode)

**11.2.21 Sector Erase (20h)**

The sector Erase instruction sets all memory within a specified sector (4K-bytes) to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Sector Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the /CS pin low and shifting the instruction code “20h” followed a 24-bit sector address (A23-A0). The Sector Erase instruction sequence is shown in figure 21.

The /CS pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Sector Erase instruction will not be executed. After /CS is driven high, the self-timed Sector Erase instruction will commence for a time duration of tSE (See AC Characteristics). While the Sector Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the BUSY bit. The BUSY bit is a 1 during the Sector Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Sector Erase cycle has finished the Write Enable Latch (WEL) bit in Status Register is cleared to 0. The Sector Erase instruction will not be executed if the addressed page is protected by the Block Protect (SEC, TB, BP2, BP1, and BP0) bits (see Status Register Memory protection table).

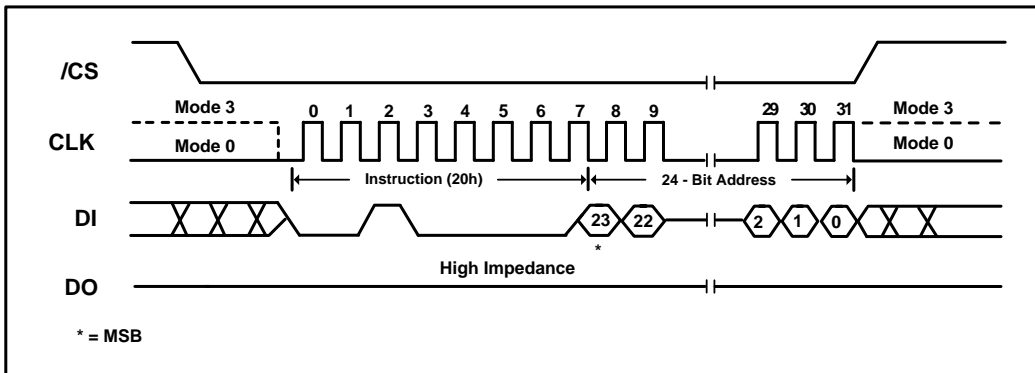


Figure 21a. Sector Erase Instruction (SPI Mode)

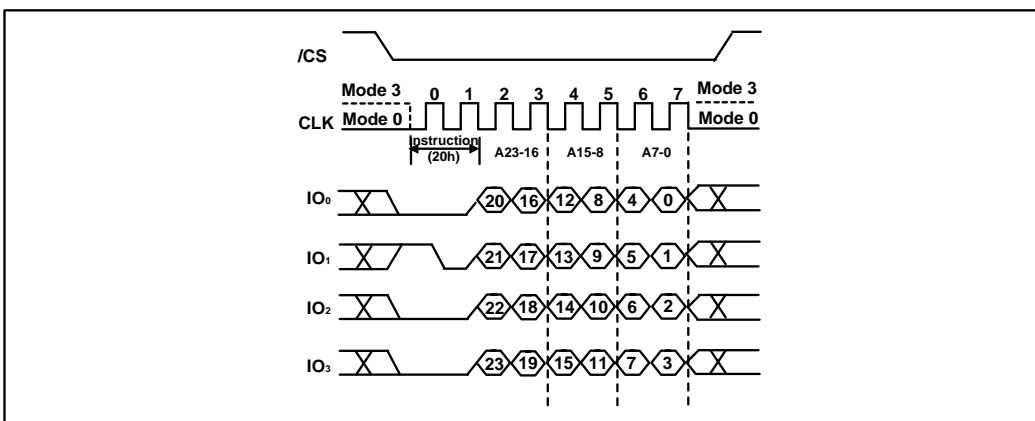


Figure 21b. Sector Erase Instruction (QPI Mode)

**11.2.22 32KB Block Erase (52h)**

The Block Erase instruction sets all memory within a specified block (32k-bytes) to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Block Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the /CS pin low and shifting the instruction code “52h” followed a 24-bit block address (A23-A0). The Block Erase instruction sequence is shown in figure 22.

The /CS pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Block Erase instruction will not be executed. After /CS is driven high, the self-timed Block Erase instruction will commence for a time duration of tBE1 (See AC Characteristics). While the Block Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the BUSY bit. The BUSY bit is a 1 during the Block Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Sector Erase cycle has finished the Write Enable Latch (WEL) bit in Status Register is cleared to 0. The Block Erase instruction will not be executed if the addressed page is protected by the Block Protect (CMP, SEC, TB, BP2, BP1, and BP0) bits (see Status Register Memory Protection table).

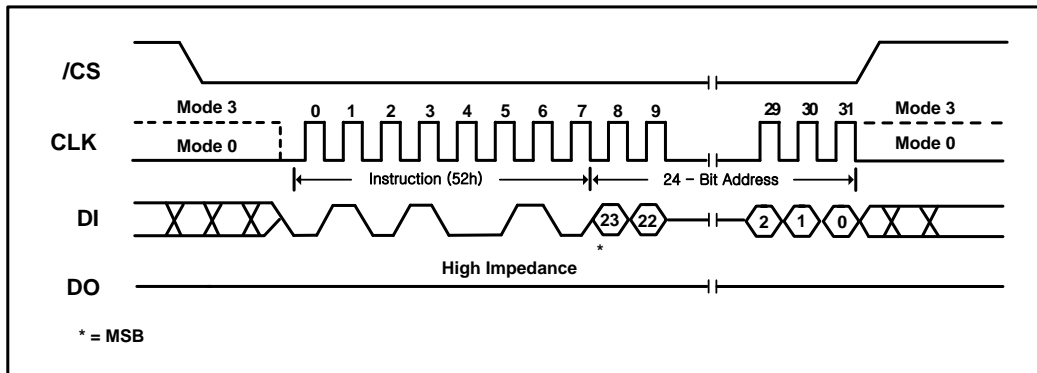


Figure 22a. 32KB Block Erase Instruction (SPI Mode)

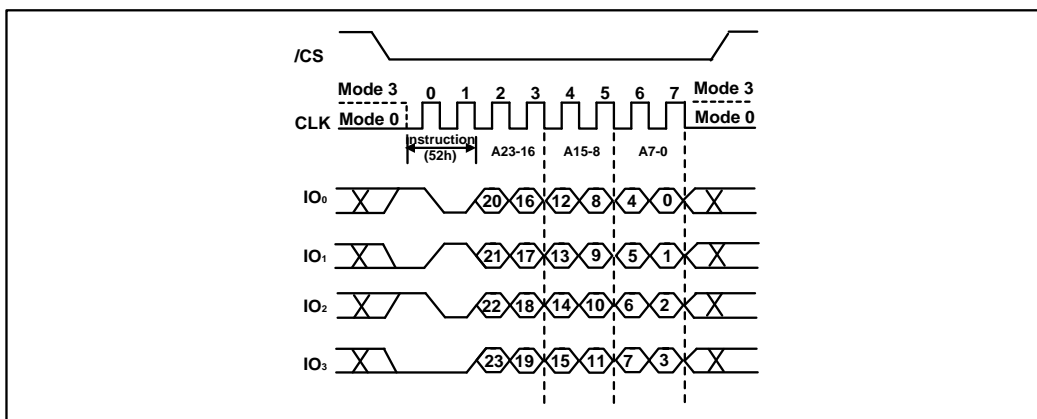


Figure 22b. 32KB Block Erase Instruction (QPI Mode)

**11.2.23 64KB Block Erase (D8h)**

The Block Erase instruction sets all memory within a specified block (64k-bytes) to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Block Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the /CS pin low and shifting the instruction code “D8h” followed a 24-bit block address (A23-A0). The Block Erase instruction sequence is shown in figure 23.

The /CS pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Block Erase instruction will not be executed. After /CS is driven high, the self-timed Block Erase instruction will commence for a time duration of tBE1 (See AC Characteristics). While the Block Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the BUSY bit. The BUSY bit is a 1 during the Block Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Block Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Block Erase instruction will not be executed if the addressed page is protected by the Block Protect (CMP, SEC, TB, BP2, BP1, and BP0) bits (see Status Register Memory Protection table).

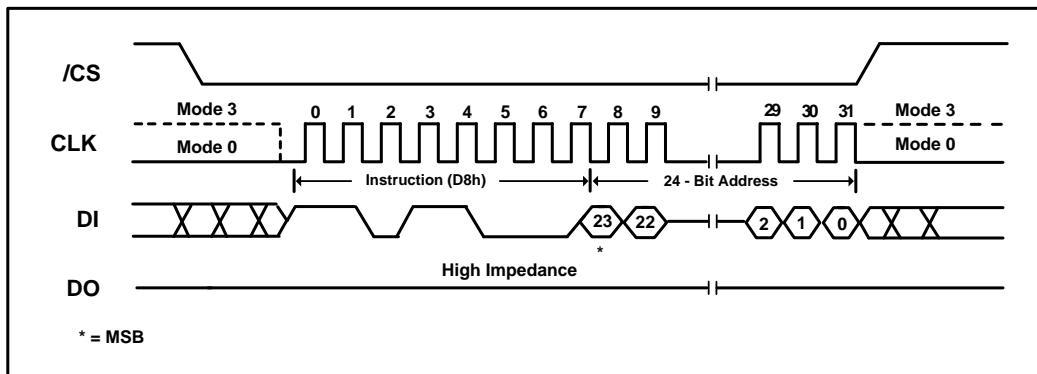


Figure 23a. 64KB Block Erase Instruction (SPI Mode)

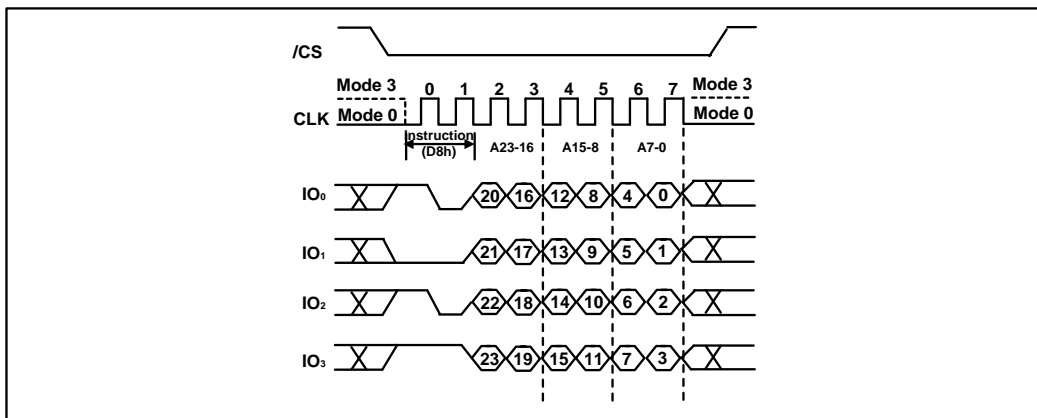


Figure 23b. 64KB Block Erase Instruction (QPI Mode)

### 11.2.24 Chip Erase (C7h / 60h)

The Chip Erase instruction sets all memory within the device to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Chip Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the /CS pin low and shifting the instruction code “C7h” or “60h”. The Chip Erase instruction sequence is shown in figure 24.

The /CS pin must be driven high after the eighth bit has been latched. If this is not done the Chip Erase instruction will not be executed. After /CS is driven high, the self-timed Chip Erase instruction will commence for a time duration of tCE (See AC Characteristics). While the Chip Erase cycle is in progress, the Read Status Register instruction may still be accessed to check the status of the BUSY bit. The BUSY bit is a 1 during the Chip Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Chip Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Chip Erase instruction will not be executed if any page is protected by the Block Protect (CMP, SEC, TB, BP2, BP1, and BP0) bits (see Status Register Memory Protection table).

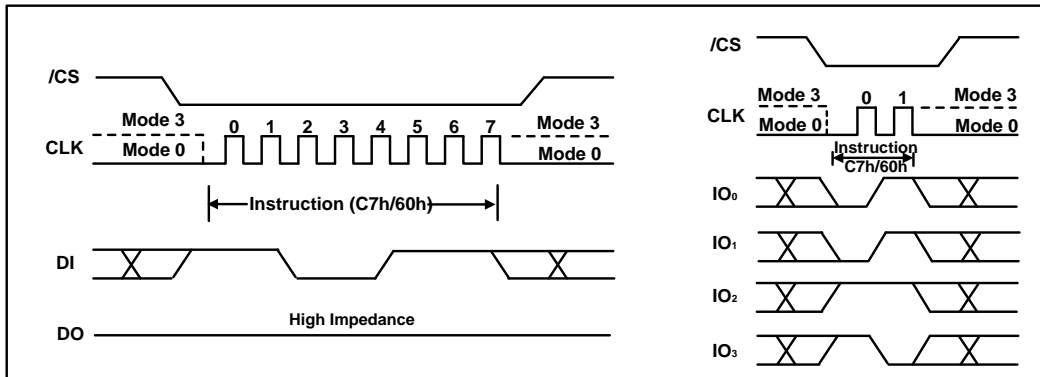


Figure 24. Chip Erase Instruction for SPI Mode (left) or QPI Mode (right)



**11.2.25 Erase / Program Suspend (75h)**

The Erase/Program Suspend instruction “75h”, allows the system to interrupt a Sector or Block Erase operation or a Page Program operation and then read from or program/erase data to, any other sectors or blocks. The Erase/Program Suspend instruction sequence is shown in figure 25.

The Write Status Register-1(01h), Write Status Register-2 (31h) instruction and Erase instructions (20h, 52h, D8h, C7h, 60h) are not allowed during Erase Suspend. Erase Suspend is valid only during the Sector or Block erase operation. If written during the Chip Erase operation, the Erase Suspend instruction is ignored. The Write Status Register-1(01h), Write Status Register-2 (31h) instruction and Program instructions (02h, 32h, 33h) are not allowed during Program Suspend. Program Suspend is valid only during the Page Program, Quad Data Input Page Program or Quad Page Program operation.

The Erase/ Program Suspend instruction “75h” will be accepted by the device only if the SUS bit in the Status Register equals to 0 and the BUSY bit equals to 1 while a Sector or Block Erase or a Page Program operation is on-going. If the SUS bit equals to 1 or the BUSY bit equals to 0, the Suspend instruction will be ignored by the device. A maximum of time of “tSUS” (See AC Characteristics) is required to suspend the erase or program operation. The BUSY bit in the Status Register will be cleared from 1 to 0 within “tSUS” and the SUS bit in the Status Register will be set from 0 to 1 immediately after Erase/Program Suspend. For a previously resumed Erase/Program operation, it is also required that the Suspend instruction “75h” is not issued earlier than a minimum of time of “tSUS” following the preceding Resume instruction “7Ah”.

Unexpected power off or Reset Instruction (99h) during the Erase/Program suspend state will reset the device and release the suspend state. SUS bit in the Status Register will also reset to 0. The data within the page, sector or block that was being suspended may become corrupted. It is recommended for the user to implement system design techniques against the accidental power interruption and preserve data integrity during erase/program suspend state.

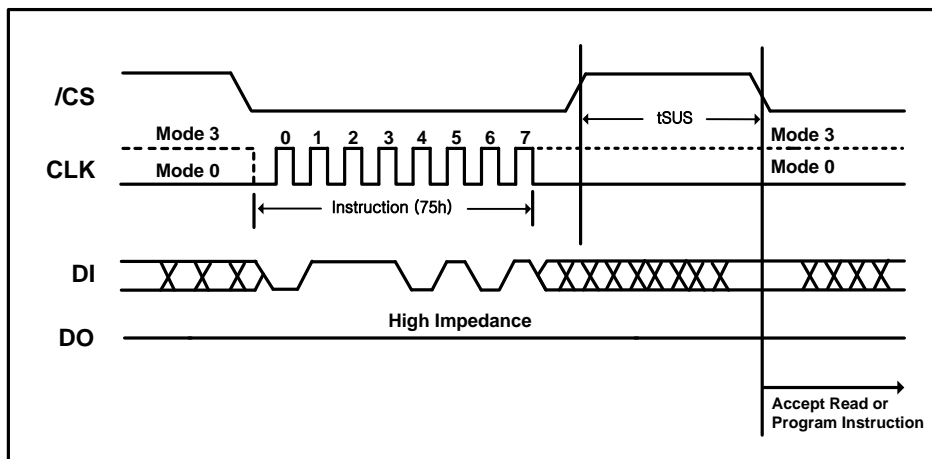


Figure 25a. Erase Suspend instruction (SPI Mode)

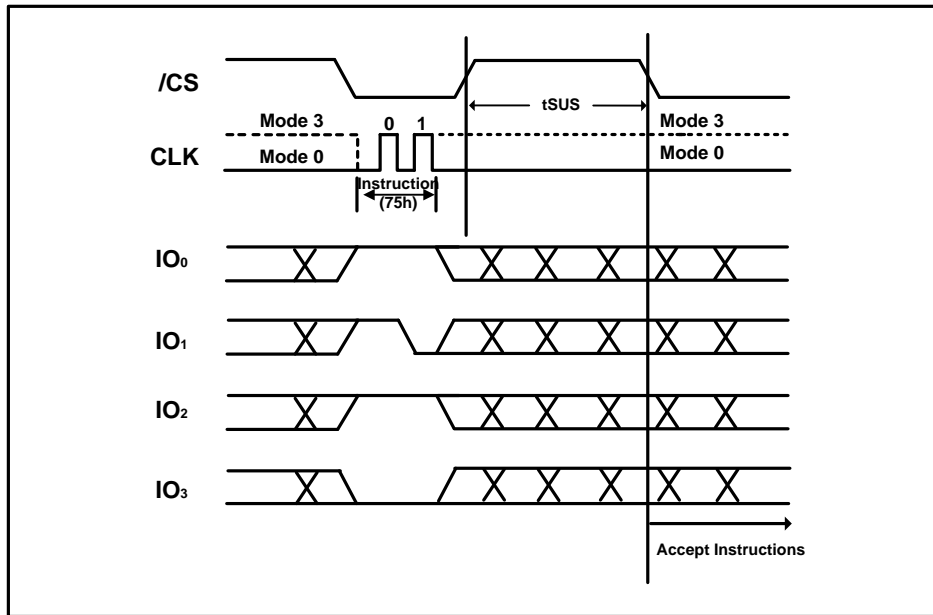


Figure 25b. Erase Suspend instruction (QPI Mode)

### 11.2.26 Erase / Program Resume (7Ah)

The Erase/Program Resume instruction “7Ah” must be written to resume the Sector or Block Erase operation or the Page Program operation after an Erase/Program Suspend. The Resume instruction “7Ah” will be accepted by the device only if the SUS bit in the Status Register equals to 1 and the BUSY bit equals to 0. After issued the SUS bit will be cleared from 1 to 0 immediately, the BUSY bit will be set from 0 to 1 within 200ns and the Sector or Block will complete the erase operation or the page will complete the program operation. If the SUS bit equals to 0 or the BUSY bit equals to 1, the Resume instruction “7Ah” will be ignored by the device. The Erase/Program Resume instruction sequence is shown in figure 26a & 26b.

Resume instruction is ignored if the previous Erase/Program Suspend operation was interrupted by unexpected power off or Reset instruction (99h). It is also required that a subsequent Erase/Program Suspend instruction not to be issued within a minimum of time of “tSUS” following a previous Resume instruction.

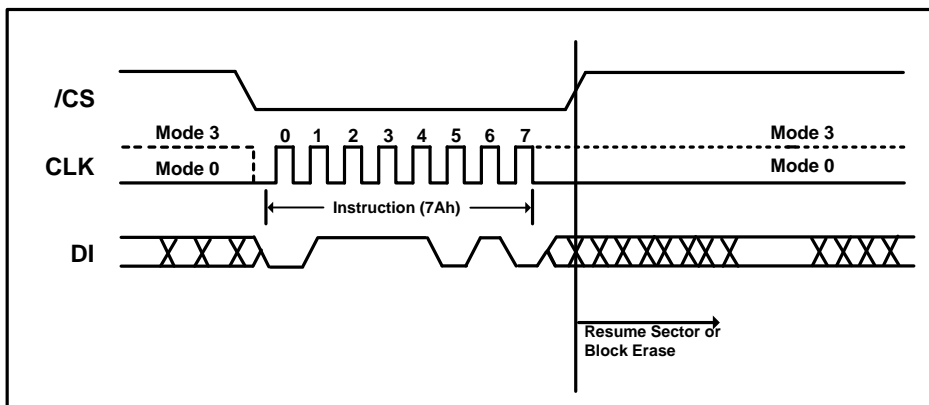


Figure 26a. Erase / Program Resume instruction (SPI Mode)

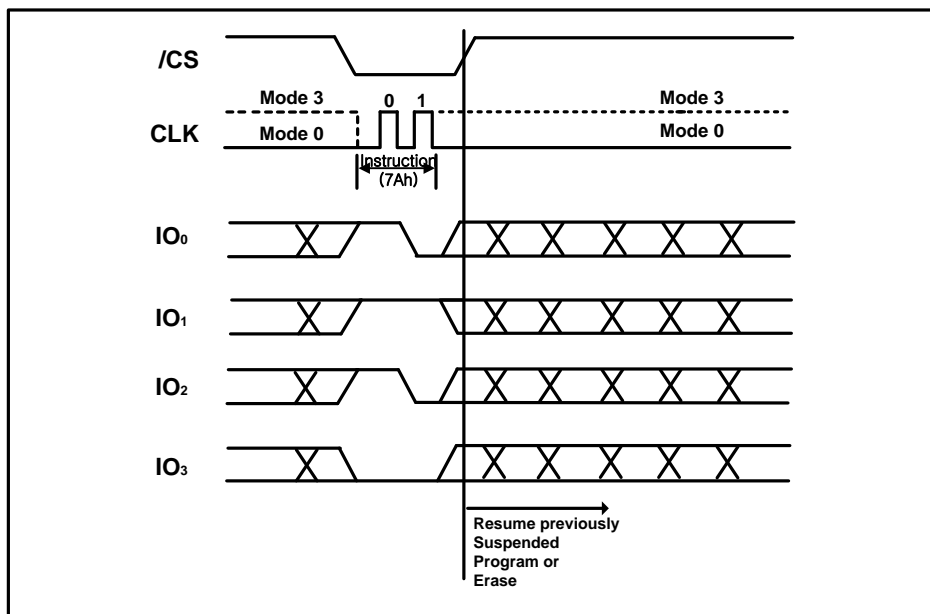


Figure 26b. Erase / Program Resume instruction (QPI Mode)

**11.2.27 Power-down (B9h)**

Although the standby current during normal operation is relatively low, standby current can be further reduced with the Power-down instruction. The lower power consumption makes the Power-down instruction especially useful for battery powered applications (See ICC1 and ICC2 in AC Characteristics). The instruction is initiated by driving the /CS pin low and shifting the instruction code “B9h” as shown in figure 27a & 27b.

The /CS pin must be driven high after the eighth bit has been latched, If this is not done the Power-down instruction will not be executed. After /CS is driven high, the Power-down state will be entered within the time duration of tDP (See AC Characteristics). While in the Release power-down /Device ID instruction, which restores the device to normal operation, will be recognized. All other instructions are ignored. This includes the Read Status Register instruction, which is always available during normal operation. Ignoring all but one instruction makes the Power Down state a useful condition for securing maximum write protection. The device always powers-up in the normal operation with the standby current of ICC1.

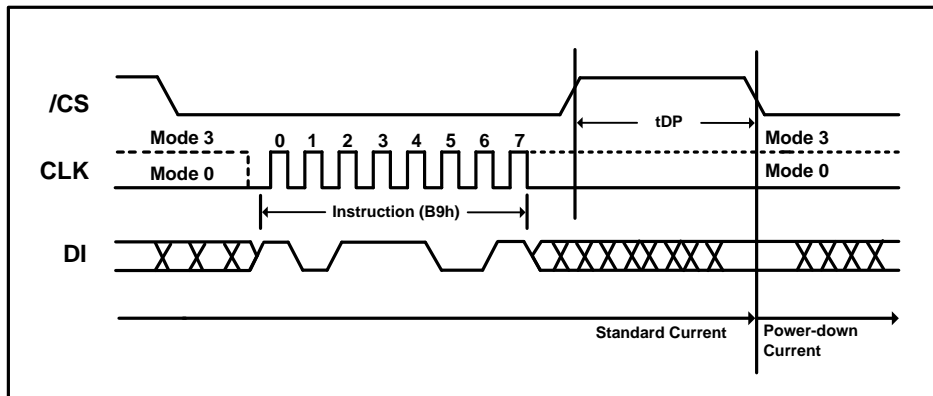


Figure 27a. Deep Power-down Instruction (SPI Mode)

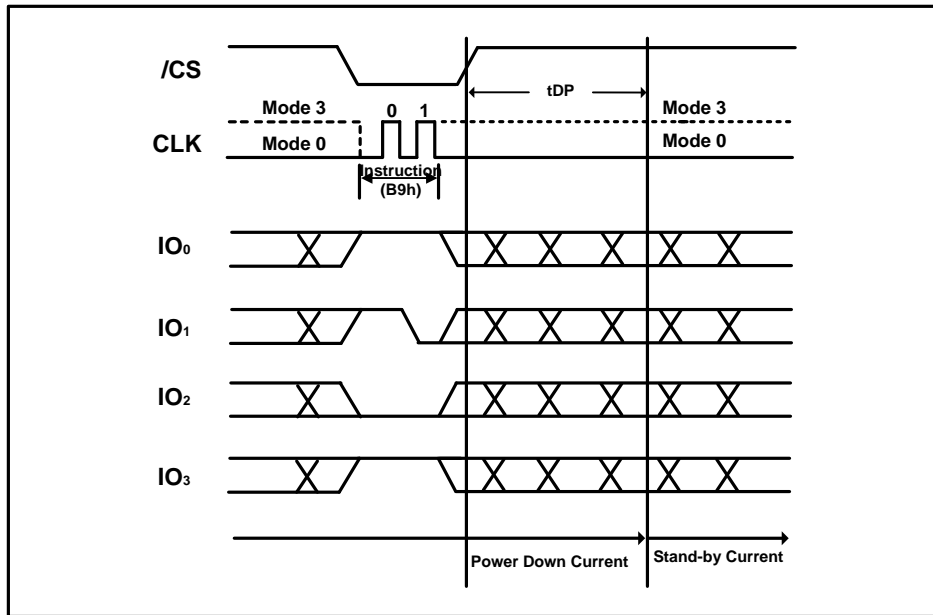


Figure 27b. Deep Power-down Instruction (QPI Mode)

### 11.2.28 Release Power-down / Device ID (ABh)

The Release from Power-down / Device ID instruction is a multi-purpose instruction. It can be used to release the device from the power-down state or obtain the device electronic identification (ID) number.

To release the device from the power-down state, the instruction is issued by driving the /CS pin low, shifting the instruction code “ABh” and driving /CS high as shown in figure 28a & 28b. Release from power-down will take the time duration of tRES1 (See AC Characteristics) before the device will resume normal operation and other instructions are accepted. The /CS pin must remain high during the tRES1 time duration.

When used only to obtain the Device ID while not in the power-down state, instruction is initiated by driving the /CS pin low and shifting the instruction code “ABh” followed by 3-dummy bytes. The Device ID bits are then shifted on the falling edge of CLK with most significant bit (MSB) first as shown in figure 28. The Device ID value for the FM25M32A is listed in Manufacturer and Device Identification table. The Device ID can be read continuously. The instruction is completed by driving /CS high.

When used to release the device from the power-down state and obtain the Device ID, the instruction is the same as previously described, and shown in figure 28c & 28d, except that after /CS is driven high it must remain high for a time duration of tRES2 (See AC Characteristics). After this time duration the device will resume normal operation and other instructions will be accepted. If the Release from power-down /Device ID instruction is issued while an Erase, Program or Write cycle is in process (when BUSY equals 1) the instruction is ignored and will not have any effects on the current cycle.

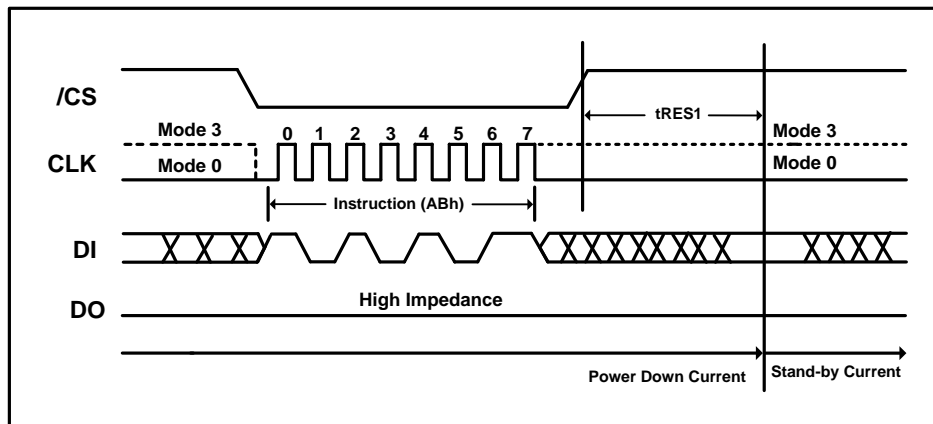


Figure 28a. Release power-down Instruction (SPI Mode)

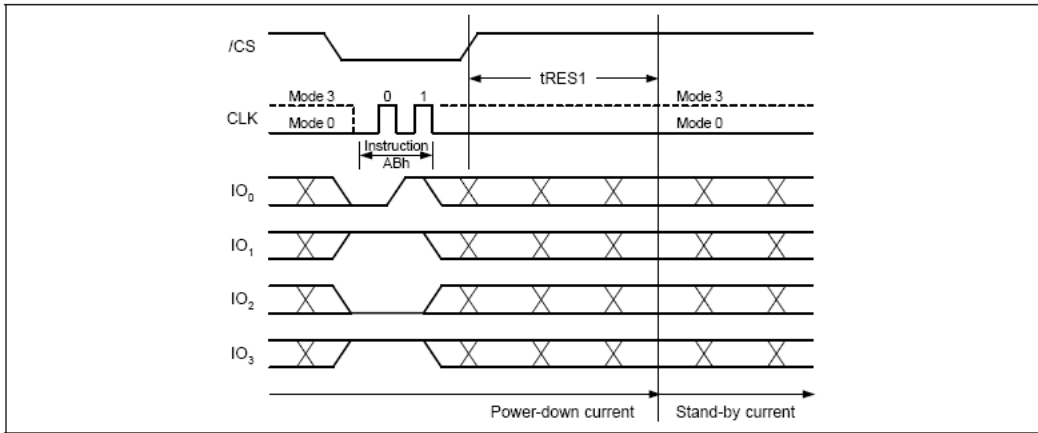


Figure 28b. Release power-down Instruction (QPI Mode)

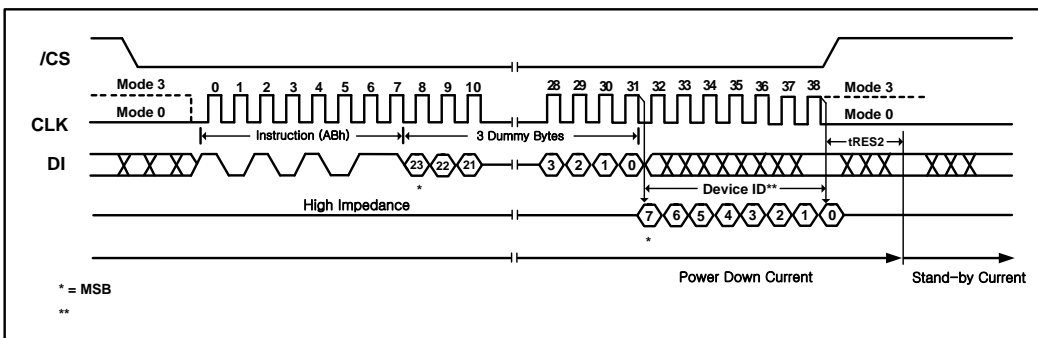


Figure 28c. Release power-down / Device ID Instruction (SPI Mode)

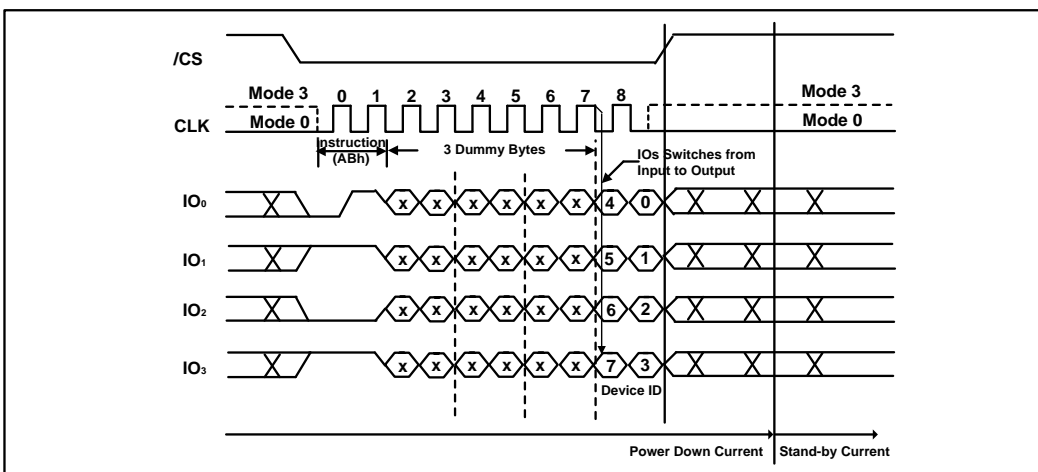


Figure 28d. Release power-down / Device ID Instruction (QPI Mode)

**11.2.29 Read Manufacturer/ Device ID (90h)**

The Read Manufacturer/ Device ID instruction is an alternative to the Release from Power-down / Device ID instruction that provides both the JEDEC assigned manufacturer ID and the specific device ID.

The Read Manufacturer/ Device ID instruction is very similar to the Release from Power-down / Device ID instruction. The instruction is initiated by driving the /CS pin low and shifting the instruction code "90h" followed by a 24-bit address (A23-A0) of 000000h. After which, the Manufacturer ID for FIDELIX SEMICONDUCTOR (F8h) and the Device ID are shifted out on the falling edge of CLK with most significant bit(MSB) first as shown in figure 29a & 29b. The Device ID value for the FM25M32A is listed in Manufacturer and Device Identification table. If the 24-bit address is initially set to 000001h the Device ID will be read first and then followed by the Manufacturer ID. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving /CS high.

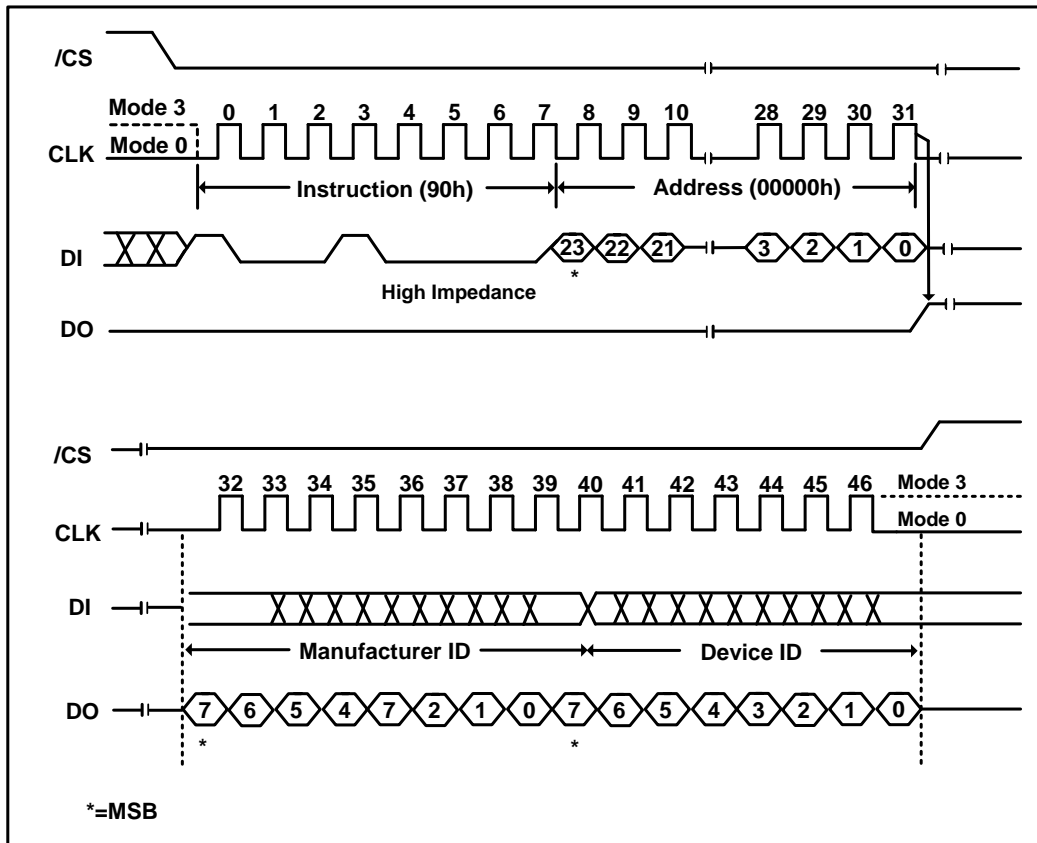


Figure 29a. Read Manufacturer/ Device ID instruction (SPI Mode)



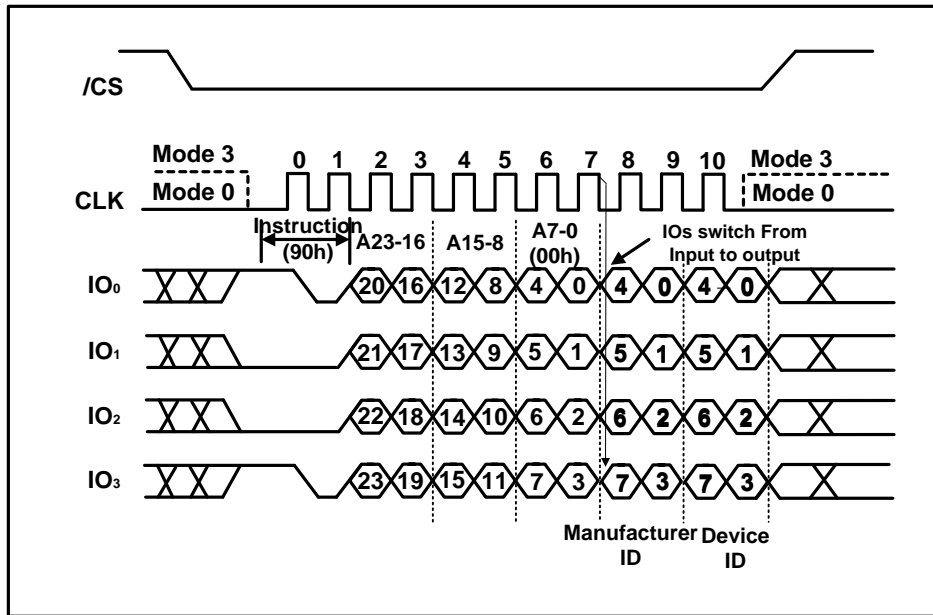


Figure 29b. Read Manufacturer/ Device ID instruction (QPI Mode)

### 11.2.30 Read Manufacturer/ Device ID Dual I/O (92h)

The Read Manufacturer/Device ID Dual I/O instruction is an alternative to the Read Device ID instruction that provides both the JEDEC assigned manufacturer ID and the specific device ID.

The Read Manufacturer/Device ID Dual I/O instruction is similar to the Fast Read Dual I/O instruction. The instruction is initiated by driving the /CS pin low and shifting the instruction code "92h" followed by a 24-bit address (A23-A0) of 000000h. After which, the Manufacturer ID for FIDELIX SEMICONDUCTOR (F8h) and the Device ID are shifted out on the falling edge of CLK with most significant bit(MSB) first as shown in figure 30. The Device ID value for the FM25M32A is listed in Manufacturer and Device Identification table. If the 24-bit address is initially set to 000001h the Device ID will be read first and then followed by the Manufacturer ID. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving /CS high.

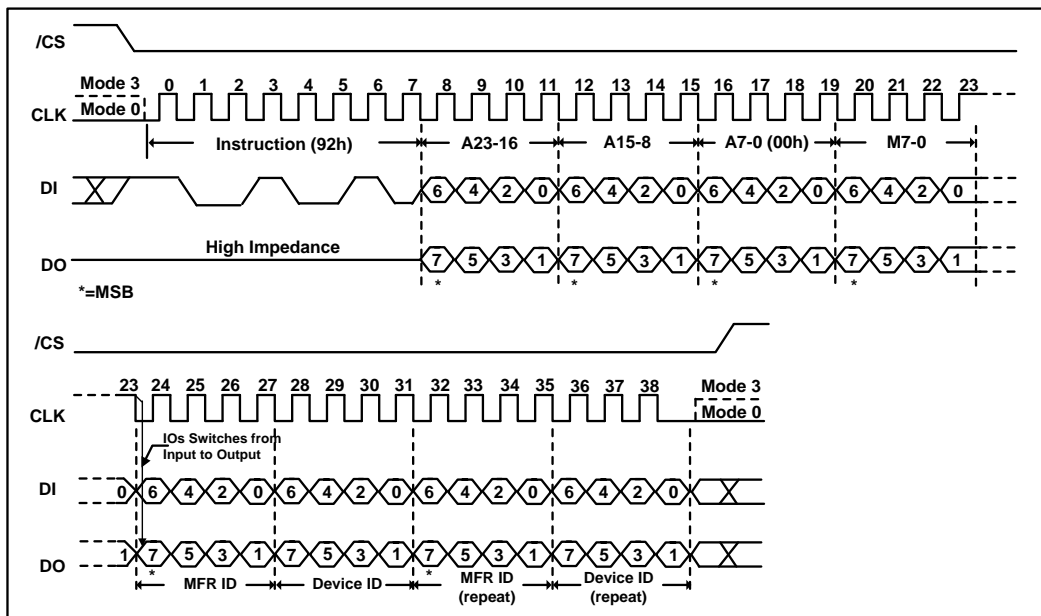


Figure 30. Read Dual Manufacturer/ Device ID Dual I/O instruction (SPI Mode)

### 11.2.31 Read Manufacturer/ Device ID Quad I/O (94h)

The Read Manufacturer/Device ID Quad I/O instruction is an alternative to the Read Device ID instruction that provides both the JEDEC assigned manufacturer ID and the specific device ID.

The Read Manufacturer/Device ID Quad I/O instruction is similar to the Fast Read Quad I/O instruction. The instruction is initiated by driving the /CS pin low and shifting the instruction code “94h” followed by a 24-bit address (A23-A0) of 000000h. After which, the Manufacturer ID for FIDELIX SEMICONDUCTOR (F8h) and the Device ID are shifted out on the falling edge of CLK with most significant bit(MSB) first as shown in figure 31. The Device ID value for the FM25M32A is listed in Manufacturer and Device Identification table. If the 24-bit address is initially set to 000001h the Device ID will be read first and then followed by the Manufacturer ID. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving /CS high.

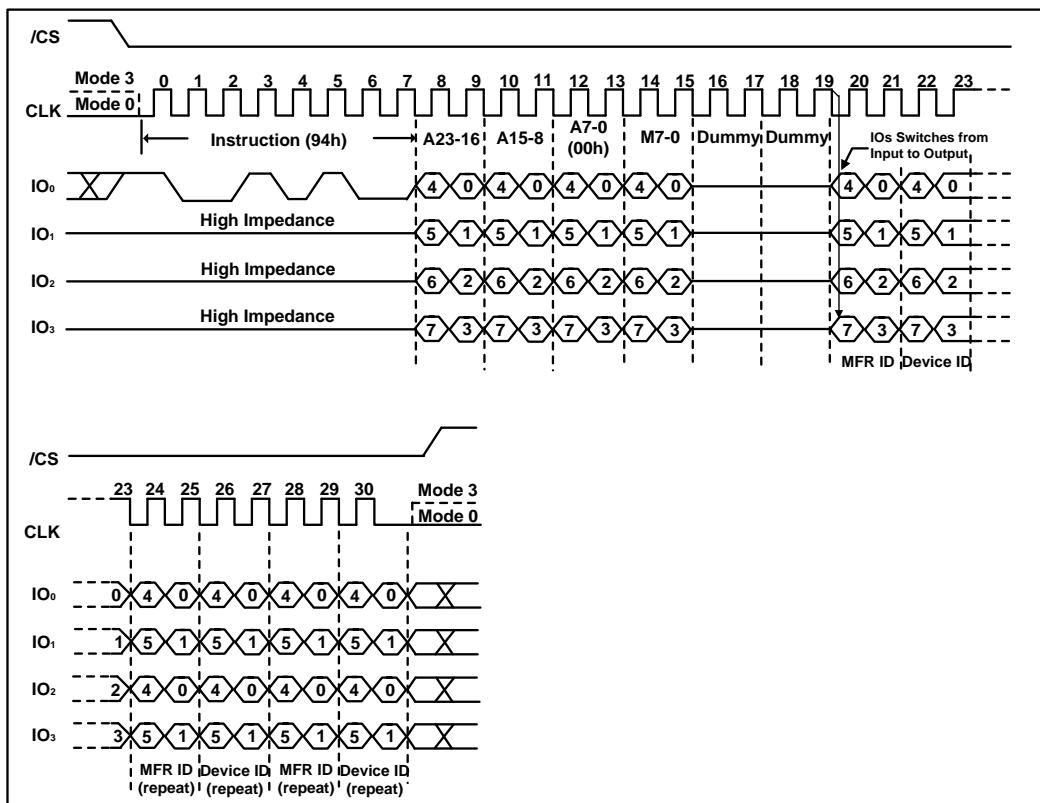


Figure 31. Read Quad Manufacturer/ Device ID instruction (SPI Mode)

**11.2.32 Read JEDEC ID (9Fh)**

For compatibility reasons, the FM25M32A provides several instructions to electronically determine the identity of the device. The Read JEDEC ID instruction is compatible with the JEDEC standard for SPI compatible serial memories that was adopted in 2003. The instruction is initiated by driving the /CS pin low and shifting the instruction code "9Fh". The instruction JEDEC assigned Manufacturer ID byte for FIDELIX SEMICONDUCTOR(F8h) and two Device ID bytes, Memory Type(ID15-ID8) and Capacity (ID7-ID0) are then shifted out on the falling edge of CLK with most significant bit (MSB) first shown in figure.32a & 32b For memory type and capacity values refer to Manufacturer and Device Identification table. The JEDEC ID can be read continuously. The instruction is completed by driving /CS high.

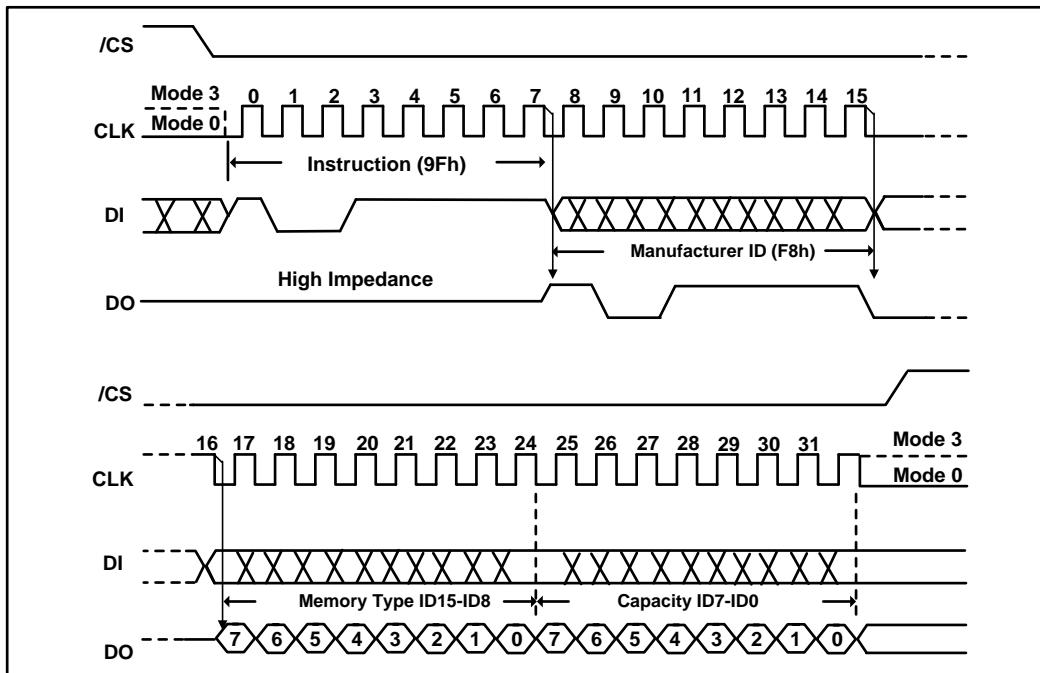


Figure 32a. Read JEDEC ID instruction (SPI Mode)

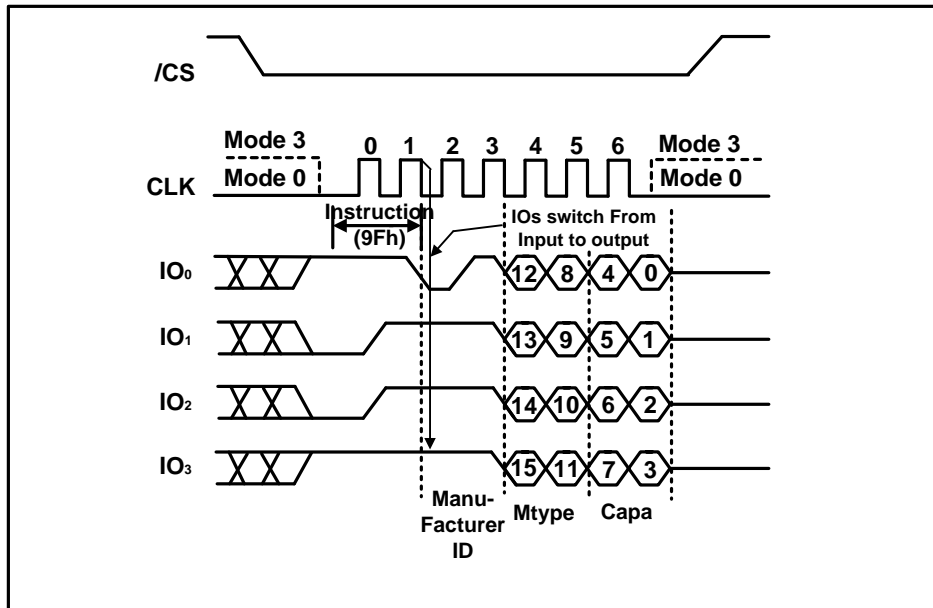


Figure 32b. Read JEDEC ID instruction (QPI Mode)

### 11.2.33 Enable QPI (38h)

The FM25M32A support both Standard/Dual/Quad Serial Peripheral interface (SPI) and Quad Peripheral Interface (QPI). However, SPI mode and QPI mode cannot be used at the same time. “Enable QPI (38h)” instruction is the only way to switch the device from SPI mode to QPI mode.

Upon power-up, the default state of the device upon is Standard/Dual/Quad SPI mode. This provides full backward compatibility with earlier generation of Fidelix serial flash memories. See Instruction Set Table 1-3 for all supported SPI commands. In order to switch the device to QPI mode, the Quad Enable (QE) bit in Status Register 2 must be set to 1 first, and an “Enable QPI (38h)” instruction must be issued. If the Quad Enable (QE) bit is 0, the “Enable QPI (38h)” instruction will be ignored and the device will remain in SPI mode.

See the instruction Set Table 4 for all the commands supported in QPI mode.

When the device is switched from SPI mode to QPI mode, the existing Write Enable and Program/Erase Suspend status, and the Wrap Length setting will remain unchanged.

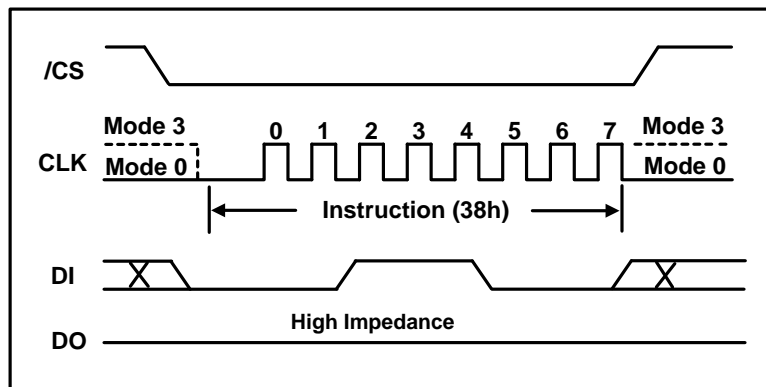


Figure 33. Enable QPI instruction (SPI Mode only)

**11.2.34 Disable QPI (FFh)**

In order to exit the QPI mode and return to the Standard/Dual/Quad SPI mode, a “Disable QPI (FFh)” instruction must be issued.

When the device is switched from QPI mode to SPI mode, the existing Write Enable Latch (WEL) and Program/Erase Suspend status, and the Wrap Length setting will remain unchanged.

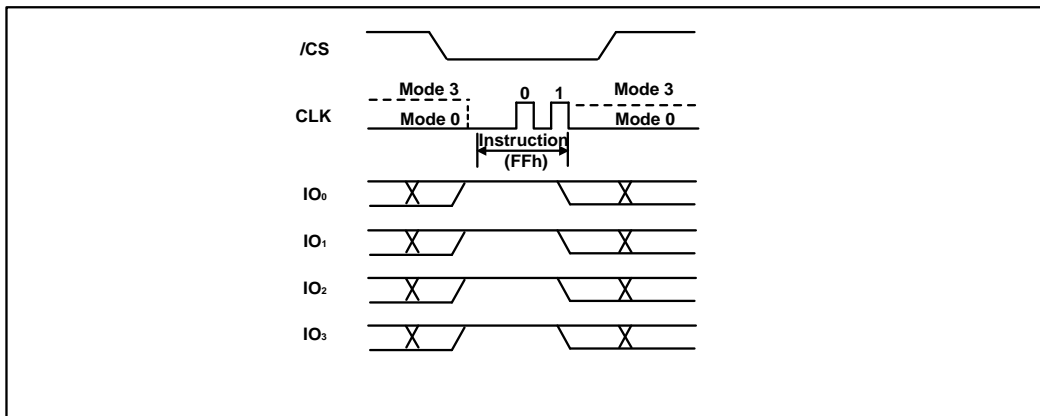


Figure 34. Disable QPI instruction (QPI Mode)

**11.2.35 Disable QPI 2 (ALL FFh)**

In order to exit the QPI mode and return to the Standard/Dual/Quad SPI mode, a “Disable QPI 2 (All FFh)” instruction can be used instead of Disable QPI (FFh) instruction. Refer to 11.2.34.

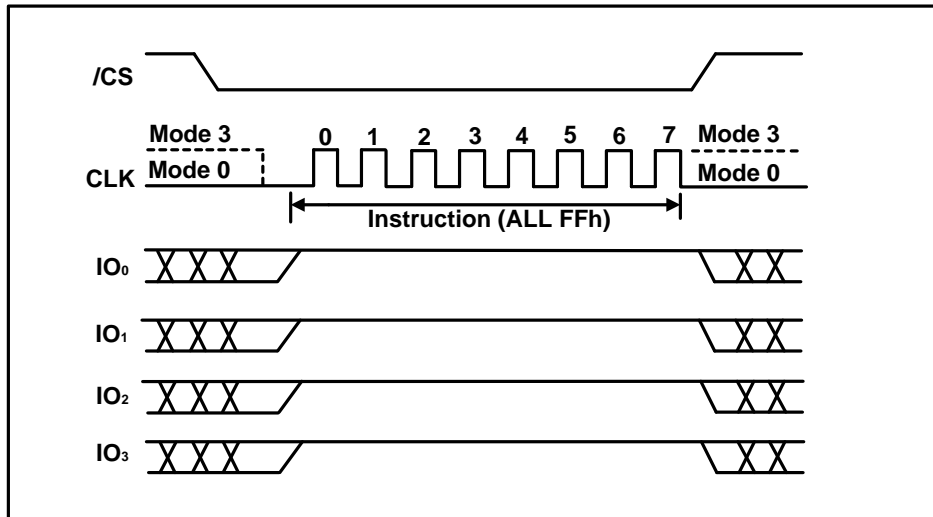


Figure 35. Disable QPI 2 instruction (QPI Mode)

**11.2.36 Enter Secured OTP (B1h)**

The Enter Secured OTP instruction is for entering the additional 4K-bit secured OTP mode. The additional 4K-bit secured OTP is independent from main array, which may be used to store unique serial number for system identifier. After entering the Secured OTP mode, and then follow standard read or program, procedure to read out the data or update data. The Secured OTP data cannot be updated again once it is lock-down

Please note that Write Status Register-1, Write Status Register-2 and Write Security Register commands are not acceptable during the access of secure OTP region. Once security OTP is lock down, only commands related with read are valid.

The Enter Secured OTP instruction sequence is shown in figure 36.

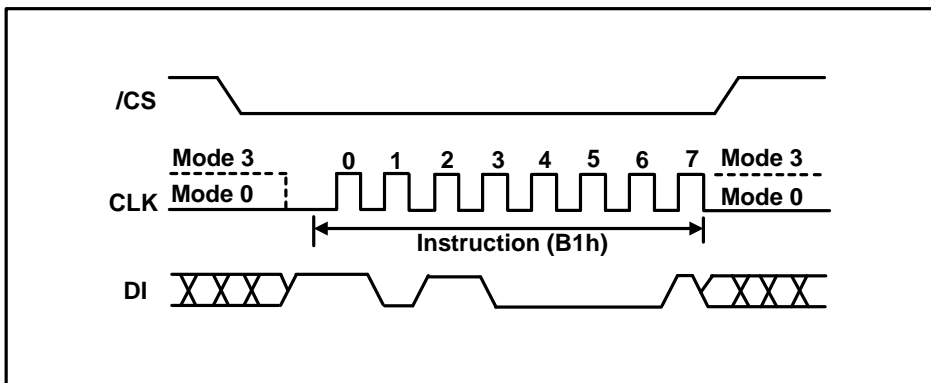


Figure 36a. Enter Secured OTP instruction (SPI Mode)



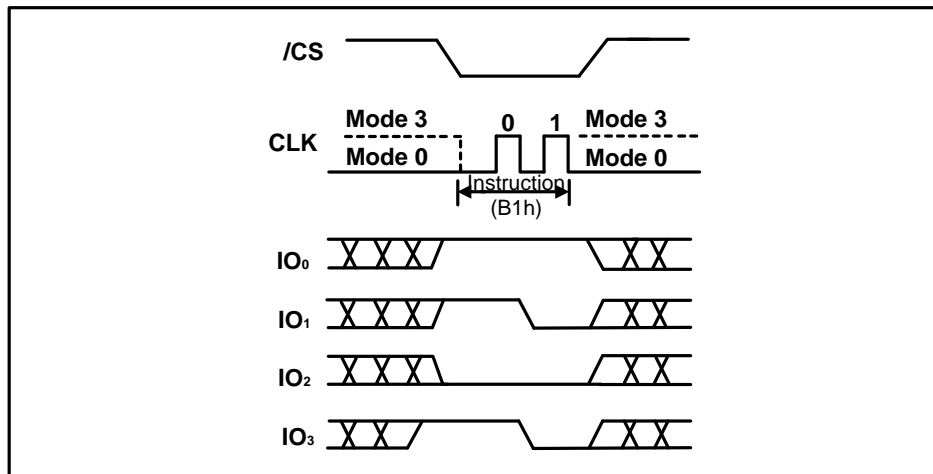


Figure 36b. Enter Secured OTP instruction (QPI Mode)

**11.2.37 Exit Secured OTP (C1h)**

The Exit Secured OTP instruction is for exiting the additional 4K-bit secured OTP mode. The Exit Secured OTP instruction sequence is shown in figure 37a & 37b.

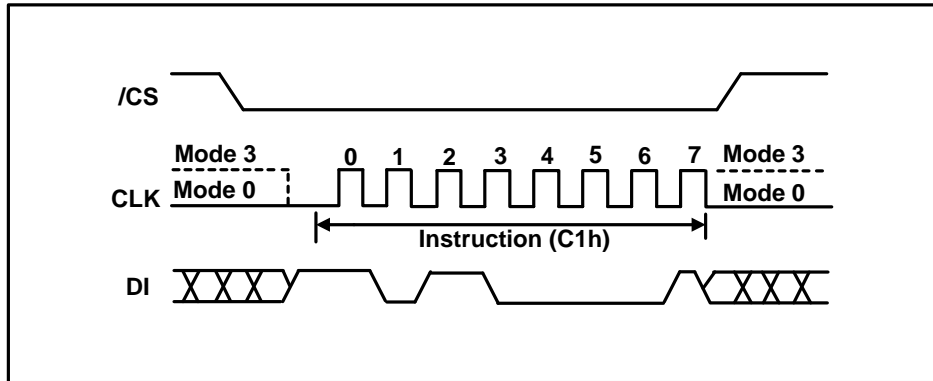


Figure 37a. Exit Secured OTP instruction (SPI Mode)

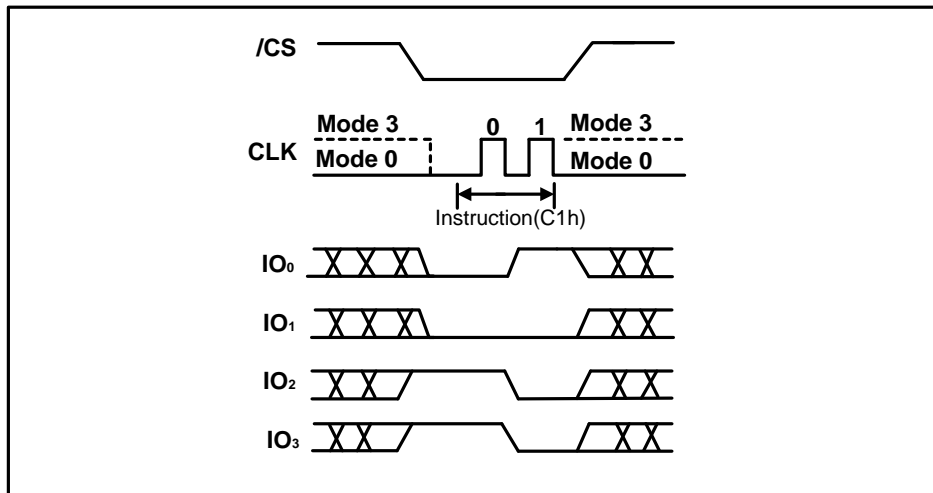


Figure 37b. Exit Secured OTP instruction (QPI Mode)

**11.2.38 Read Security Register (2Bh)**

The Read Security Register instruction is for reading the value of Security Register bits. The Read Security Register can be read at any time (even in program/erase/write status register-1 and write status register-2 condition) and continuously.

The definition of the Security Register bits is as below:

**Secured OTP Indicator bit.** The Secured OTP indicator bit shows the chip is locked by factory before ex-factory or not. When it is “0”, it indicates non-factory lock, “1” indicates factory-lock.

**Lock-down Secured OTP (LDSO) bit.** By writing Write Security Register instruction, the LDSO bit may be set to “1” for customer lock-down purpose. However, once the bit is set to “1” (Lock-down), the LDSO bit and the 4K-bit Secured OTP area cannot be updated any more. While it is in 4K-bit Secured OTP mode, array access is not allowed to write.

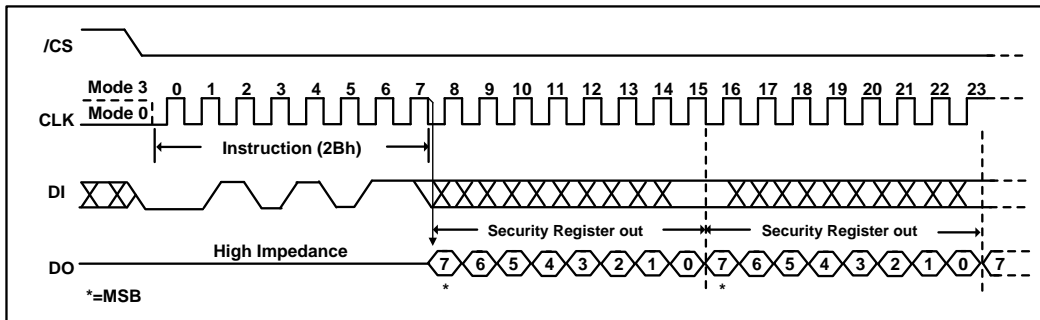


Figure 38a. Read Security Register instruction (SPI Mode)

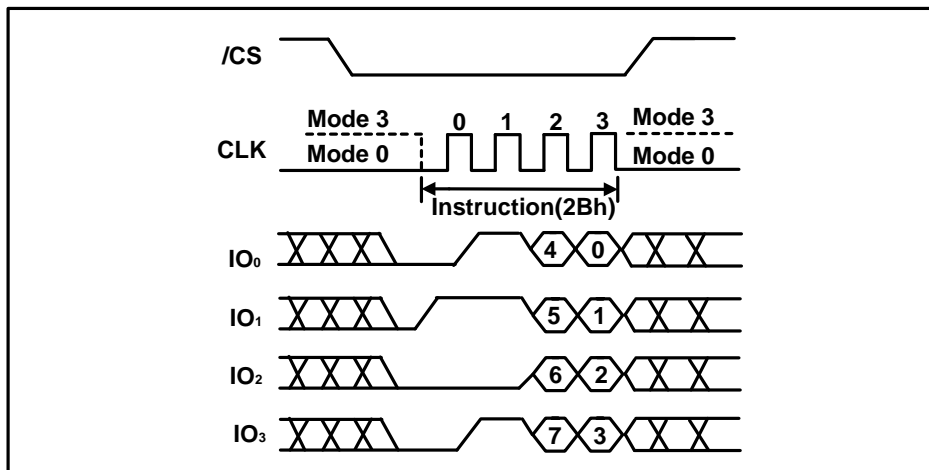


Figure 38b. Read Security Register instruction (QPI Mode)

**Security Register Definition**

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
x	x	x	x	x	x	LDSO (indicate if lock- down)	Secured OTP indicator bit
reserved	reserved	reserved	reserved	reserved	reserved	0 = not lock-down 1 = lock- down(can not program/e rase OTP)	0 = non factory lock 1 = factory lock
Volatile bit	Volatile bit	Volatile bit	Volatile bit	Volatile bit	Volatile bit	Non- Volatile bit	Non- Volatile bit

**11.2.39 Write Security Register (2Fh)**

The Write Security Register instruction is for changing the values of Security Register bits. Unlike Write Status Register, the WREN instruction is not required before writing Write Security Register instruction. The Write Security Register instruction may change the value of bit1 (LDSO bit) for customer to lock-down the 4K-bit Secured OTP area. Once the LDSO bit is set to “1”, the Secured OTP area cannot be updated any more.

The /CS must go high exactly at the boundary; otherwise, the instruction will be rejected and not executed.

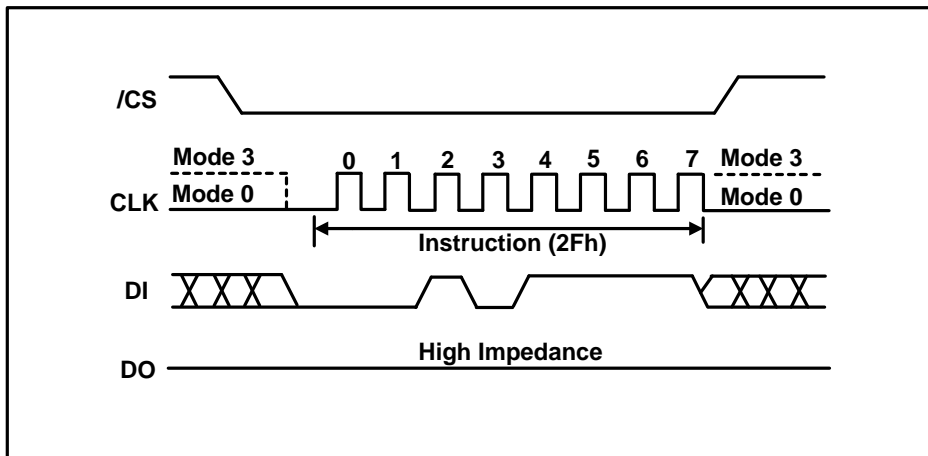


Figure 39a. Write Security Register instruction (SPI Mode)

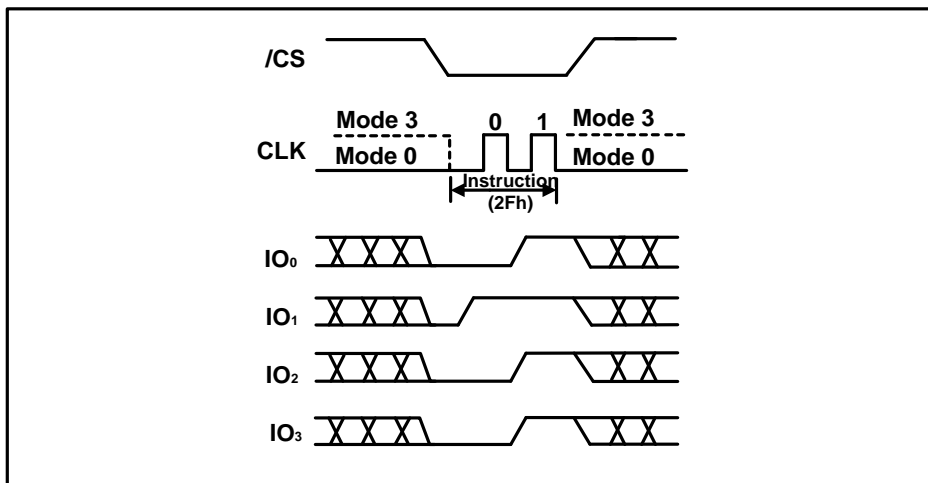


Figure 39b. Write Security Register instruction (SPI Mode)

**4K-bit Secured OTP**

It's for unique identifier to provide 4K-bit one-time-program area for setting device unique serial number which may be set by factory or system customer. Please refer to table of “4K-bit secured OTP definition”.

- Security register bit 0 indicates whether the chip is locked by factory or not.
- To program the 4K-bit secured OTP by entering 4K-bit secured OTP mode (with ENSO command) and going through normal program procedure, and then exiting 4K-bit secured OTP

mode by writing EXSO command

- Customer may lock-down bit1 as "1". Please refer to "table of security register definition" for security register bit definition and table of "4K-bit secured OTP definition" for address range definition.
- Note. Once lock-down whatever by factory or customer, it cannot be changed any more. While in 4K-bit secured OTP mode, array access is not allowed to write.

**4K-bit secured OTP definition**

Address range	Size	Standard Factory Lock	Customer Lock
000000 ~ 00000F	128-bit	ESN (Electrical Serial Number)	Determined by customer
000010 ~ 0001FF	3968-bit	N/A	

### 11.2.40 Set Burst with Wrap (77h)

The Set Burst with Wrap (77h) instruction is used in conjunction with “Fast Read Quad I/O” and “Word Read Quad I/O” instructions to access a fixed length of 8/16/32/64-byte section within a 256-byte page. Certain applications can benefit from this feature and improve the overall system code execution performance.

Similar to a Fast Read Quad I/O instruction, the Set Burst with Wrap instruction is initiated by driving the /CS pin low and then shifting the instruction code “77h” followed by 24 dummy bits and 8 “Wrap Bits”, W7-0. The instruction sequence is shown in Set Burst with Wrap Instruction Sequence.

Wrap bit W7 and the lower nibble W3-0 are not used.

W6, W5	W4 = 0		W4 = 1(Default)	
	Wrap Around	Wrap Length	Wrap Around	Wrap Length
0 0	Yes	8-byte	No	N/A
0 1	Yes	16-byte	No	N/A
1 0	Yes	32-byte	No	N/A
1 1	Yes	64-byte	No	N/A

Once W6-4 is set by a Set Burst with Wrap instruction, all the following “Fast Read Quad I/O” and Word Read Quad I/O instructions will use the W6-4 setting to access the 8/16/32/64-byte section within any page. To exit the “Wrap Around” function and return to normal read operation, another Set Burst with Wrap instruction should be issued to set W4 = 1. The default value of W4 upon power on is 1. In the case of a system Reset while W4 = 0, it is recommended that the controller issues a Set Burst with Wrap instruction or Reset (99h) instruction to reset W4 = 1 prior to any normal Read instructions since FM25M32A does not have a hardware Reset Pin.

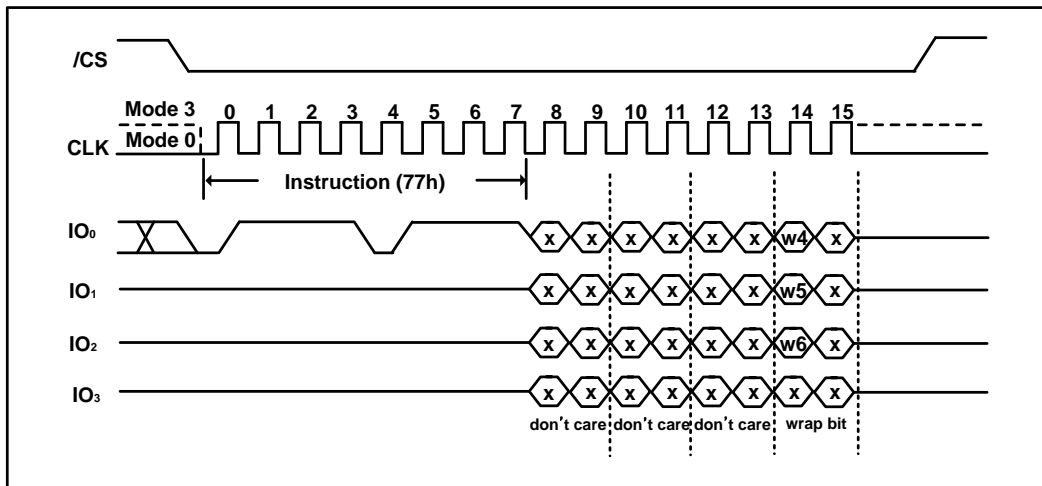


Figure 40. Set Burst with Wrap Instruction Sequence

**11.2.41 Word Read Quad I/O (E7h)**

The Word Read Quad I/O (E7h) instruction is similar to the Fast Read Quad I/O (EBh) instruction except that the lowest Address bit (A0) must equal 0 and only two dummy clock are required prior to the data output. The Quad I/O dramatically reduces instruction overhead allowing faster random access for code execution (XIP) directly from the Quad SPI. The Quad Enable bit (QE) of Status Register-2 must be set to enable the Word Read Quad I/O instruction.

**Word Read Quad I/O with “Continuous Read Mode”**

The Word Read Quad I/O instruction can further reduce instruction overhead through setting the “Continuous Read Mode” bits (M7-0) after the input Address bits (A23-0), as shown in Figure 41a. The upper nibble of the (M7-4) controls the length of the next Word Read Quad I/O instruction through the inclusion or exclusion of the first byte instruction code. The lower nibble bits of the (M[3:0]) are don't care (“X”). However, the IO pins should be high-impedance prior to the falling edge of the first data out clock.

If the “Continuous Read Mode” bits M[7-4]= Ah, then the next Fast Read Quad I/O instruction (after /CS is raised and then lowered) does not require the E7h instruction code, as shown in Figure 41b. This reduces the instruction sequence by eight clocks and allows the Read address to be immediately entered after /CS is asserted low. If the “Continuous Read Mode” bits M[7:4] do not equal to Ah(1,0,1,0) the next instruction (after /CS is raised and then lowered) requires the first byte instruction code, thus returning to normal operation.

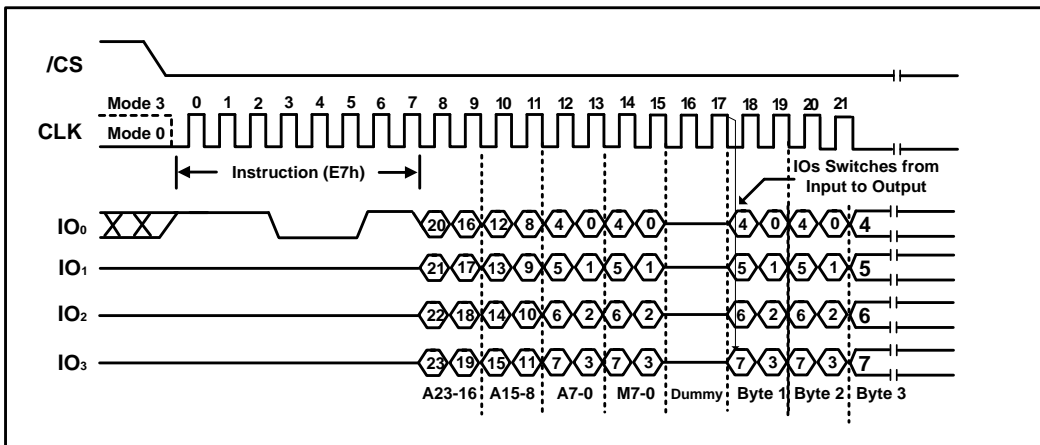


Figure 41a. Word Read Quad I/O instruction (Initial instruction or previous set M7-0 ≠ Ah, SPI Mode)



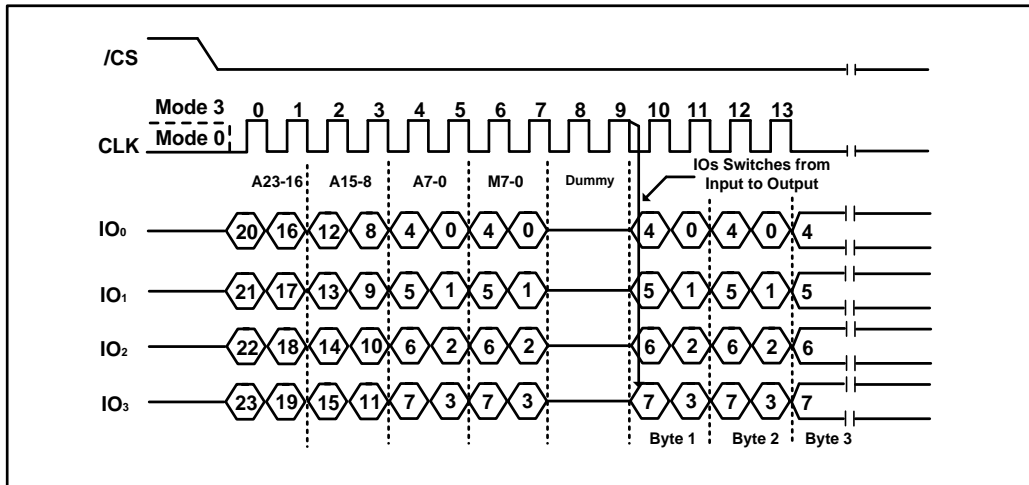


Figure 41b. Word Read Quad I/O instruction (Previous instruction set M7-0= Axh, SPI Mode)

**Word Read Quad I/O with “8/16/32/64-Byte Wrap Around” in Standard SPI mode**

The Word Read Quad I/O instruction can also be used to access a specific portion within a page by issuing a “Set Burst with Wrap” (77h) command prior to E7h. The “Set Burst with Wrap” (77h) command can either enable or disable the “Wrap Around” feature for the following E7h commands. When “Wrap Around” is enabled, the output data starts at the initial address specified in the instruction, once it reaches the ending boundary of the 8/16/32/64-byte section, the output will wrap around to the beginning boundary automatically until /CS is pulled high to terminate the command.

The Burst with Wrap feature allows applications that use cache to quickly fetch a critical address and then fill the cache afterwards within a fixed length (8/16/32/64-byte) of data without issuing read commands.

The “Set Burst with Wrap” instruction allows three “Wrap Bits”, W6-4 to be set. The W4 bit is used to enable or disable the “Wrap Around” operation while W6-5 are used to specify the length of the wrap around section within a page. See 11.2.40 for detail descriptions.

**11.2.42 Burst Read with Wrap (0Ch)**

The “Burst Read with Wrap (0Ch)” instruction provides an alternative way to perform the read operation with “Wrap Around” in QPI mode. The instruction is similar to the “Fast Read (0Bh)” instruction in QPI mode, except the addressing of the read operation will “Wrap Around” to the beginning boundary of the “Wrap Length” once the ending boundary is reached.

The “Wrap Length” and the number of dummy of clocks can be configured by the “Set Read Parameters (C0h)” instruction.

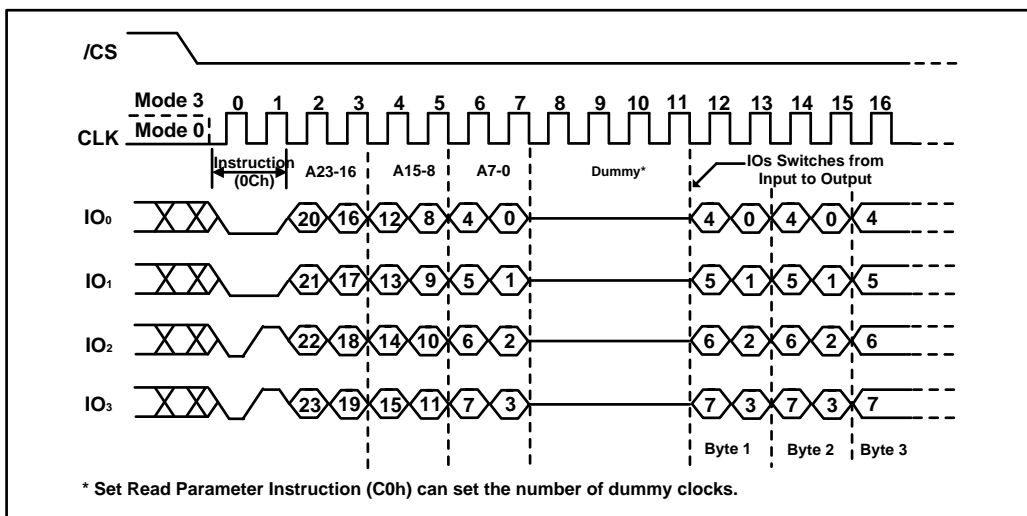


Figure 42. Burst Read with Wrap instruction (QPI Mode)

**11.2.43 Set Read Parameters (C0h)**

In QPI mode, to accommodate a wide range of applications with different needs for either maximum read frequency or minimum data access latency, “Set Read Parameters (C0h)” instruction can be used to configure the number of dummy clocks for “Fast Read (0Bh)”, “Fast Read Quad I/O (EBh)” & “Burst Red with Wrap (0Ch)” instructions, and to configure the number of bytes of “Wrap Length” for the “Burst Read with Wrap (0Ch)” instruction.

In Standard SPI mode, the “Set Read Parameters (C0h)” instruction is not accepted. The dummy clocks for various Fast Read instructions in Standard/Dual/Quad SPI mode are fixed, please refer to the instruction. Table 11.2.2-11.2.5 for details. The “Wrap Length” is set by W5-4 bit in the “Set Burst with Wrap (77h)” instruction. This setting will remain unchanged when the device is switched from Standard SPI mode to QPI mode.

The default “Wrap Length” after a power up or a Reset instruction is 8 bytes, the default number of dummy clocks is 4.

P4	DUMMY CLOCKS	Maximum READ FREQ.
0	4	80MHz
1	6	104MHz

P1 – P0	WRAP LENGTH
0 0	8-byte
0 1	16-byte
1 0	32-byte
1 1	64-byte

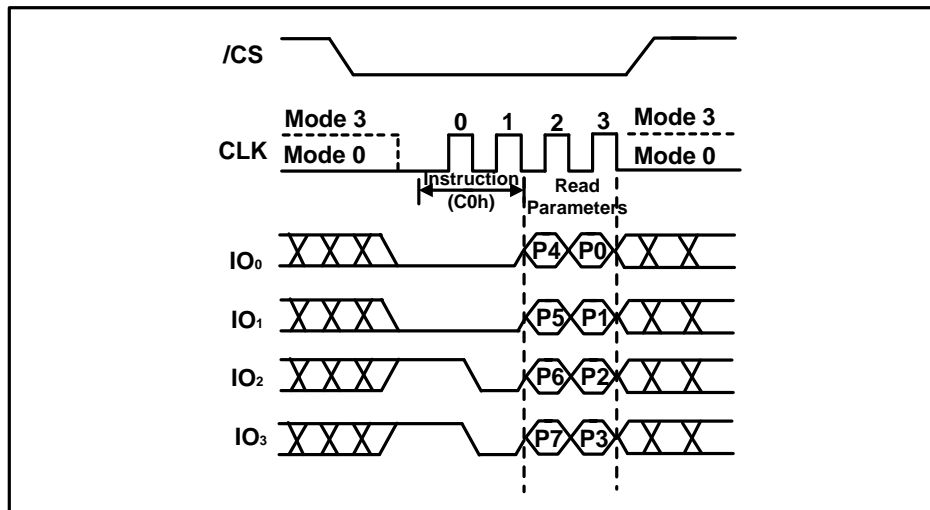


Figure 43. Set Read Parameters instruction (QPI Mode)

### 11.2.44 Enable Reset (66h) and Reset (99h)

Because of the small package and the limitation on the number of pins, the FM25M32A provide a software Reset instruction instead of a dedicated RESET pin. Once the Reset instruction is accepted, any on-going internal operations will be terminated and the device will return to its default power-on state and lose all the current volatile settings, such as Volatile Status Register bits, Write Enable Latch (WEL) status, Program/Erase Suspend status, Read parameter setting(P7-P0), Continuous Read Mode bit setting(M7-M0) and Wrap bit setting(W6-W4).

“Enable Reset (66h)” and “Reset (99h)” instructions can be issued in either SPI mode or QPI mode. To avoid accidental reset, both instructions must be issued in sequence. Any other commands other than “Reset (99h)” after the “Enable (66h)” command will disable the “Reset Enable” state. A new sequence of “Enable Reset (66h)” and “Reset (99h)” is needed to reset the device. Once the Reset command is accepted by the device will take approximately  $t_{RST} = 30\mu s$  to reset. During this period, no command will be accepted.

Data corruption may happen if there is an on-going or suspended internal Erase or Program operation when Reset command sequence is accepted by device. It is recommended to check the BUSY bit and the SUS bit in Status Register before issuing the Reset command sequence.

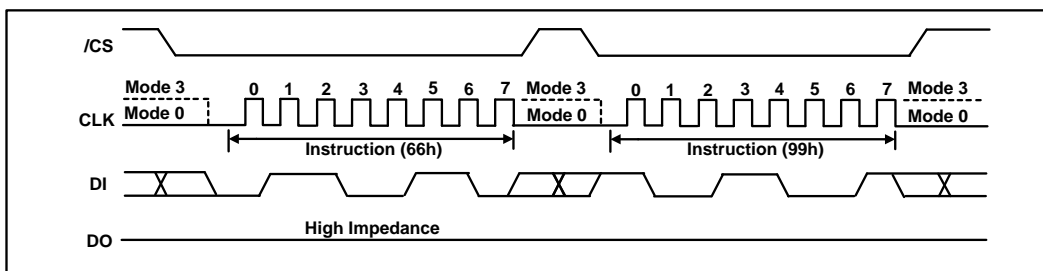


Figure 44a. Enable Reset and Reset Instruction (SPI Mode)

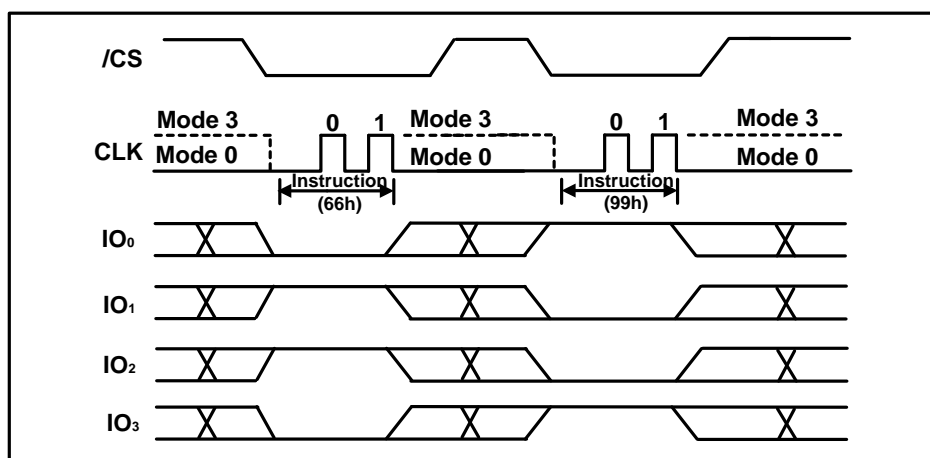


Figure 44b. Enable Reset and Reset Instruction (QPI Mode)

**11.2.45 Read Serial Flash Discovery Parameter (SFDP)**

The Read Serial Flash Discovery Parameter (SFDP) instruction allows reading the Serial Flash Discovery Parameter area (SFDP). This SFDP area is composed of 2048 read-only bytes containing operating characteristics and vendor specific information. The SFDP area is factory programmed. If the SFDP area is blank, the device is shipped with all the SFDP bytes at FFh. If only a portion of the SFDP area is written to, the portion not used is shipped with bytes in erased state (FFh). The instruction sequence for the read SFDP has the same structure as that of a Fast Read instruction. First, the device is selected by driving Chip Select (/CS) Low. Next, the 8-bit instruction code (5Ah) and the 24-bit address are shifted in, followed by 8 dummy clock cycles. The bytes of SFDP content are shifted out on the Serial Data Output (DO) starting from the specified address. Each bit is shifted out during the falling edge of Serial Clock (CLK). The instruction sequence is shown here. The Read SFDP instruction is terminated by driving Chip Select (/CS) High at any time during data output.

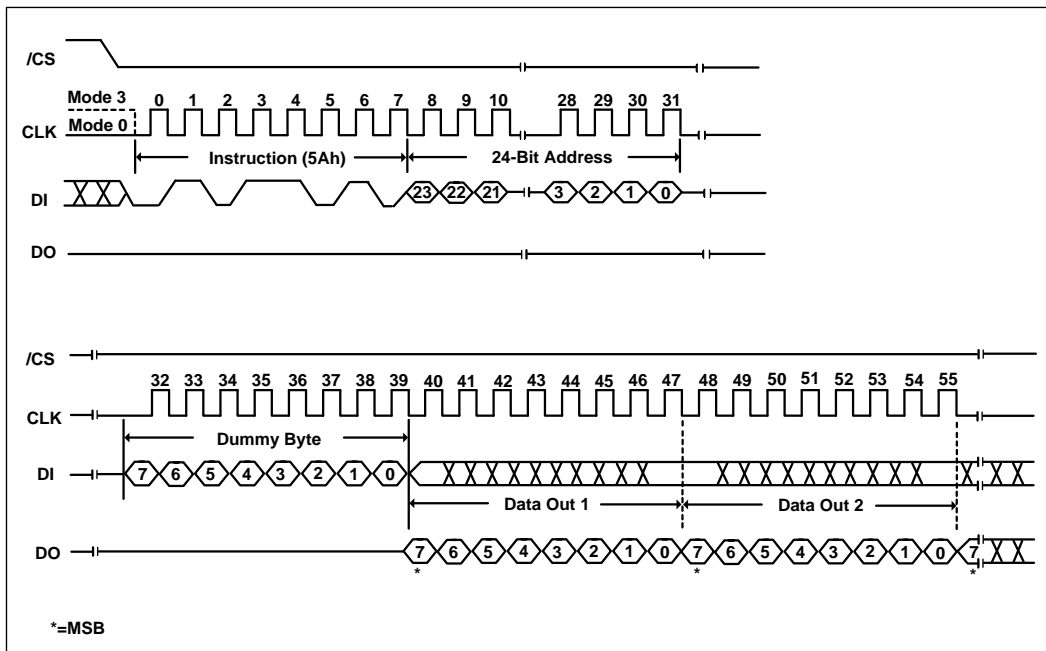


Figure 45. Read SFDP Register Instruction Sequence Diagram

**Read Serial Flash Discovery Parameter (SFDP)**

BYTE ADDRESS	DATA	DESCRIPTION	COMMENT
00h	53h	SFDP Signature	SFDP Signature =50444653h
01h	46h	SFDP Signature	
02h	44h	SFDP Signature	
03h	50h	SFDP Signature	
04h	01h	SFDP Minor Revisions	SFDP revision 1.1
05h	01h	SFDP Major Revisions	
06h	00h	Number of Parameter Header(NPH)	1 Parameter Header
07h	FFh	Reserved	
08h	F8h	PID(0) <sup>(3)</sup> : Manufacture JEDEC ID	F8h = Fidelix
09h	00h	PID(0) : Serial Flash Basics Minor Revisions	Serial Flash Basics Revision 1.0
0Ah	01h	PID(0) : Serial Flash Basics Major Revisions	
0Bh	04h	PID(0) : Serial Flash Basics Length	4 Dwords <sup>(2)</sup>
0Ch	80h	PID(0) : Address of Parameter ID(0) Table (A7-A0)	PID(0) Table Address = 000080h
0Dh	00h	PID(0) : Address of Parameter ID(0) Table (A15-A8)	
0Eh	00h	PID(0) : Address of Parameter ID(0) Table (A23-A16)	
0Fh	FFh	Reserved	
10h	F8h	PID(1) : Manufacture JEDEC ID	F8h = Fidelix
11h	00h	PID(1) : Serial Flash Properties Minor Revisions	Serial Flash Basics Revision 1.0
12h	01h	PID(1) : Serial Flash Properties Major Revisions	
13h	00h	PID(1) : Serial Flash Properties Length	00h = Unimplemented
14h	90h	PID(1) : Address of Parameter ID(0) Table (A7-A0)	PID(1) Table Address = 000090h
15h	00h	PID(1) : Address of Parameter ID(0) Table (A15-A8)	
16h	00h	PID(1) : Address of Parameter ID(0) Table (A23-A16)	
17h	FFh	Reserved	
... <sup>(1)</sup>	FFh	Reserved	
80h	E5h	Bit[7:5] = 111      Reserved	
		Bit[4:3] = 00      Non-volatile Status Register	
		Bit[2] = 1          Page Programmable	
		Bit[1:0] = 01      Support 4KB Erase	

**Read Serial Flash Discovery Parameter(SFDP) (cont'd)**

BYTE ADDRESS	DATA	DESCRIPTION	COMMENT
81h	20h	4K-Byte Erase Opcode	
82h	F1h	Bit[7] = 1      Reserved	
		Bit[6] = 1      Supports Single Input Quad Output	
		Bit[5] = 1      Supports Quad Input Quad Output	
		Bit[4] = 1      Supports Dual Input Dual Output	
		Bit[3] = 0      Dual Transfer Rate not Supported	
		Bit[2:1] = 00    3-Byte/24-Bit Addressing	
		Bit[1] = 1      Supports Single Input Dual Output	
83h	FFh	Reserved	
84h	FFh	Flash Size in Bits	32 Mega Bits = 01FFFFFFh
85h	FFh	Flash Size in Bits	
86h	FFh	Flash Size in Bits	
87h	01h	Flash Size in Bits	
88h	44h	Bit[7:5] = 010    8 Mode Bits are needed Bit[4:0] = 00100    16 Dummy Bits are needed	
89h	EBh	Quad Input Quad Output Fast Read Opcode	
8Ah	08h	Bit[7:5] = 000    No Mode Bits are needed	Fast Read Quad Output Setting
		Bit[4:0] = 01000    8 Dummy Bits are needed	
8Bh	6Bh	Single Input Quad Output Fast Read Opcode	
8Ch	08h	Bit[7:5] = 000    No Mode Bits are needed	Fast Read Dual Output Setting
		Bit[4:0] = 01000    8 Dummy Bits are needed	
8Dh	3Bh	Single Input Dual Output Fast Read Opcode	
8Eh	80h	Bit[7:5] = 100    8 Mode Bits are needed	Fast Read Dual I/O Setting
		Bit[4:0] = 00000    No Dummy Bits are needed	
8Fh	BBh	Dual Input Dual Output Fast Read Opcode	
... <sup>(1)</sup>	FFh	Reserved	
EFh	FFh	Reserved	
F0h-FFh	xxh	Reserved	

**Notes:**

1. Data stored in Byte Address 18h to 7Fh & 90h to FFh are Reserved, the value is FFh.
2. 1 Dword = 4 Bytes.
3. PID(x) = Parameter Identification Table(x)

## 12. ELECTRICAL CHARACTERISTICS

### 12.1 Absolute Maximum Ratings <sup>(1)</sup>

PARAMETERS	SYMBOL	CONDITIONS	RANGE	UNIT
Supply Voltage	VCC		-0.6 to VCC+0.4	V
Voltage Applied to Any Pin	VIO	Relative to Ground	-0.6 to VCC +0.4	V
Transient Voltage on any Pin	VIOT	<20nS Transient Relative to Ground	-1.0V to VCC +1.0V	V
Storage Temperature	TSTG		-65 to +150	°C
Lead Temperature	TLEAD		See Note <sup>(3)</sup>	°C
Electrostatic Discharge Voltage	VESD	Human Body Model <sup>(4)</sup>	-2000 to +2000	V

**Notes:**

1. Specification for FM25M32A is preliminary. See preliminary designation at the end of this document.
2. This device has been designed and tested for the specified operation ranges. Proper operation outside of these levels is not guaranteed. Exposure to absolute maximum ratings may affect device reliability. Exposure beyond absolute maximum ratings may cause permanent damage.
3. Compliant with JEDEC Standard J-STD-20C for small body Sn-Pb or Pb-free (Green) assembly and the European directive on restrictions on hazardous substances (RoHS) 2002/95/EU.
4. JEDEC Std JESD22-A114A (C1=100pF, R1=1500 ohms, R2=500 ohms).

### 12.2 Operating Ranges

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNIT
Erase/Program Cycles	VCC	FR = 104MHz (Single/Dual/Quad SPI) fR = 50MHz (Read Data 03h)	1.65	1.95	V
Temperature, Operating	Tj	Industrial	-40	+85	°C

### 12.3 Endurance and Data Retention

PARAMETER	CONDITIONS	MIN	MAX	UNIT
Erase/Program Cycles	4KB sector, 32/64KB block or full chip.	100,000		Cycles
Data Retention	Full Temperature Range		20	years



### 12.4 Power-up Timing and Write Inhibit Threshold

PARAMETER	SYMBOL	SPEC		UNIT
		MIN	MAX	
VCC(min) to /CS Low	tVSL <sup>(1)</sup>	10		μs
Time Delay Before Write Instruction	tPUW <sup>(1)</sup>	1	10	ms
Write Inhibit Threshold Voltage	VWI <sup>(1)</sup>	1.0	1.4	V

**Note:**

1. These parameters are characterized only.

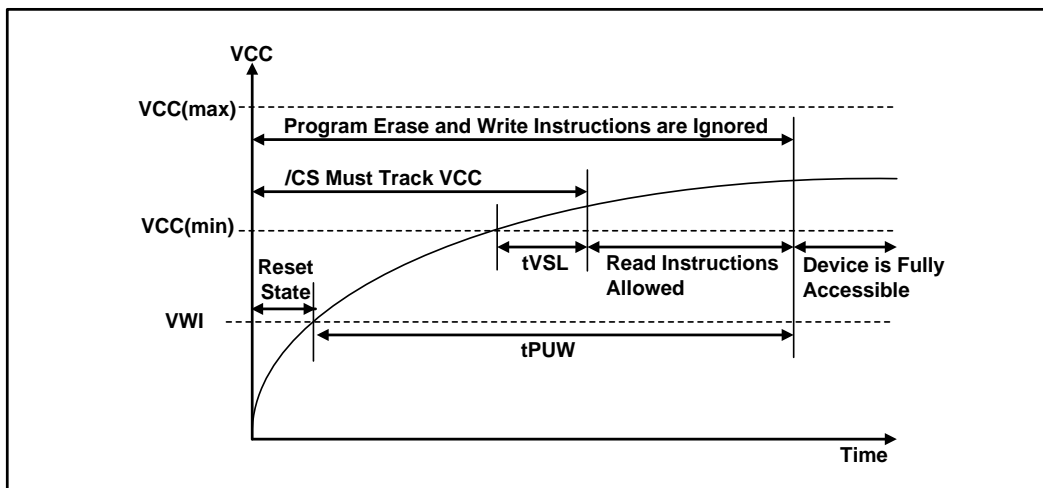


Figure 47. Power-up Timing and Voltage Levels

### 12.5 DC Electrical Characteristics

PARAMETER	SYMBOL	CONDITION	SPEC			UNIT
			MIN	TYP	MAX	
Input Capacitance	CIN <sup>(1)</sup>	VIN=0V <sup>(2)</sup>			6	pF
Output Capacitance	COU <sup>(1)</sup>	VOU=0V <sup>(2)</sup>			8	pF
Input Leakage	ILI				±2	μA
I/O Leakage	ILO				±2	μA
Standby Current	ICC1	/CS=VCC, VIN=GND or VCC		10	50	μA
Power-down Current	ICC2	/CS=VCC, VIN=GND or VCC		3	10	μA
Current Read Data/ Dual/Quad 1MHz <sup>(2)</sup>	ICC3	C=0.1 VCC / 0.9VCC IO=Open			15	mA
Current Read Data/ Dual/Quad 50MHz <sup>(2)</sup>	ICC3	C=0.1 VCC / 0.9VCC IO=Open			20	mA
Current Read Data/ Dual/Quad 80MHz <sup>(2)</sup>	ICC3	C=0.1 VCC / 0.9VCC IO=Open			30	mA
Current Read Data/ Dual/Quad 104MHz <sup>(2)</sup>	ICC3	C=0.1 VCC / 0.9VCC IO=Open			40	mA
Current Write Status Register	ICC4	/CS=VCC		10	18	mA
Current page Program	ICC5	/CS=VCC		20	25	mA
Current Sector/Block Erase	ICC6	/CS=VCC		20	25	mA
Current Chip Erase	ICC7	/CS=VCC		20	25	mA
Input Low Voltages	VIL		-0.5		VCC x0.3	V
Input High Voltages	VIH		VCC x0.7		VCC +0.4	V
Output Low Voltages	VOL	IOL= 100μA			0.2	V
Output High Voltages	VOH	IOH=-100μA	VCC -0.2			V

**Notes:**

1. Tested on sample basis and specified through design and characterization data, TA = 25°C, VCC = 1.8V.
2. Checked Board Pattern.

## 12.6 AC Measurement Conditions

PARAMETER	SYMBOL	SPEC		UNIT
		MIN	MAX	
Load Capacitance	$C_L$		30	pF
Input Rise and Fall Times	$T_R, T_F$		5	ns
Input Pulse Voltages	$V_{IN}$	0.2 VCC to 0.8 VCC		V
Input Timing Reference Voltages	IN	0.3 VCC to 0.7 VCC		V
Output Timing Reference Voltages	OUT	0.5 VCC to 0.5 VCC		V

**Note:**

1. Output Hi-Z is defined as the point where data out is no longer driven.

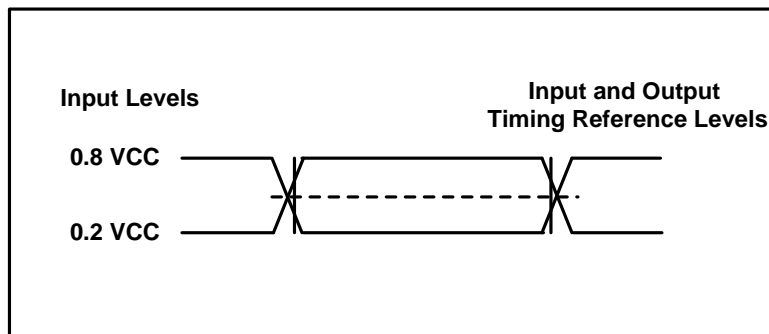


Figure 48. AC Measurement I/O Waveform

**12.7 AC Electrical Characteristics**

DESCRIPTION	SYMBOL	ALT	SPEC			UNIT
			MIN	TYP	MAX	
Clock frequency For all instructions, except Read Data (03h) 1.65V-1.95V VCC & Industrial Temperature	FR	$f_c$	D.C.		104	MHz
Clock freq. Read Data instruction (03h)	$f_R$		D.C.		50	MHz
Clock High, Low Time except Read Data (03h)	tCLH, tCLL <sup>(1)</sup>		4			ns
Clock High, Low Time for Read Data (03h) instructions	tCRLH, tCRLL <sup>(1)</sup>		8			ns
Clock Rise Time peak to peak	tCLCH <sup>(2)</sup>		0.1			V/ns
Clock Fall Time peak to peak	tCHCL <sup>(2)</sup>		0.1			V/ns
/CS Active Setup Time relative to CLK	tSLCH	tCSS	5			ns
/CS Not Active Hold Time relative to CLK	tCHSL		5			ns
Data In Setup Time	tDVCH	tDSU	2			ns
Data In Hold Time	tCHDX	tDH	5			ns
/CS Active Hold Time relative to CLK	tCHSH		5			ns
/CS Not Active Setup Time relative to CLK	tSHCH		5			ns
/CS Deselect Time (for Read instructions/ Write, Erase and Program instructions)	tSHSL	tCSH	10/50			ns
Output Disable Time	tSHQZ <sup>(2)</sup>	tDIS			7	ns
Clock Low to Output Valid	tCLQV	tV			7	ns
Output Hold Time	tCLQX	tHO	0			ns
/Hold Active Setup Time relative to CLK	tHLCH		5			ns

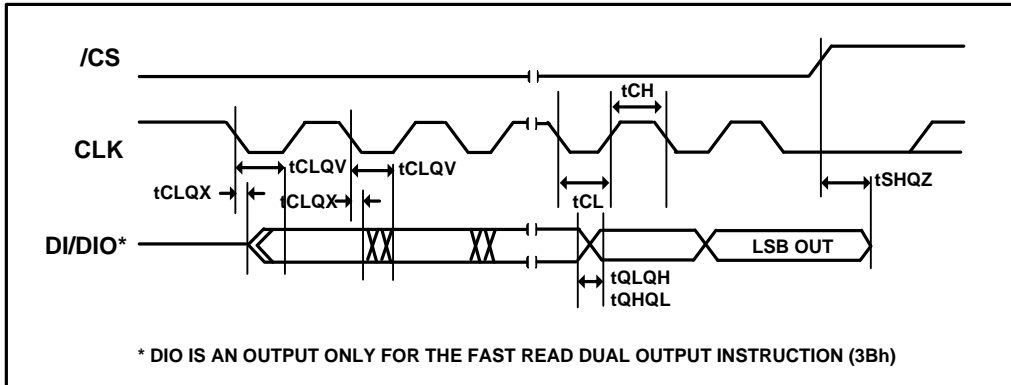
**12.8 AC Electrical Characteristics (cont'd)**

DESCRIPTION	SYMBOL	ALT	SPEC			UNIT
			MIN	TYP	MAX	
/HOLD Active Hold Time relative to CLK	tCHHH		5			ns
/HOLD Not Active Setup Time relative to CLK	tHHCH		5			ns
/HOLD Not Active Hold Time relative to CLK	tCHHL		5			ns
/HOLD to Output Low-Z	tHHQX <sup>(2)</sup>	t <sub>LZ</sub>			7	ns
/HOLD to Output High-Z	tHLQZ <sup>(2)</sup>	t <sub>HZ</sub>			12	ns
Write Protect Setup Time Before /CS Low	tWHSL <sup>(3)</sup>		20			ns
Write Protect Setup Time After /CS High	tSHWL <sup>(3)</sup>		100			ns
/CS High to Power-down Mode	tDP <sup>(2)</sup>				3	μs
/CS High to Standby Mode without Electronic Signature Read	tRES1 <sup>(2)</sup>				3	μs
/CS High to Standby Mode with Electronic Signature Read	tRES2 <sup>(2)</sup>				1.8	μs
/CS High to next Instruction after Suspend	tSUS <sup>(2)</sup>				20	μs
CS High to next Instruction after Reset	tRST <sup>(2)</sup>				30	μs
Write Status Register Time	tW			10	15	ms
Byte Program Time	tBP			10	150	μs
Page Program Time	tPP			1.5	5	ms
Sector Erase Time(4KB)	tSE			40	300	ms
Block Erase Time(32KB)	tBE1			200	1000	ms
Block Erase Time(64KB)	tBE2			300	1500	ms
Chip Erase Time	tCE			10	50	s

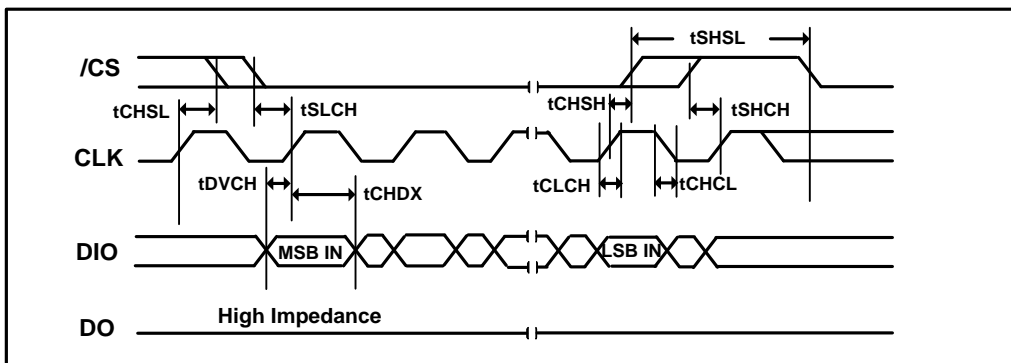
**Notes:**

1. Clock high + Clock low must be less than or equal to 1/fc.
2. Value guaranteed by design and/or characterization, not 100% tested in production.
3. Only applicable as a constraint for a Write Status Register instruction when Sector Protect Bit is set to 1.
4. Commercial temperature only applies to Fast Read (F<sub>R1</sub> & F<sub>R2</sub>). Industrial temperature applies to all other parameters.

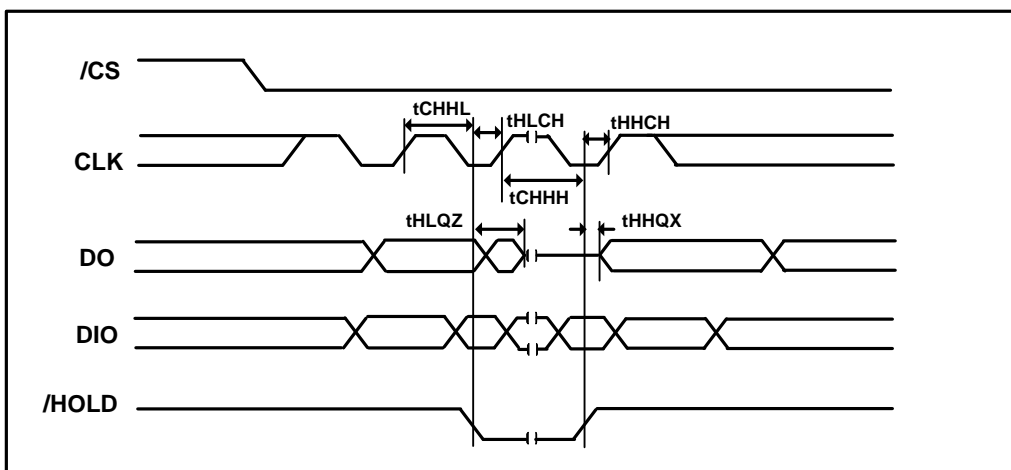
### 12.9 Serial Output Timing



### 12.10 Input Timing

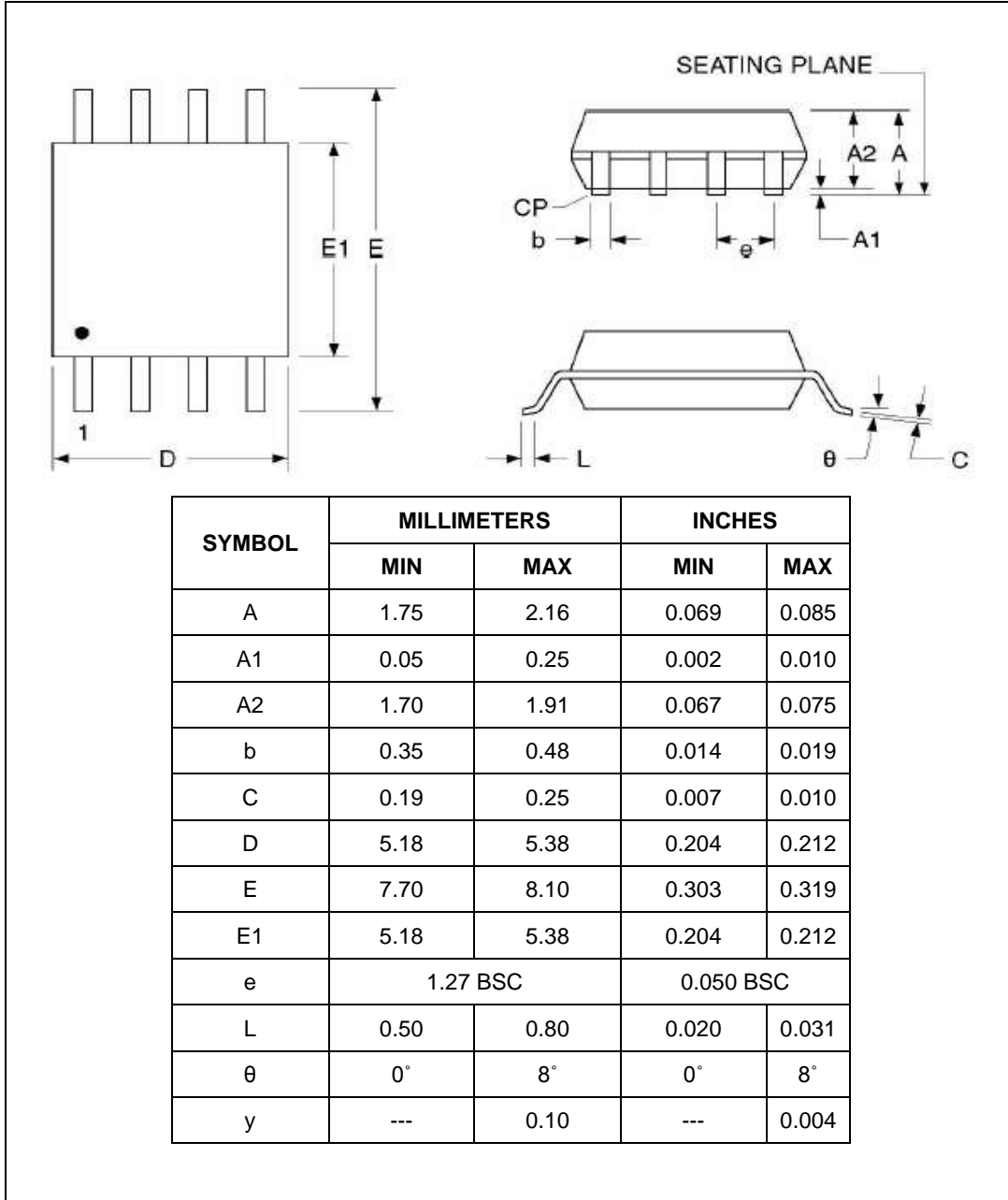


### 12.11 Hold Timing



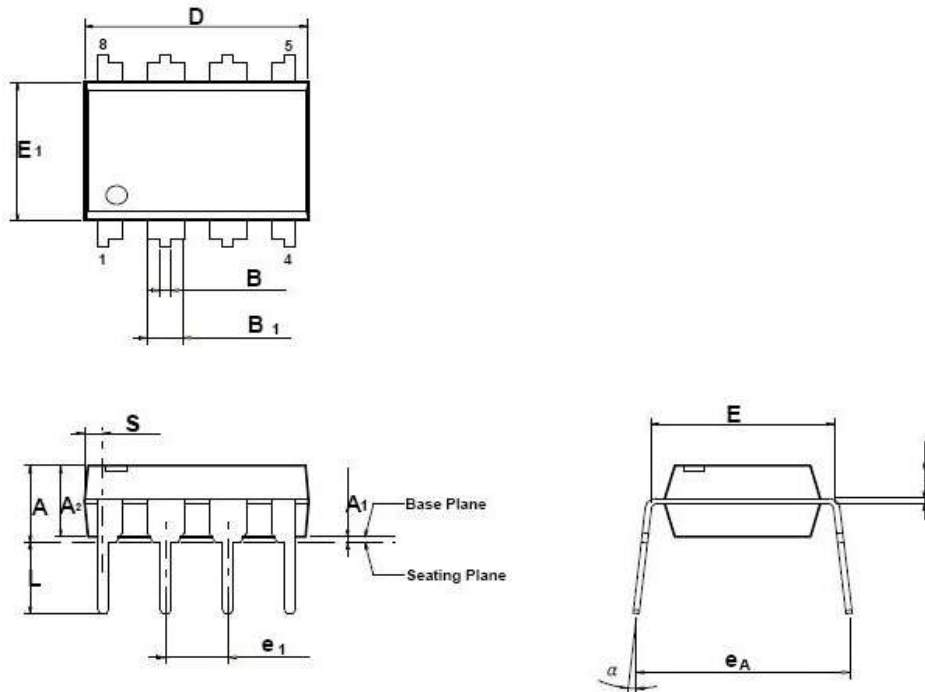
### 13. PACKAGE SPECIFICATION

#### 13.1 8-Pin SOIC 208-mil



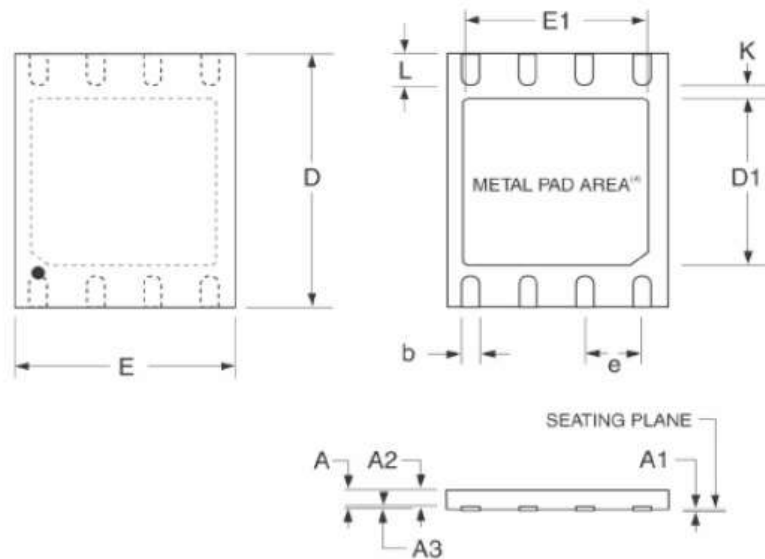
**Notes:**

1. Controlling dimensions: inches, unless otherwise specified.
2. BSC = Basic lead spacing between centers.
3. Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
4. Formed leads shall be planar with respect to one another within .0004 inches at the seating plane.

**13.2 8-Pin PDIP 300-mil**


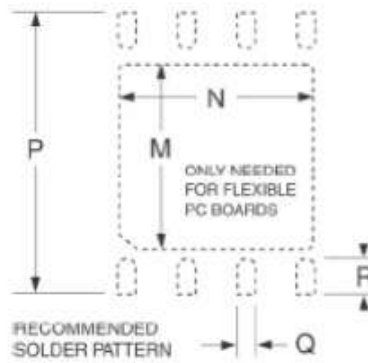
SYMBOL	Dimension in inch			Dimension in min		
	MIN	Nom	MAX	MIN	Nom	MAX
A	---	---	0.210	---	---	5.334
A <sub>1</sub>	0.015	---	---	0.381	---	---
A <sub>2</sub>	0.125	0.130	0.135	3.18	3.30	3.43
B	0.016	0.018	0.022	0.41	0.46	0.56
B <sub>1</sub>	0.058	0.060	0.064	1.47	1.52	1.63
c	0.008	0.010	0.014	0.20	0.25	0.36
D	0.360	0.365	0.370	9.14	9.27	9.40
E	0.290	0.300	0.310	7.37	7.62	7.87
E <sub>1</sub>	0.245	0.250	0.255	6.22	6.35	6.48
e <sub>1</sub>	0.090	0.100	0.110	2.29	2.54	2.79
L	0.120	0.130	0.140	3.05	3.30	3.56
α	0	---	15	0	---	15
e A	0.335	0.355	0.375	8.51	9.02	9.53
S	---	---	0.045	---	---	1.14



**13.3 8-contact 6x5 WSON**


SYMBOL	MILLIMETERS			INCHES		
	MIN	TYP.	MAX	IN	TYP.	MAX
A	0.70	0.75	0.80	0.0276	0.0295	0.0315
A1	0.00	0.02	0.05	0.0000	0.0008	0.0019
2		0.55			0.0126	
A3	0.19	0.20	0.25	0.0075	0.0080	0.0098
b	0.36	0.40	0.48	0.0138	0.0157	0.0190
D <sup>(3)</sup>	5.90	6.00	6.10	0.2320	0.2360	0.2400
D1	3.30	3.40	3.50	0.1299	0.1338	0.1377
E	4.90	5.00	5.10	0.1930	0.1970	0.2010
E1 <sup>(3)</sup>	4.20	4.30	4.40	0.1653	0.1692	0.1732
e <sup>(2)</sup>	1.27 BSC			0.0500 BSC		
K	0.20			0.0080		
L	0.50	0.60	0.75	0.0197	0.0236	0.0295

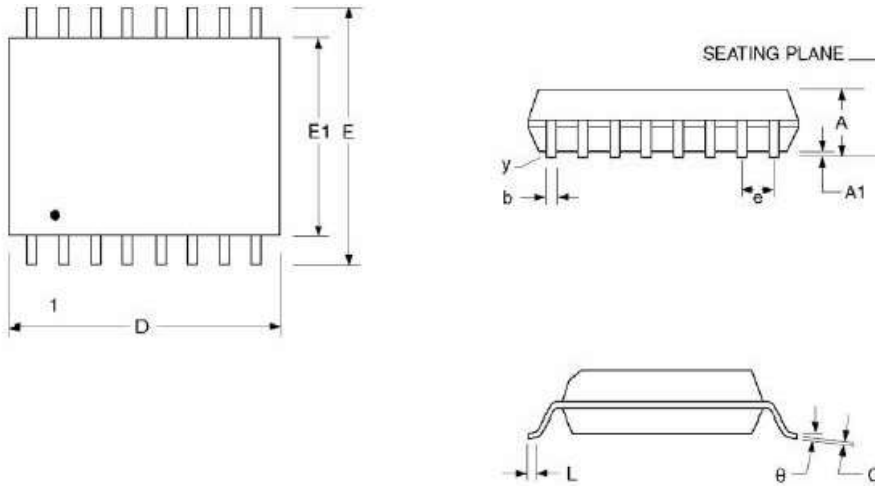
## 13.4 8-contact 6x5 WSON Cont'd.



SYMBOL	MILLIMETERS			INCHES		
	MIN	TYP.	MAX	MIN	TYP.	MAX
<b>SOLDER PATTERN</b>						
M		3.40			0.1338	
N		4.30			0.1692	
P		6.00			0.2360	
Q		0.50			0.0196	
R		0.75			0.0255	

**Notes:**

1. Advanced Packaging Information; please contact FIDELIX SEMICONDUCTOR for the latest minimum and maximum specifications.
2. BSC = Basic lead spacing between centers.
3. Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
4. The metal pad area on the bottom center of the package is connected to the device ground (GND pin). Avoid placement of exposed PCB bias under the pad.

**13.5 16-Pin SOIC 300-mil**


SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.36	2.64	0.093	0.104
A1	0.10	0.30	0.005	0.012
b	0.33	0.51	0.013	0.020
C	0.18	0.28	0.007	0.000
D <sup>(3)</sup>	10.08	10.49	0.397	0.413
E	10.01	10.64	0.394	0.419
E1 <sup>(3)</sup>	7.39	7.59	0.291	0.299
e <sup>(2)</sup>	1.27BSC		0.050	
L	0.39	1.27	0.015	0.050
θ	0°	8°	0°	8°
y	---	0.076	---	0.003

**Notes:**

1. Controlling dimensions: inches, unless otherwise specified.
2. BSC = Basic lead spacing between centers.
3. Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.

**14. ORDERING INFORMATION<sup>(1)</sup>**

